Tutorial on Memory-Centric Computing: Processing-Using-Memory

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Prof. Onur Mutlu

ISCA 2024

29 June 2024

SAFARI

ETH zürich

Agenda

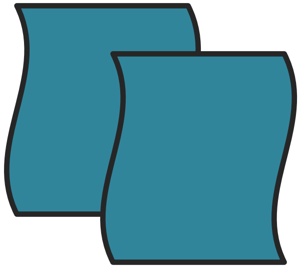
- Introduction to Memory-Centric Computing Systems
- Invited Talk by Prof. Minsoo Rhu:
  "*Memory-Centric Computing Systems – For AI and Beyond*"
- Coffee Break
- Real-World Processing-Near-Memory Systems
- Processing-Using-Memory Architectures for Bulk Bitwise Op.
- Invited Talk by Prof. Saugata Ghose:
  "*RACER and ReRAM PUM*"
- PIM Programming & Infrastructure for PIM Research
- Closing Remarks

Processing in Memory: Two Approaches

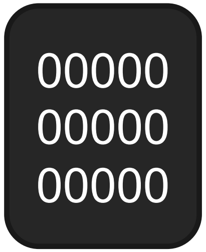
1. Processing near Memory
2. Processing using Memory

Starting Simple: Data Copy and Initialization

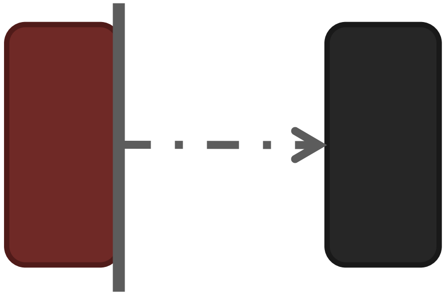
memmove & *memcpy*: 5% cycles in Google's datacenter [Kanev+ ISCA'15]



Forking

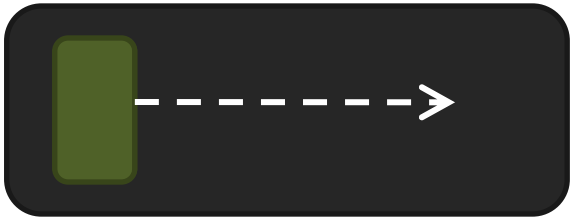


Zero initialization
(e.g., security)



Checkpointing

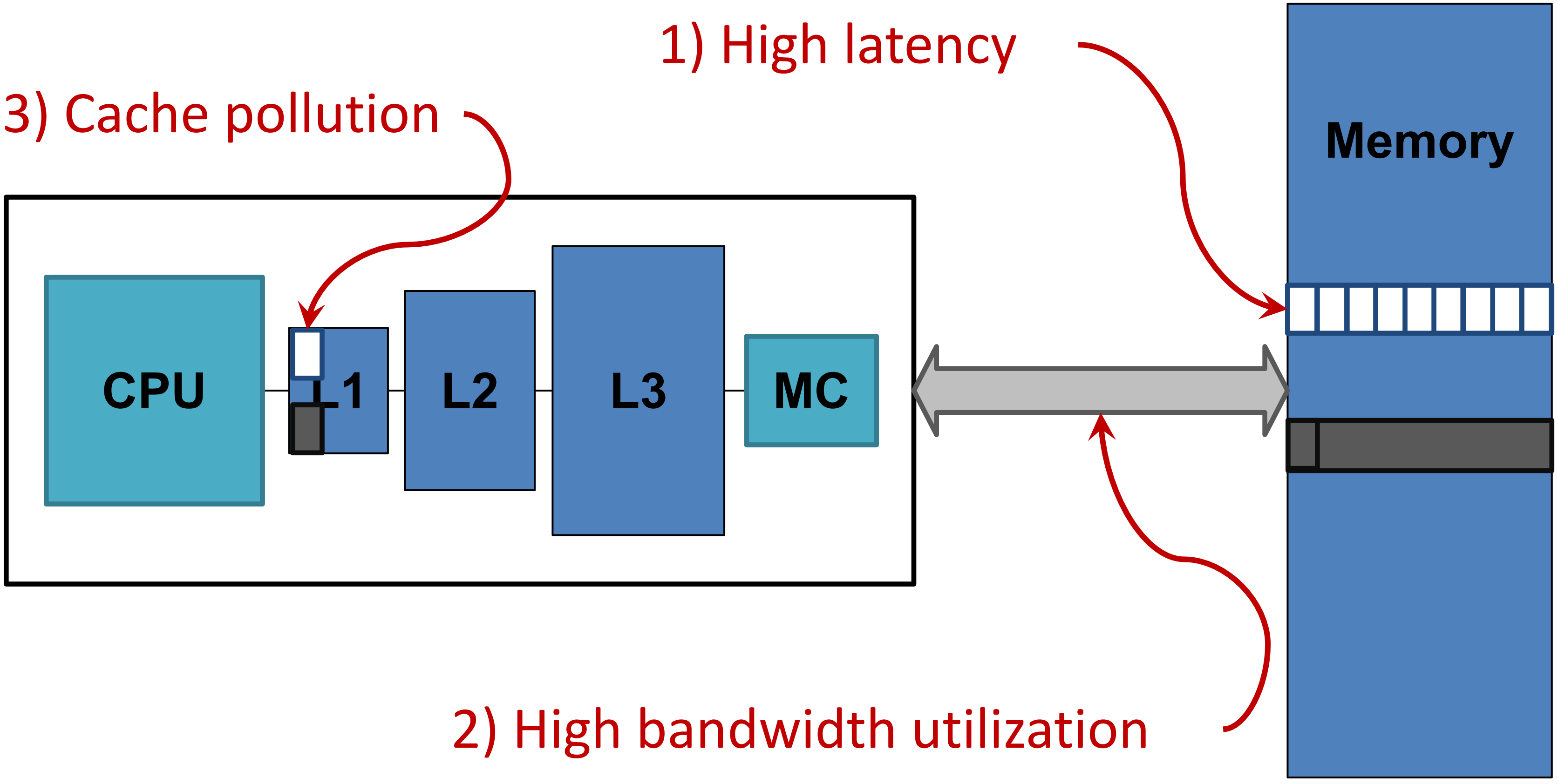
VM Cloning
Deduplication



Page Migration

● ● ●
Many more

Today's Systems: Bulk Data Copy



1) High latency

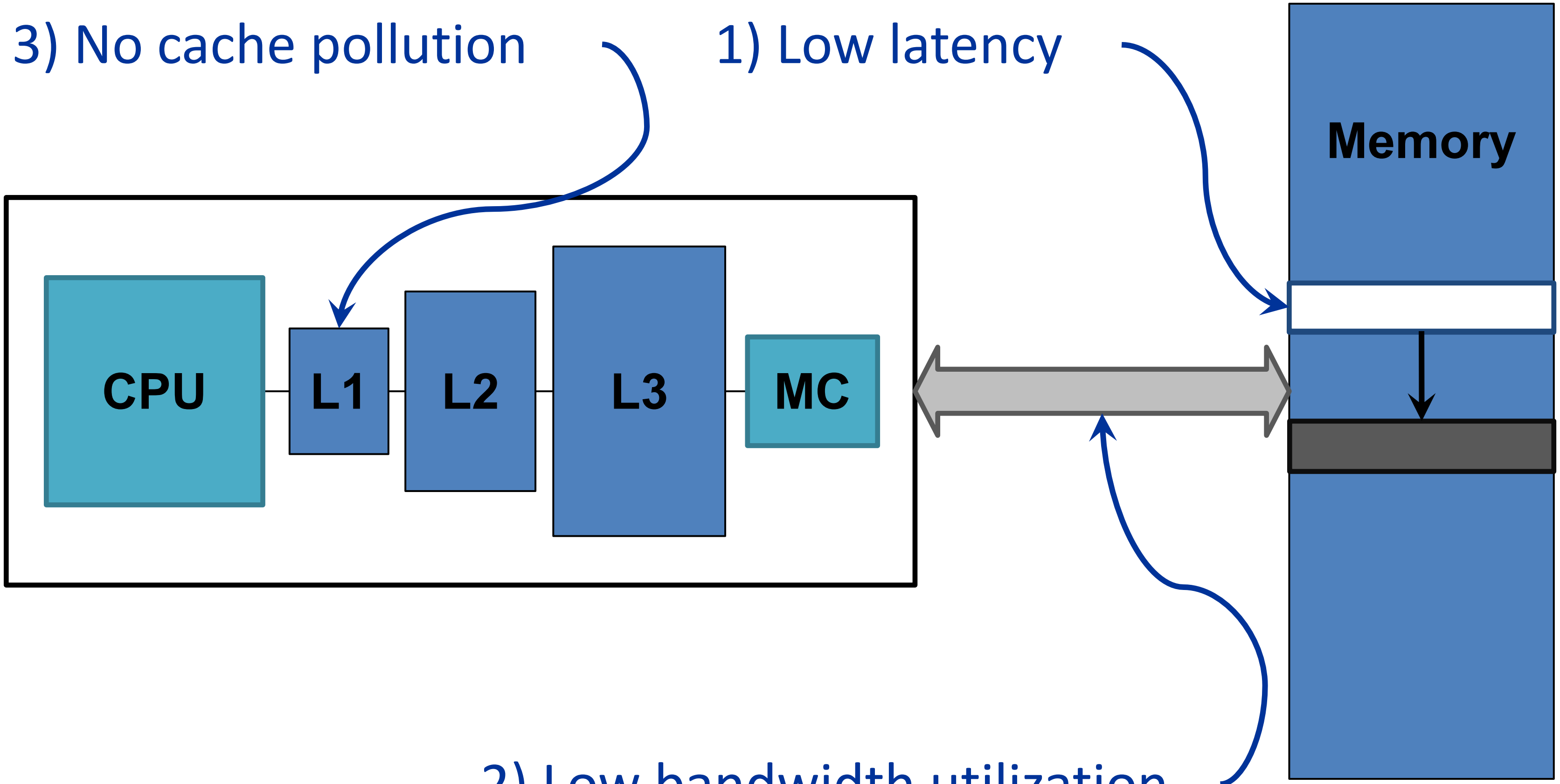
3) Cache pollution

2) High bandwidth utilization

4) Unwanted data movement

1046ns, 3.6uJ (for 4KB page copy via DMA)

Future Systems: In-Memory Copy



3) No cache pollution

1) Low latency

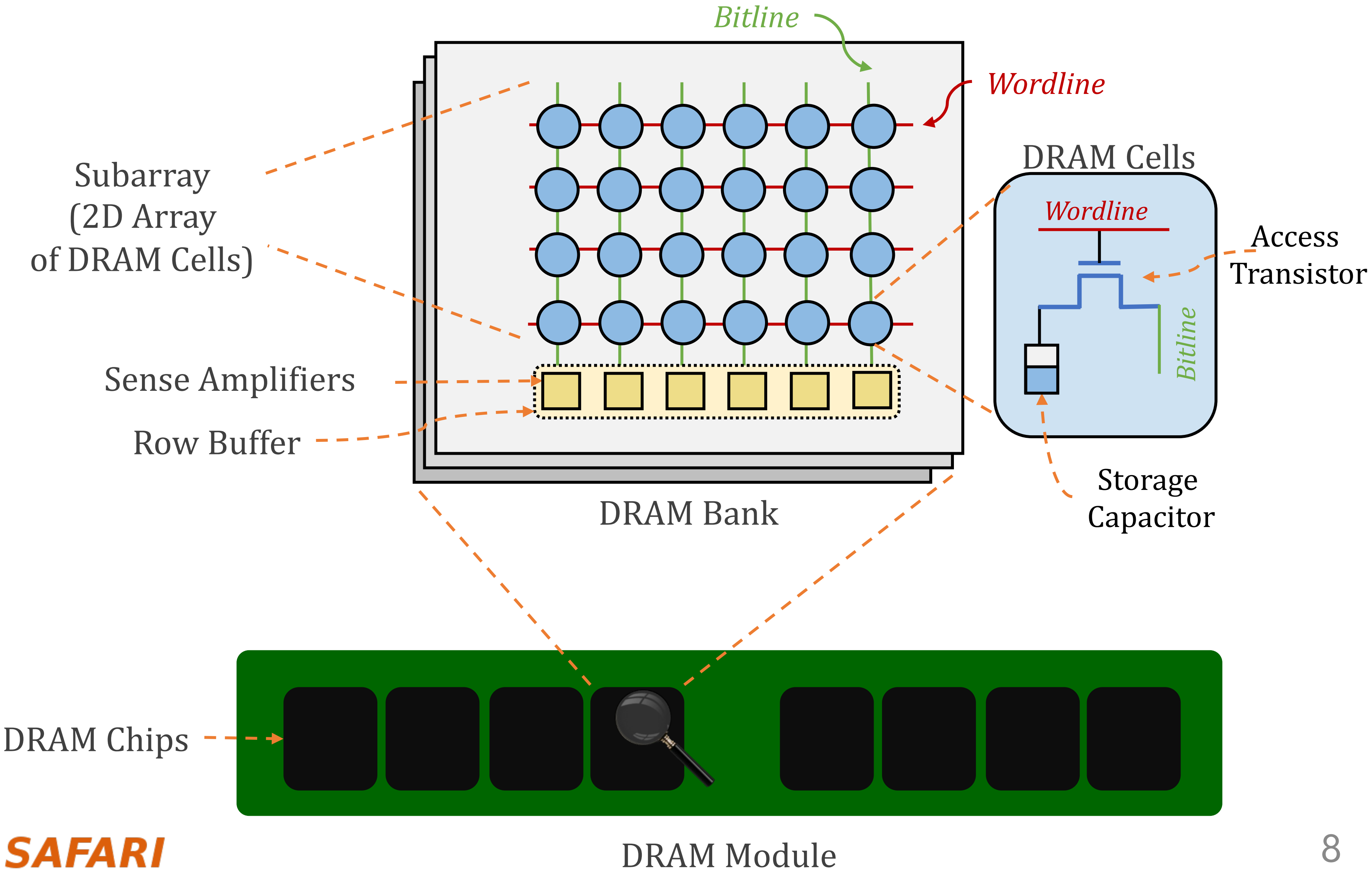
2) Low bandwidth utilization

4) No unwanted data movement

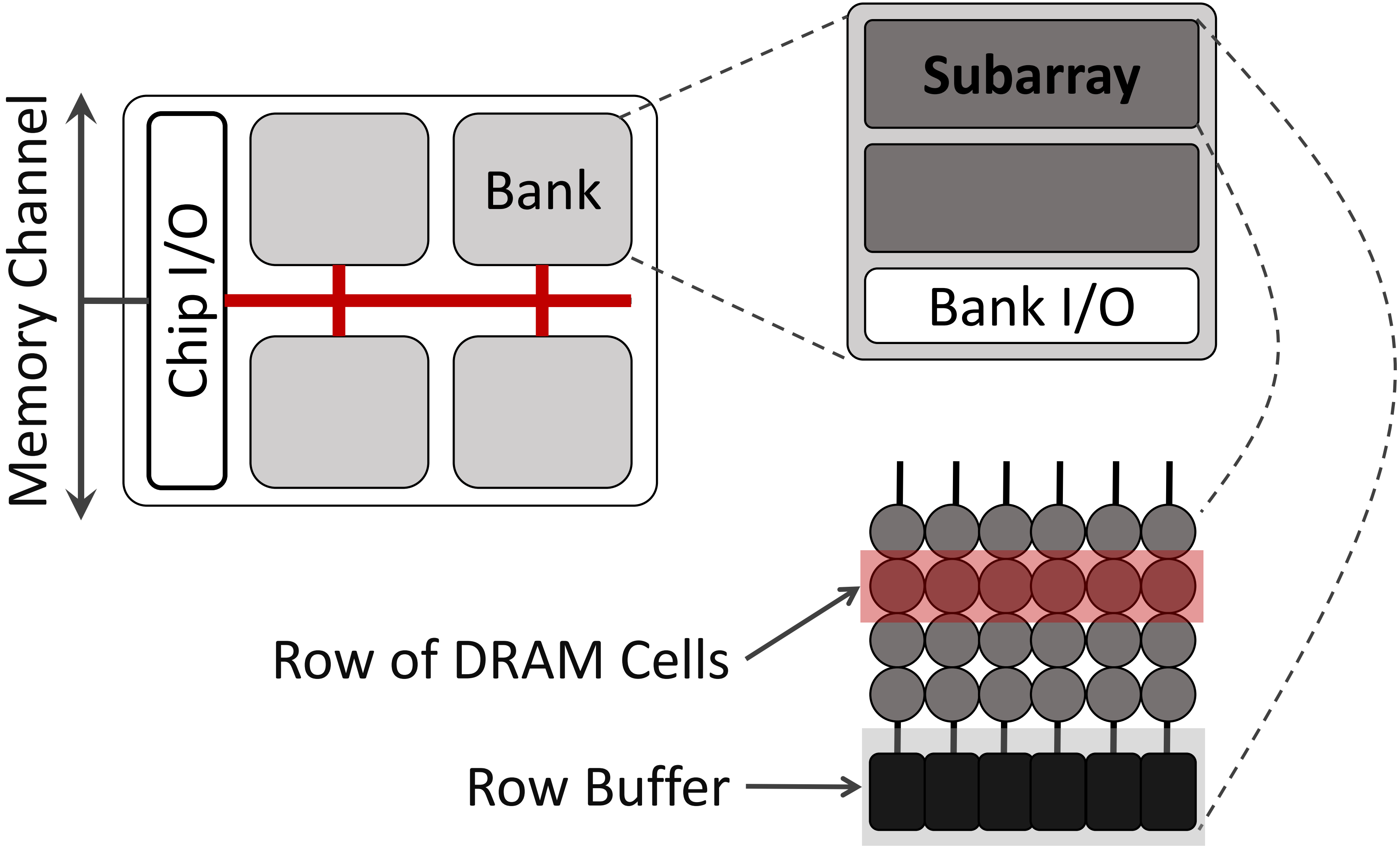
1046ns, 3.6uJ → 90ns, 0.04uJ

Brief Review: Inside A DRAM Chip

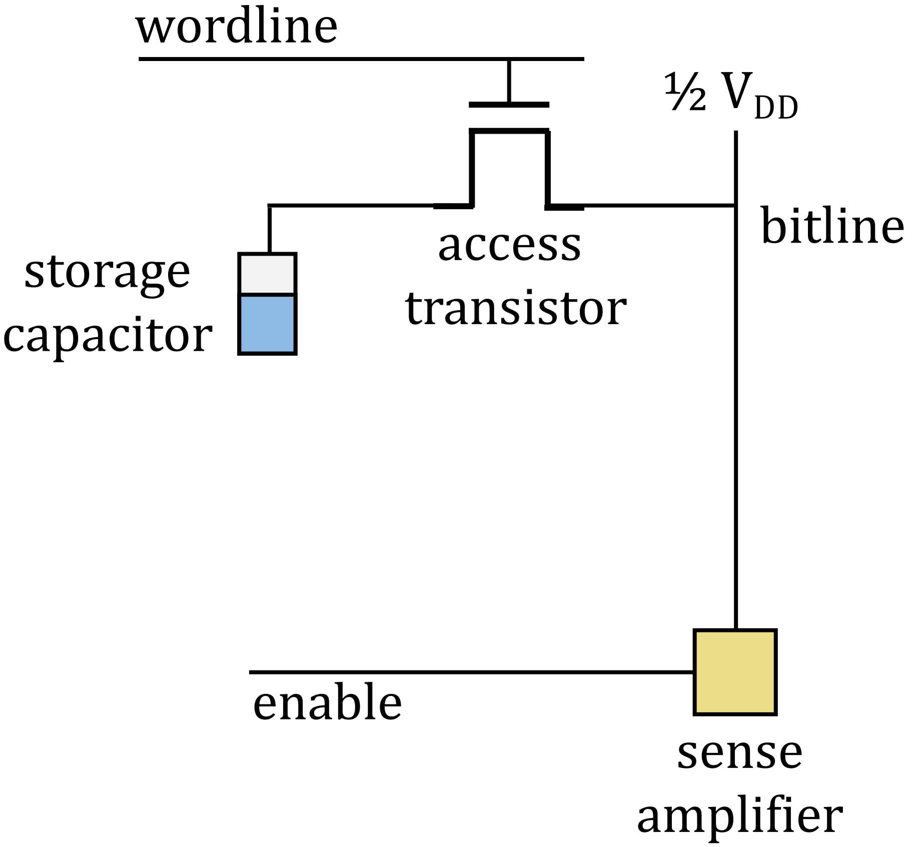
Inside a DRAM Chip



Inside a DRAM Chip: Another View



DRAM Cell Operation

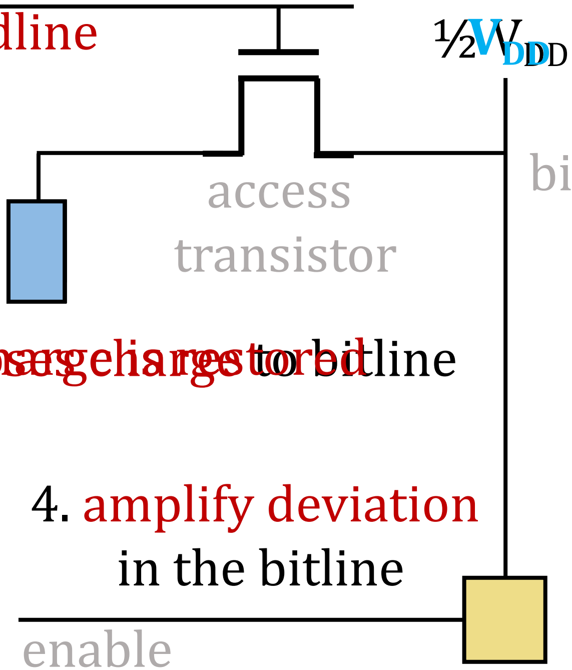


1. ACTIVATE (ACT)

2. READ/WRITE

3. PRECHARGE (PRE)

DRAM Cell Operation (1/3)



wordline

1. raise wordline

$\frac{1}{2}V_{DD}$

$V_{DD} + \delta$

bitline

storage capacitor

access transistor

2. capacitor charge to bitline

5. capacitor charge is restored

4. amplify deviation in the bitline

3. enable sense amplifier

enable

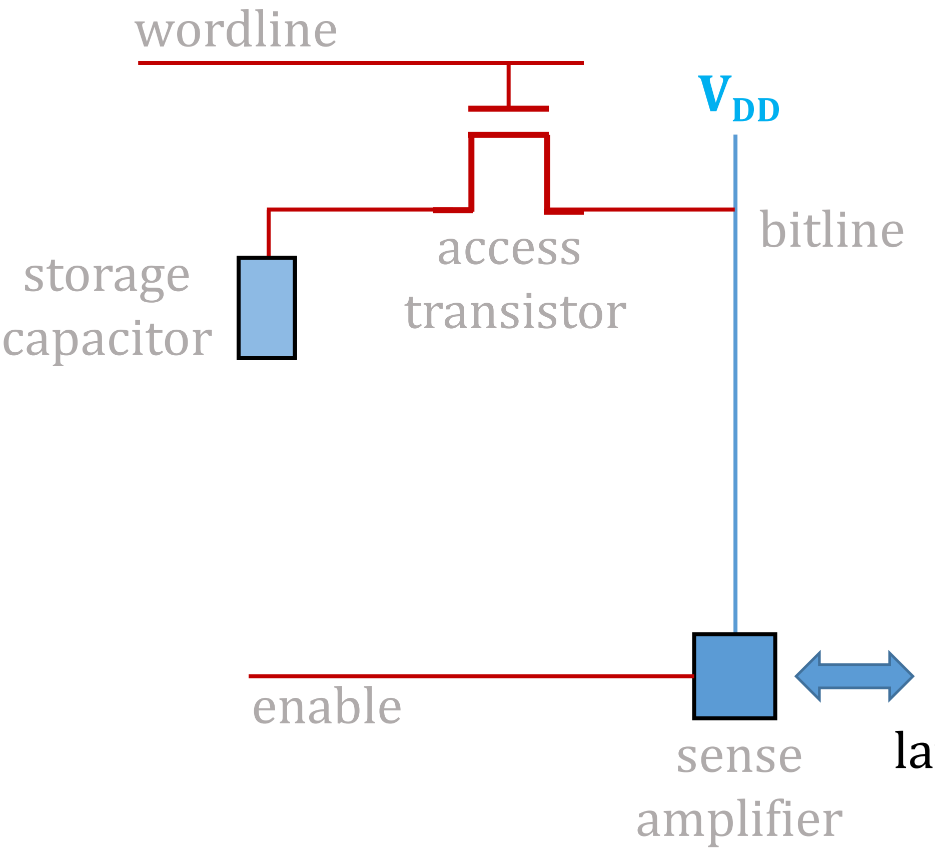
sense amplifier

1. ACTIVATE (ACT)

2. READ/WRITE

3. PRECHARGE (PRE)

DRAM Cell Operation (2/3)



1. ACTIVATE (ACT)

2. READ/WRITE

3. PRECHARGE (PRE)

read/write charge latched in sense amplifier

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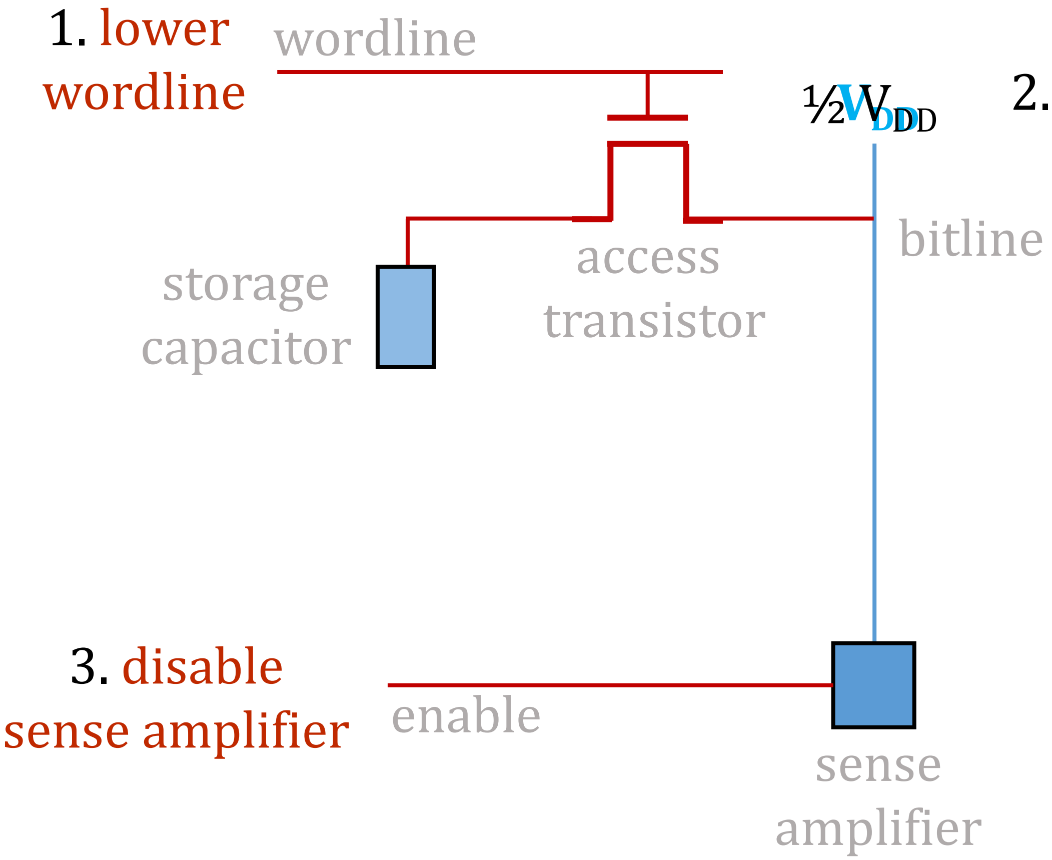
DRAM Cell Operation (3/3)



1. lower wordline

2. precharge bitline for next access

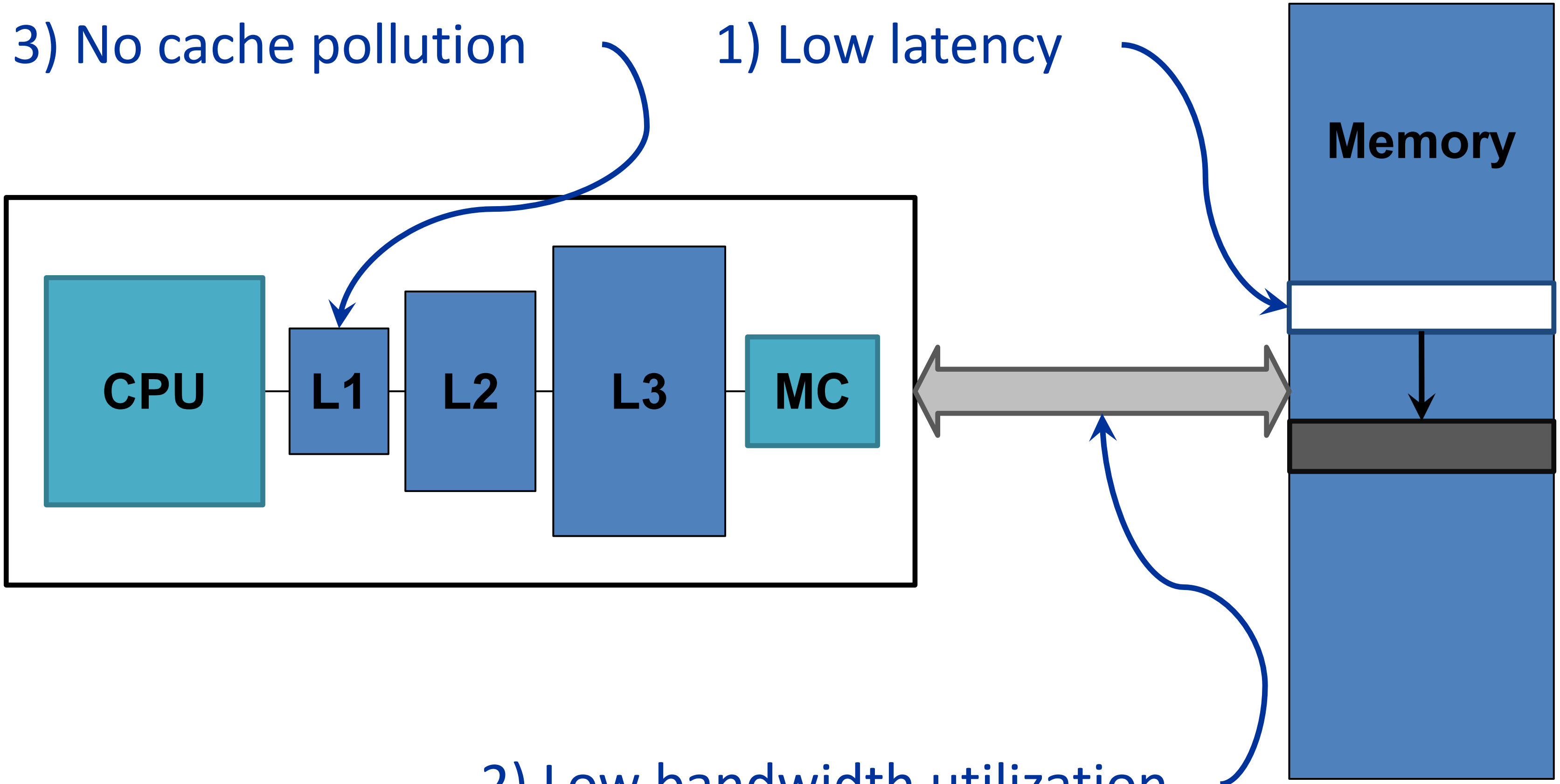
3. disable sense amplifier

1. ACTIVATE (ACT)

2. READ/WRITE

3. PRECHARGE (PRE)

Future Systems: In-Memory Copy



3) No cache pollution

1) Low latency

2) Low bandwidth utilization

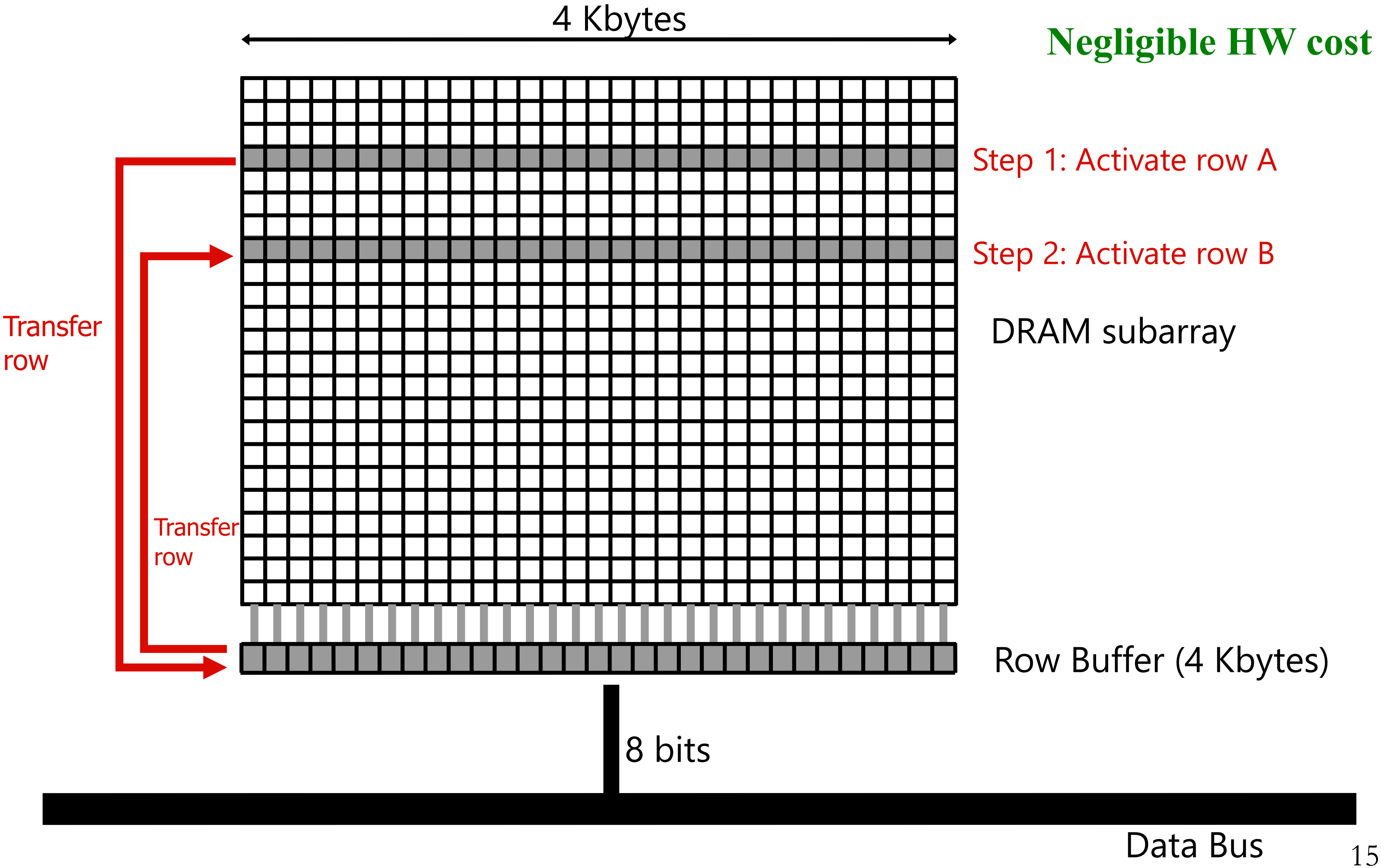
4) No unwanted data movement

1046ns, 3.6uJ → 90ns, 0.04uJ

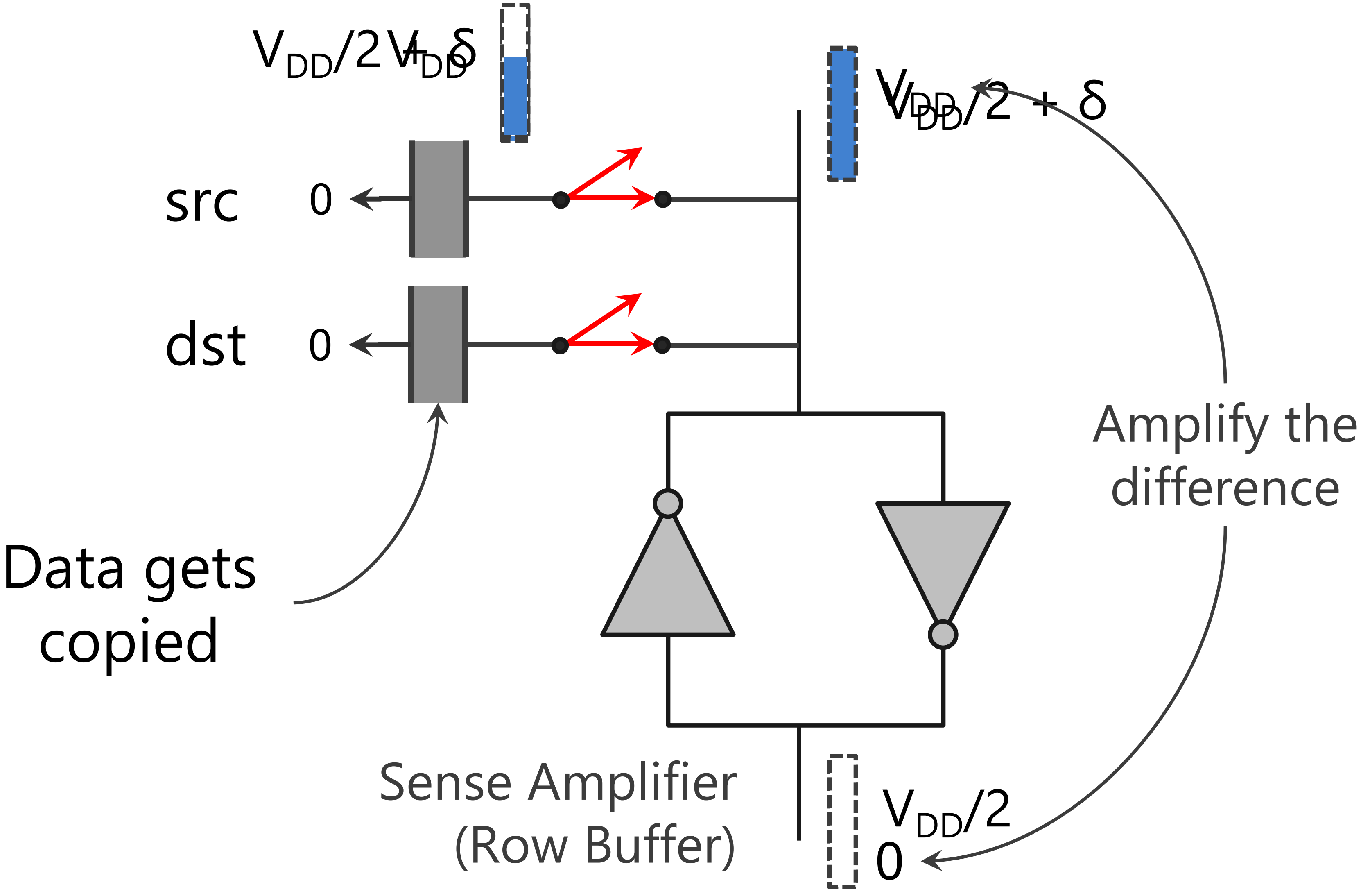
RowClone: In-DRAM Row Copy

Idea: Two consecutive ACTivates

Negligible HW cost



RowClone: Intra-Subarray

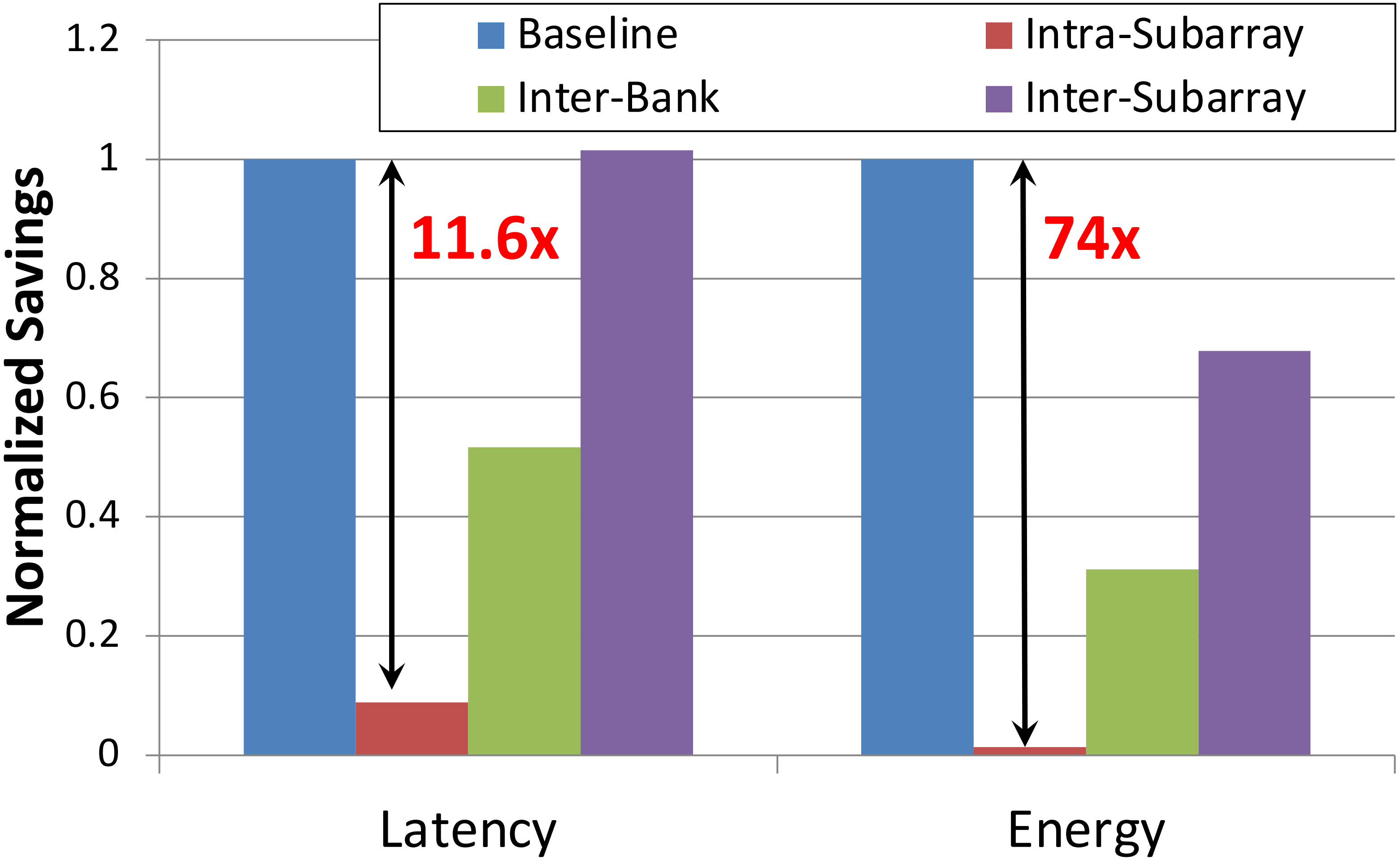


Data gets copied

Amplify the difference

Sense Amplifier (Row Buffer)

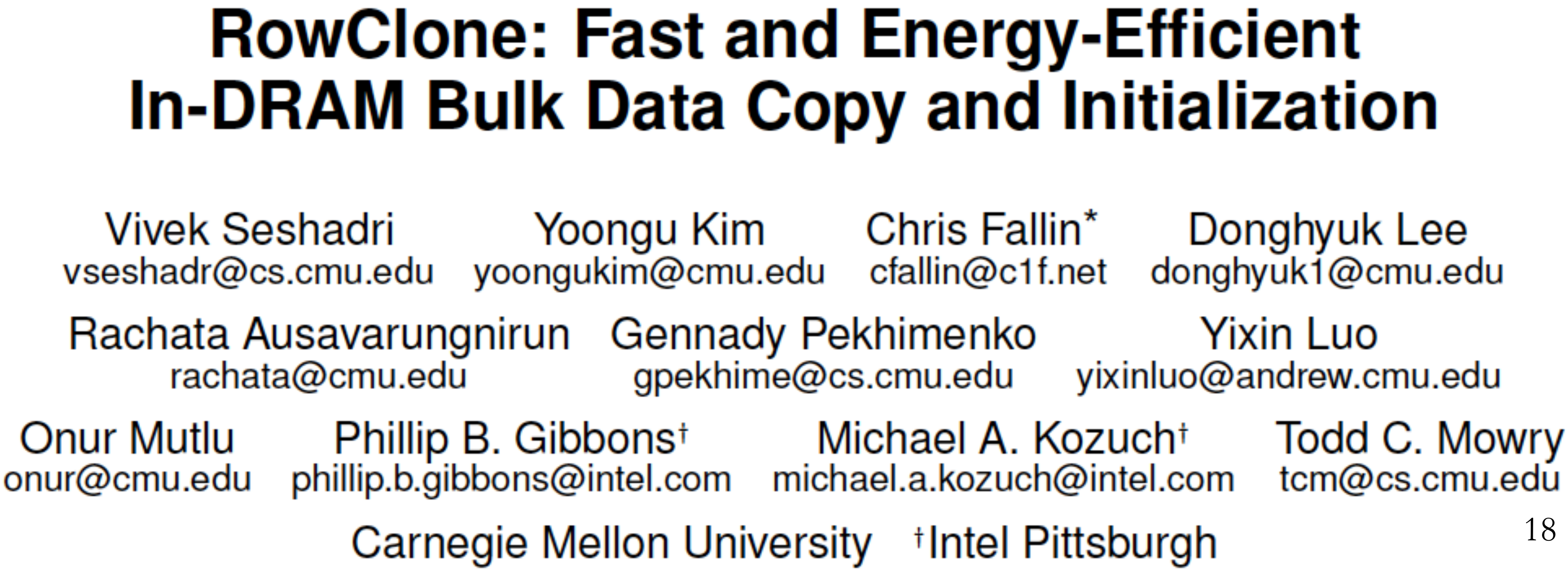
RowClone: Latency and Energy Savings



Seshadri et al., "RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data," MICRO 2013.

More on RowClone

- Vivek Seshadri, Yoongu Kim, Chris Fallin, Donghyuk Lee, Rachata Ausavarungnirun, Gennady Pekhimenko, Yixin Luo, Onur Mutlu, Michael A. Kozuch, Phillip B. Gibbons, and Todd C. Mowry, **"RowClone: Fast and Energy-Efficient In-DRAM Bulk Data Copy and Initialization"** *Proceedings of the 46th International Symposium on Microarchitecture (**MICRO**)*, Davis, CA, December 2013. [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)] [Poster (pptx) (pdf)]



RowClone: Fast and Energy-Efficient In-DRAM Bulk Data Copy and Initialization

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Carnegie Mellon University †Intel Pittsburgh

RowClone Extensions and Follow-Up Work

- Can we do faster inter-subarray copy?
  - Yes, see LISA [Chang et al., HPCA 2016]

- Can we enable data movement at smaller granularities within a bank?
  - Yes, see FIGARO [Wang et al., MICRO 2020]

- Can we do better inter-bank copy?
  - Yes, see Network-on-Memory [CAL 2020]

- Can similar ideas and DRAM properties be used to perform computation on data?
  - Yes, see Ambit [Seshadri et al., CAL 2015, MICRO 2017]

LISA: Increasing Connectivity in DRAM

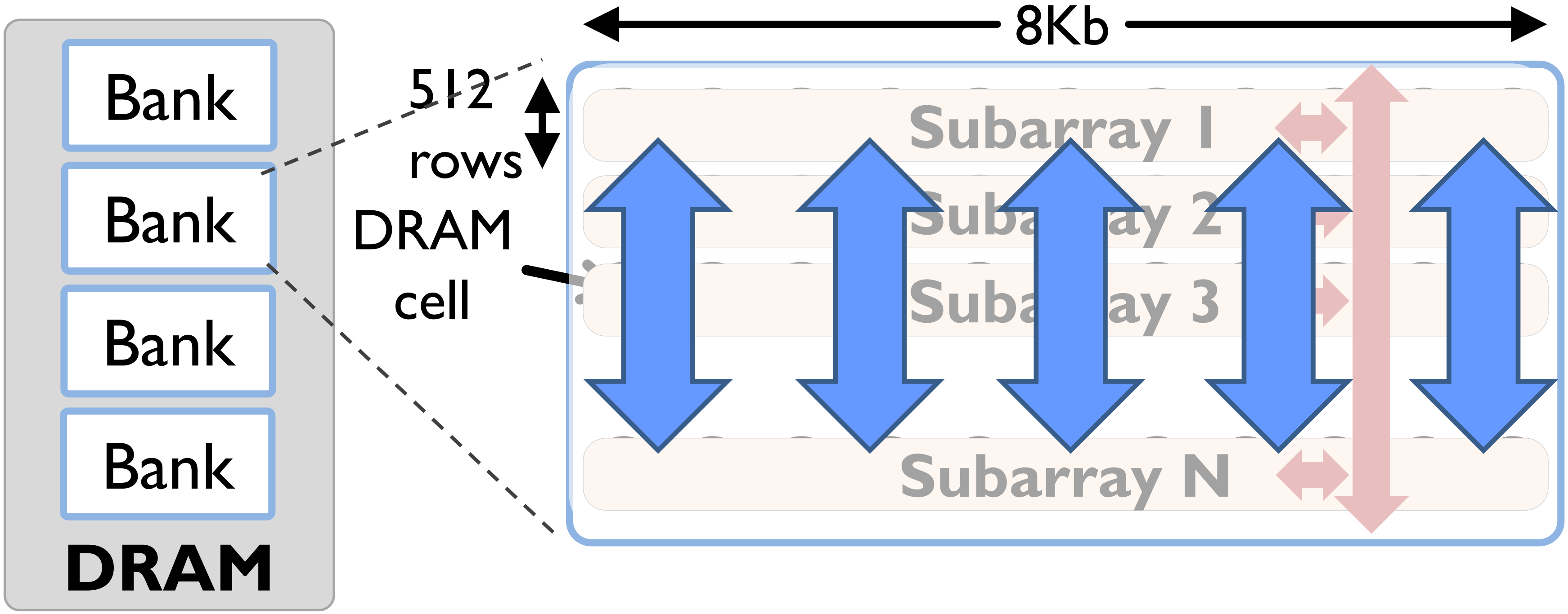
- Kevin K. Chang, Prashant J. Nair, Saugata Ghose, Donghyuk Lee, Moinuddin K. Qureshi, and Onur Mutlu,
"Low-Cost Inter-Linked Subarrays (LISA): Enabling Fast Inter-Subarray Data Movement in DRAM"
Proceedings of the 22nd International Symposium on High-Performance Computer Architecture (***HPCA***), Barcelona, Spain, March 2016.
[Slides (pptx) (pdf)]
[Source Code]

Low-Cost Inter-Linked Subarrays (LISA): Enabling Fast Inter-Subarray Data Movement in DRAM

Kevin K. Chang[†], Prashant J. Nair[*], Donghyuk Lee[†], Saugata Ghose[†], Moinuddin K. Qureshi[*], and Onur Mutlu[†]

[†]*Carnegie Mellon University* [*]*Georgia Institute of Technology*

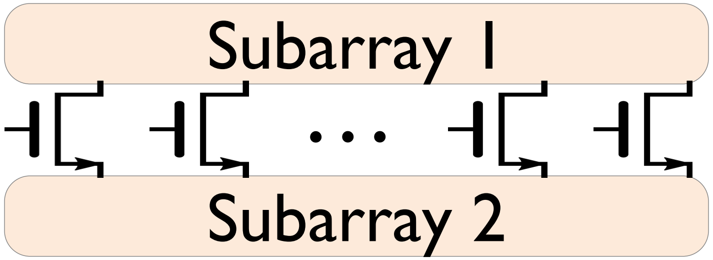
Moving Data Inside DRAM?



Goal: Provide a new substrate to enable wide connectivity between subarrays

Key Idea and Applications

- **Low-cost Inter-linked subarrays (LISA)**
  - Fast bulk data movement between subarrays
  - Wide datapath via isolation transistors: 0.8% DRAM chip area



- LISA is a **versatile substrate** → new applications

Fast bulk data copy: Copy latency 1.363ms→0.148ms (9.2x)
→ 66% speedup, -55% DRAM energy

In-DRAM caching: Hot data access latency 48.7ns→21.5ns (2.2x)
→ 5% speedup

Fast precharge: Precharge latency 13.1ns→5.0ns (2.6x)
→ 8% speedup

More on LISA

- Kevin K. Chang, Prashant J. Nair, Saugata Ghose, Donghyuk Lee, Moinuddin K. Qureshi, and Onur Mutlu,
  "Low-Cost Inter-Linked Subarrays (LISA): Enabling Fast Inter-Subarray Data Movement in DRAM"
  *Proceedings of the 22nd International Symposium on High-Performance Computer Architecture (**HPCA**)*, Barcelona, Spain, March 2016.
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Low-Cost Inter-Linked Subarrays (LISA): Enabling Fast Inter-Subarray Data Movement in DRAM

Kevin K. Chang[†], Prashant J. Nair[*], Donghyuk Lee[†], Saugata Ghose[†], Moinuddin K. Qureshi[*], and Onur Mutlu[†]

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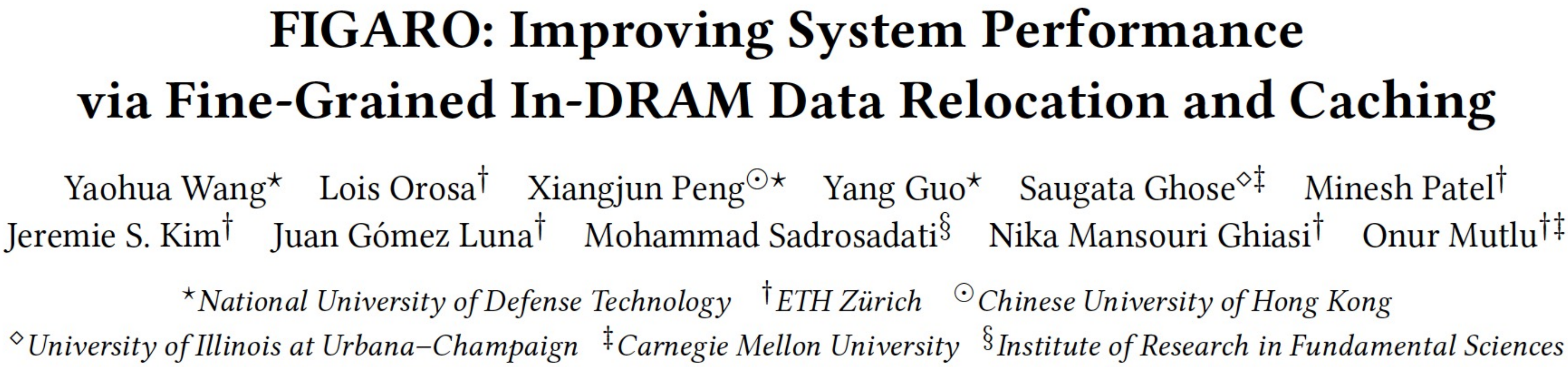
FIGARO: Fine-Grained In-DRAM Copy

- Yaohua Wang, Lois Orosa, Xiangjun Peng, Yang Guo, Saugata Ghose, Minesh Patel, Jeremie S. Kim, Juan Gómez Luna, Mohammad Sadrosadati, Nika Mansouri Ghiasi, and Onur Mutlu, **"FIGARO: Improving System Performance via Fine-Grained In-DRAM Data Relocation and Caching"** *Proceedings of the 53rd International Symposium on Microarchitecture (**MICRO**)*, Virtual, October 2020.



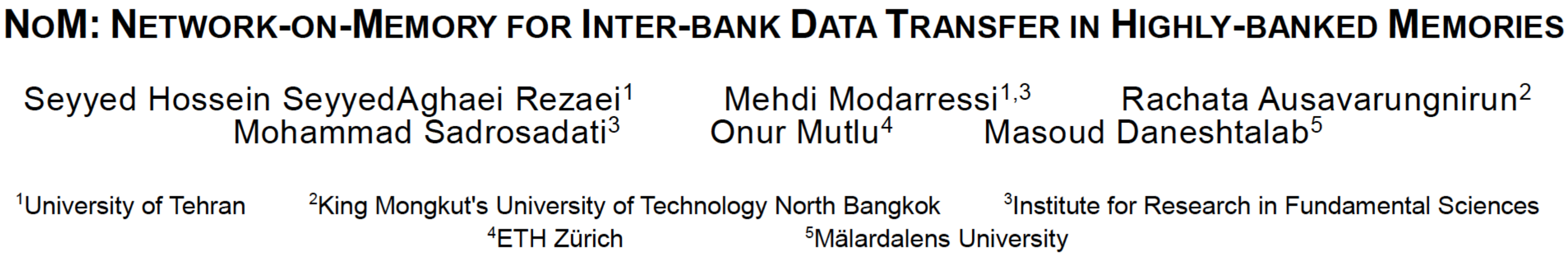
FIGARO: Improving System Performance via Fine-Grained In-DRAM Data Relocation and Caching

Yaohua Wang[⋆] Lois Orosa[†] Xiangjun Peng[⊙⋆] Yang Guo[⋆] Saugata Ghose[◇‡] Minesh Patel[†]
Jeremie S. Kim[†] Juan Gómez Luna[†] Mohammad Sadrosadati[§] Nika Mansouri Ghiasi[†] Onur Mutlu[†‡]

[⋆]*National University of Defense Technology* [†]*ETH Zürich* [⊙]*Chinese University of Hong Kong*
[◇]*University of Illinois at Urbana–Champaign* [‡]*Carnegie Mellon University* [§]*Institute of Research in Fundamental Sciences*

Network-On-Memory: Fast Inter-Bank Copy

- Seyyed Hossein SeyyedAghaei Rezaei, Mehdi Modarressi, Rachata Ausavarungnirun, Mohammad Sadrosadati, Onur Mutlu, and Masoud Daneshtalab,
  "NoM: Network-on-Memory for Inter-Bank Data Transfer in Highly-Banked Memories"
  IEEE Computer Architecture Letters (***CAL***), to appear in 2020.



NoM: Network-on-Memory for Inter-bank Data Transfer in Highly-banked Memories

Seyyed Hossein SeyyedAghaei Rezaei[1] Mehdi Modarressi[1,3] Rachata Ausavarungnirun[2]
Mohammad Sadrosadati[3] Onur Mutlu[4] Masoud Daneshtalab[5]

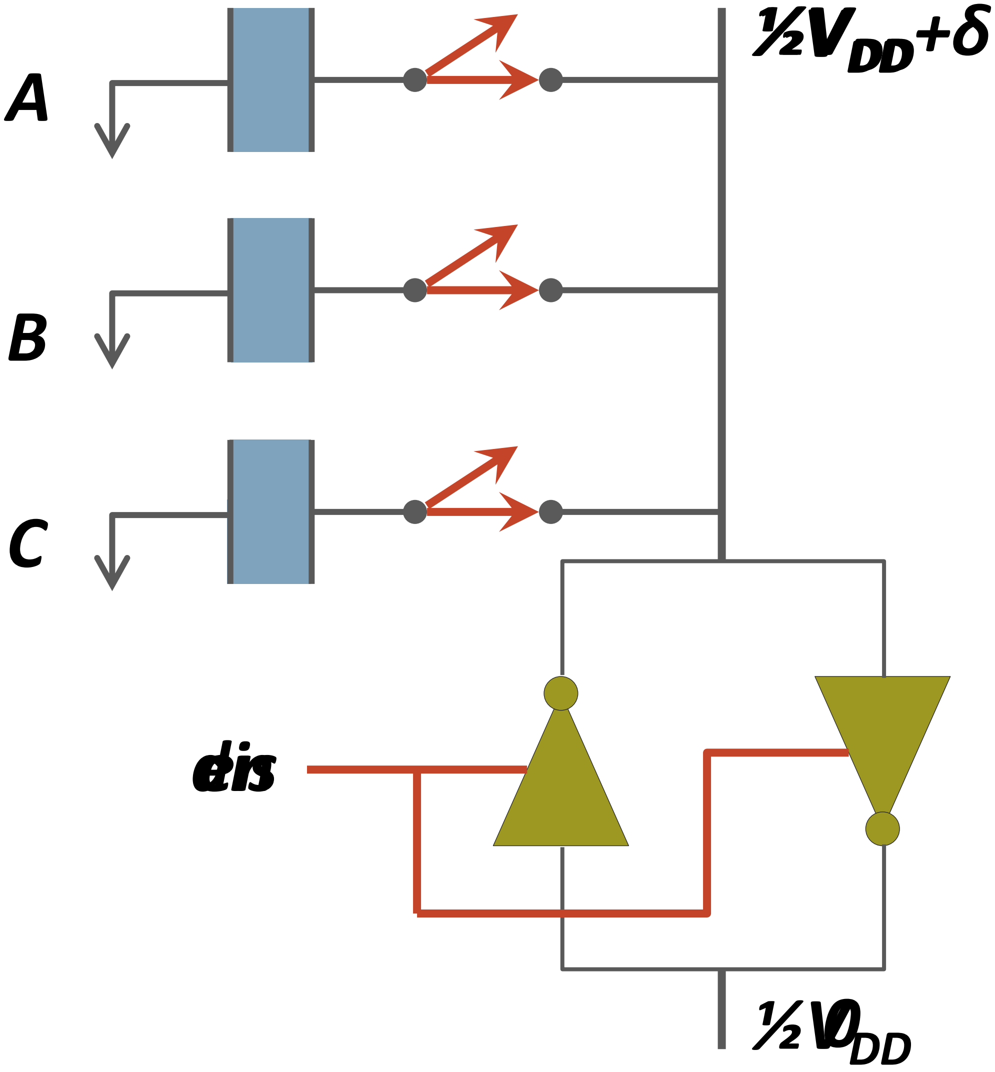
[1]University of Tehran [2]King Mongkut's University of Technology North Bangkok [3]Institute for Research in Fundamental Sciences
[4]ETH Zürich [5]Mälardalens University

(Truly) In-Memory Computation

- We can support in-DRAM AND, OR, NOT, MAJ
- At low cost
- Using analog computation capability of DRAM
  - Idea: activating multiple rows performs computation
- 30-60X performance and energy improvement
  - Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology," MICRO 2017.

- New memory technologies enable even more opportunities
  - Memristors, resistive RAM, phase change mem, STT-MRAM, ...
  - Can operate on data with minimal movement

In-DRAM AND/OR: Triple Row Activation



Final State

AB + BC + AC

C(A + B) + ~C(AB)

Seshadri+, “Fast Bulk Bitwise AND and OR in DRAM”, IEEE CAL 2015.

In-DRAM Bulk Bitwise AND/OR Operation

- BULKAND A, B → C
- Semantics: Perform a bitwise AND of two rows A and B and store the result in row C

- R0 – reserved zero row, R1 – reserved one row
- D1, D2, D3 – Designated rows for triple activation

1. RowClone A into D1
2. RowClone B into D2
3. RowClone R0 into D3
4. ACTIVATE D1,D2,D3
5. RowClone Result into C

More on In-DRAM Bulk AND/OR

- Vivek Seshadri, Kevin Hsieh, Amirali Boroumand, Donghyuk Lee, Michael A. Kozuch, Onur Mutlu, Phillip B. Gibbons, and Todd C. Mowry,
"Fast Bulk Bitwise AND and OR in DRAM"
IEEE Computer Architecture Letters (***CAL***), April 2015.

Fast Bulk Bitwise AND and OR in DRAM

Vivek Seshadri*, Kevin Hsieh*, Amirali Boroumand*, Donghyuk Lee*,
Michael A. Kozuch†, Onur Mutlu*, Phillip B. Gibbons†, Todd C. Mowry*

*Carnegie Mellon University †Intel Pittsburgh

In-DRAM NOT: Dual Contact Cell

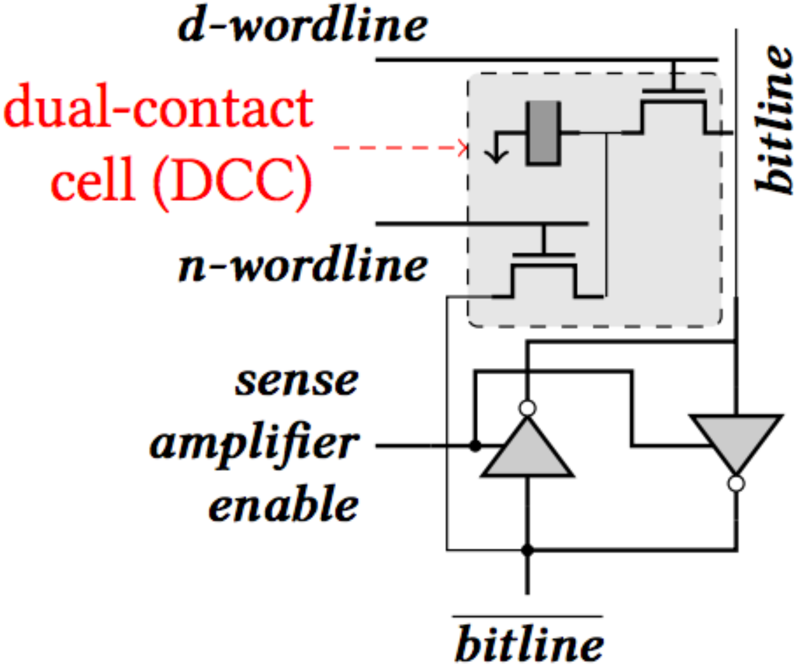


Figure 5: A dual-contact cell connected to both ends of a sense amplifier

Idea:

Feed the negated value in the sense amplifier into a special row

Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

In-DRAM NOT Operation

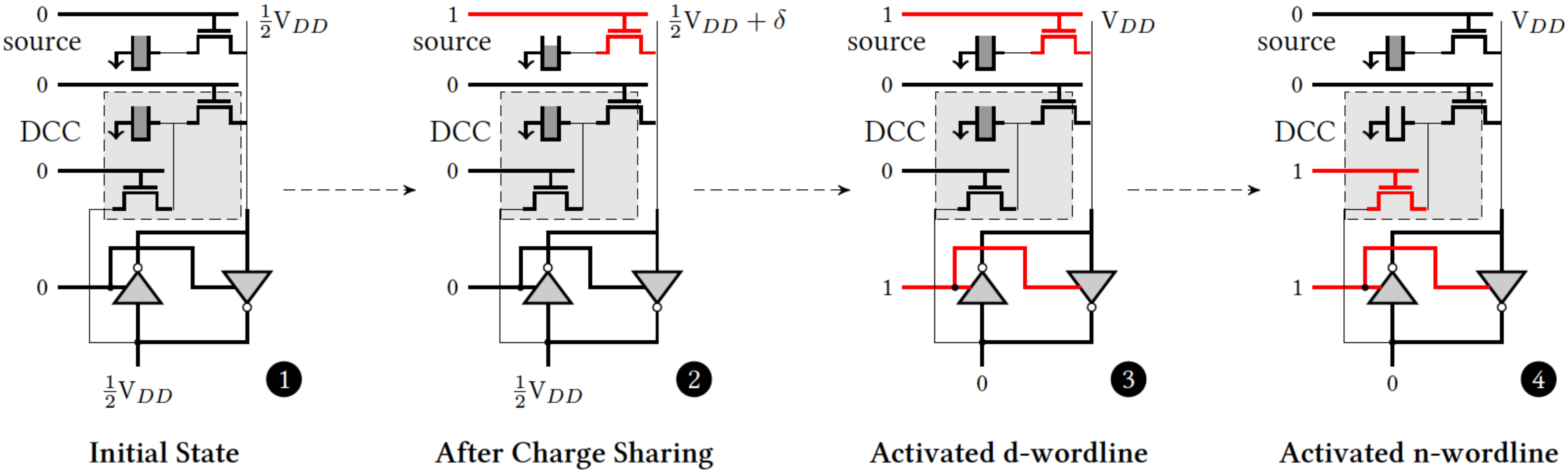


Figure 5: Bitwise NOT using a dual contact capacitor

Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

Performance: In-DRAM Bitwise Operations

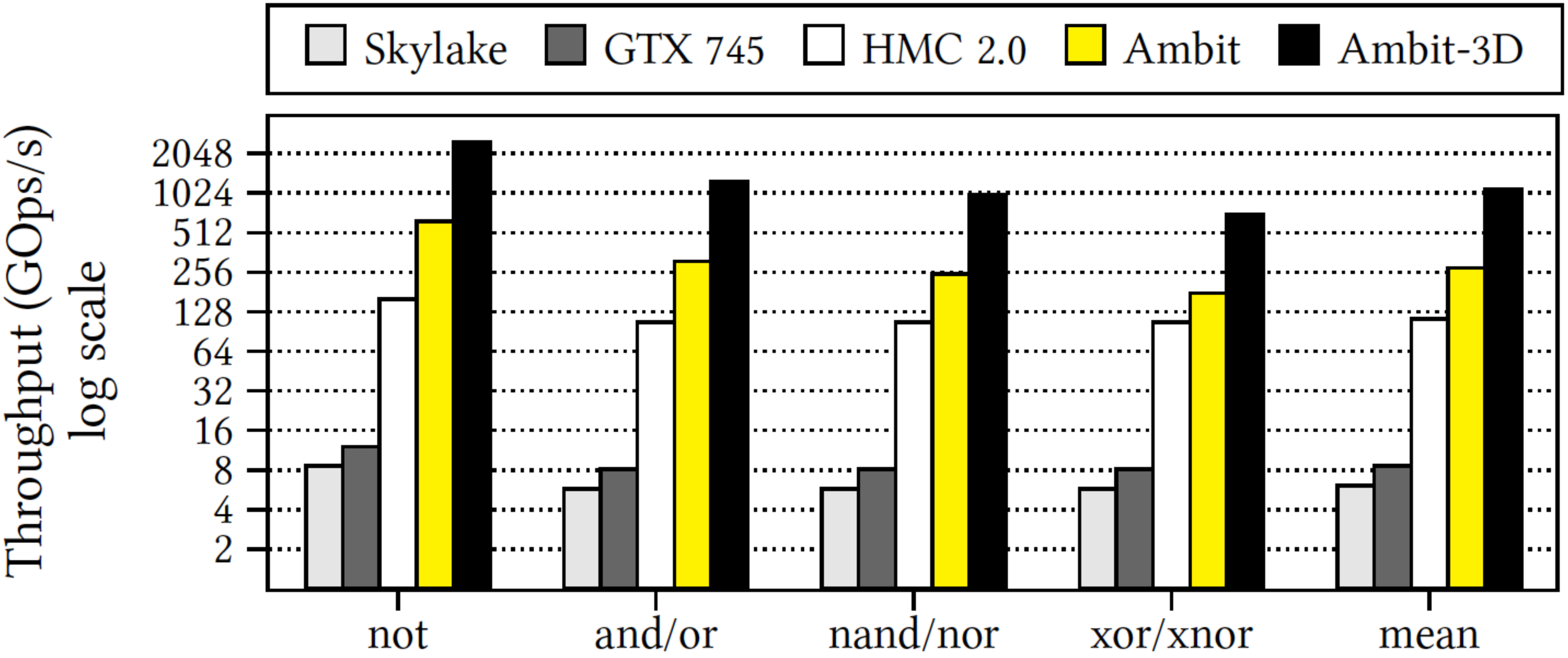
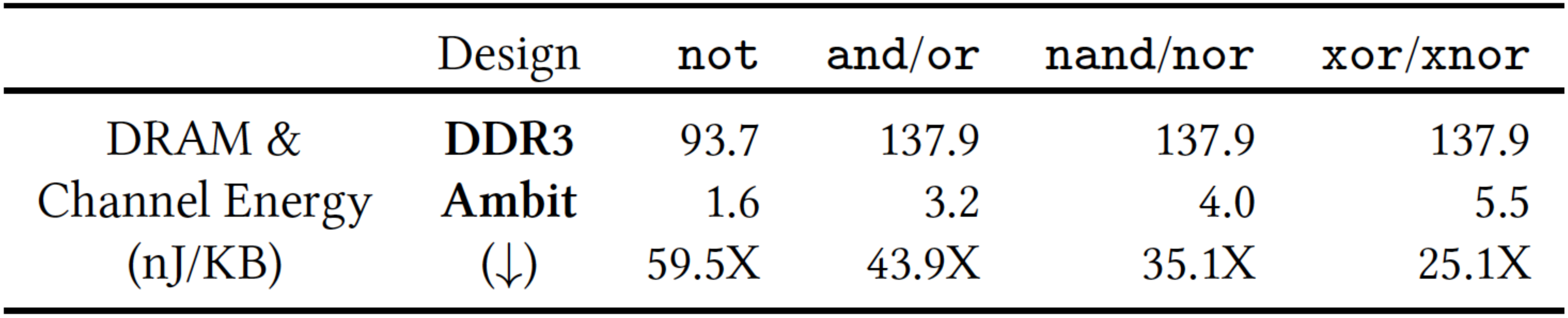


Figure 9: Throughput of bitwise operations on various systems.

Energy of In-DRAM Bitwise Operations

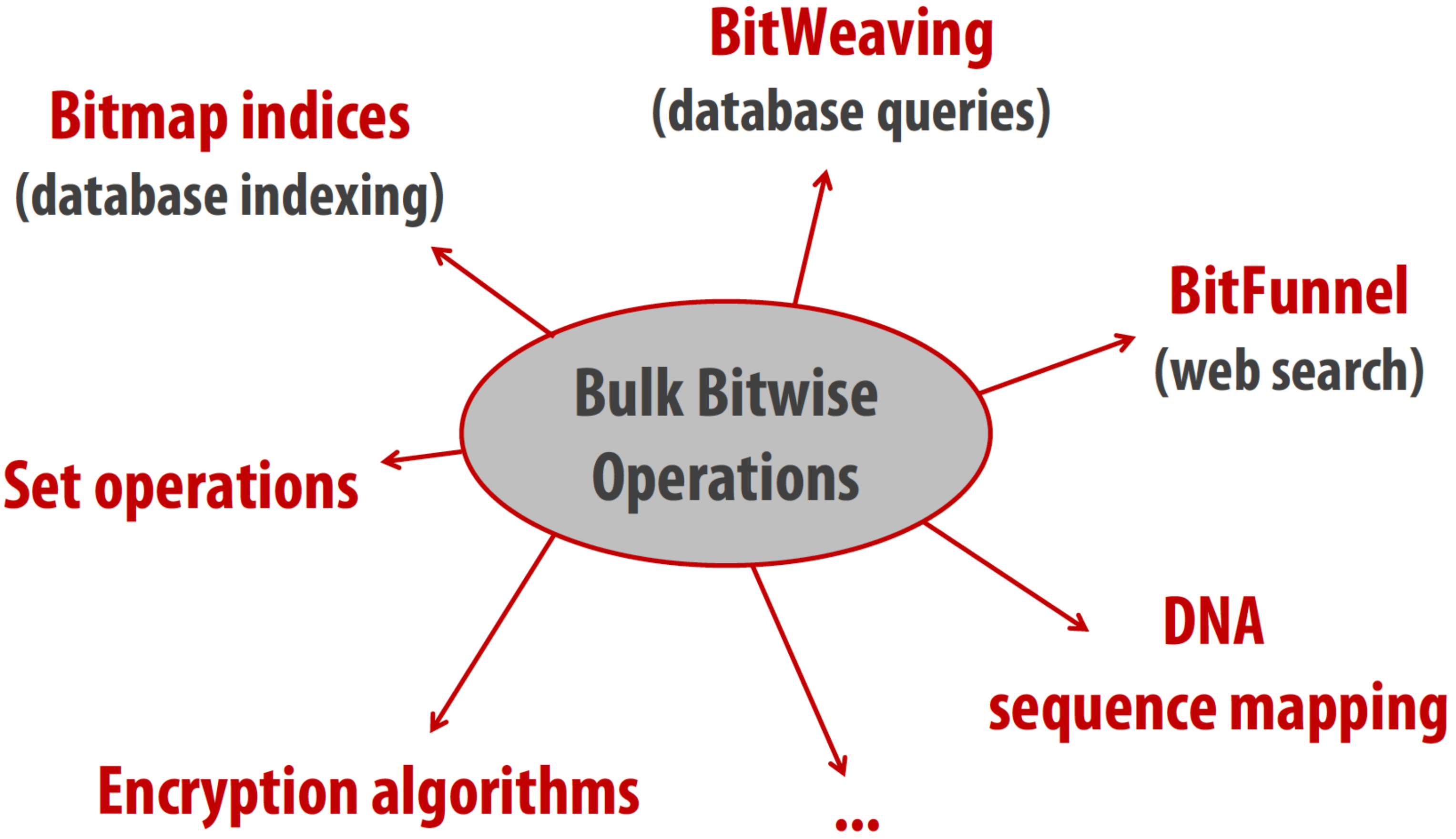


	Design	not	and/or	nand/nor	xor/xnor
DRAM & Channel Energy (nJ/KB)	**DDR3**	93.7	137.9	137.9	137.9
	Ambit	1.6	3.2	4.0	5.5
	(↓)	59.5X	43.9X	35.1X	25.1X

Table 3: Energy of bitwise operations. (↓) indicates energy reduction of Ambit over the traditional DDR3-based design.

Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

Bulk Bitwise Operations in Workloads



Bulk Bitwise Operations

Bitmap indices
(database indexing)

BitWeaving
(database queries)

BitFunnel
(web search)

Set operations

DNA
sequence mapping

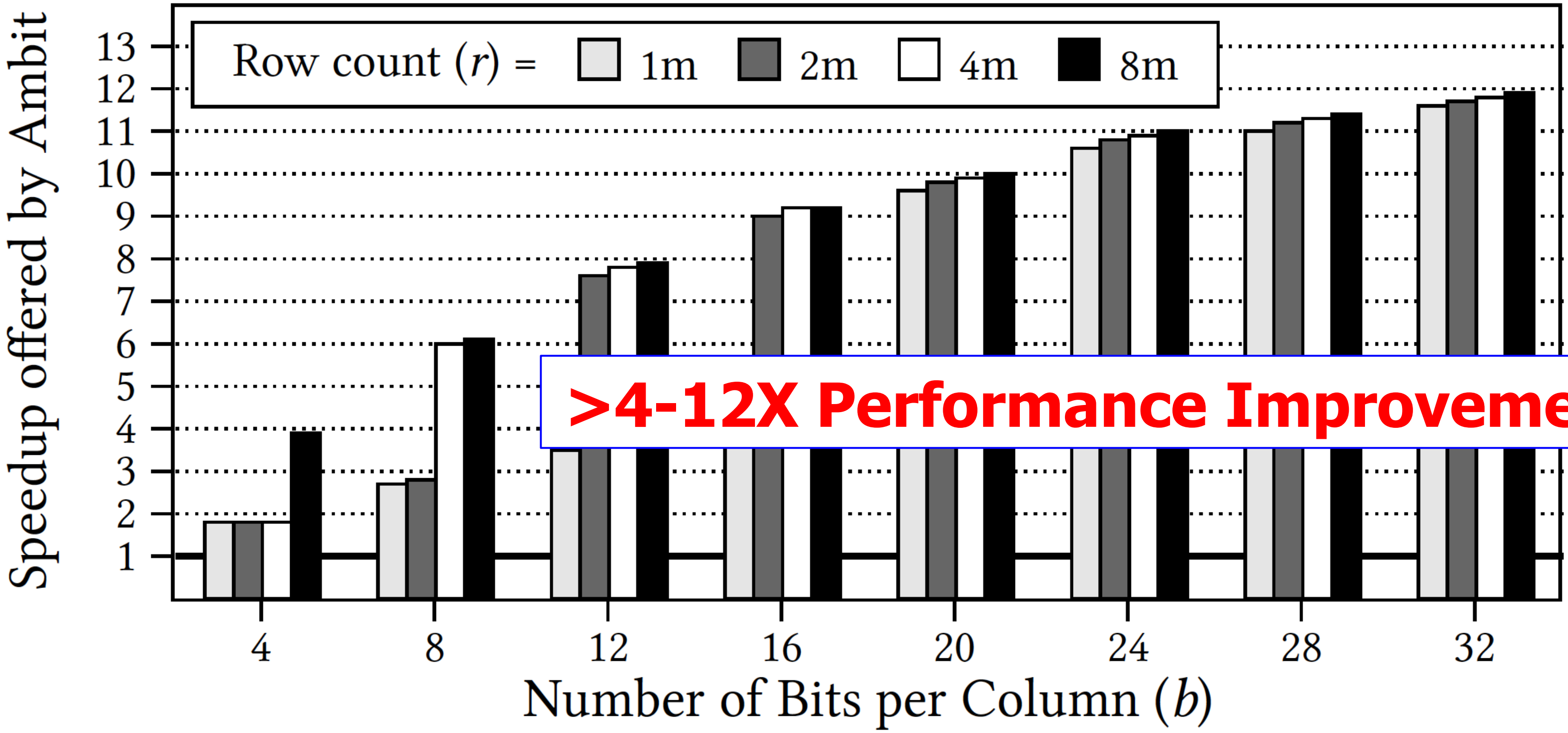
Encryption algorithms

...

[1] Li and Patel, BitWeaving, SIGMOD 2013
[2] Goodwin+, BitFunnel, SIGIR 2017

In-DRAM Acceleration of Database Queries

`‘select count(*) from T where c1 <= val <= c2’`



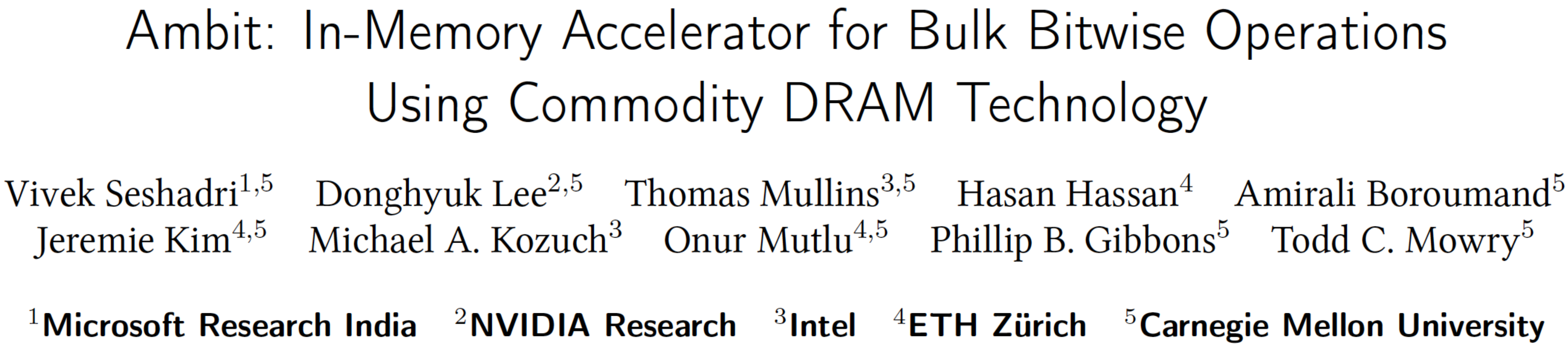
>4-12X Performance Improvement

Figure 11: Speedup offered by Ambit over baseline CPU with SIMD for BitWeaving

Seshadri+, “Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology,” MICRO 2017.

More on Ambit

- Vivek Seshadri, Donghyuk Lee, Thomas Mullins, Hasan Hassan, Amirali Boroumand, Jeremie Kim, Michael A. Kozuch, Onur Mutlu, Phillip B. Gibbons, and Todd C. Mowry,
  "Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology"
  Proceedings of the 50th International Symposium on Microarchitecture (***MICRO***), Boston, MA, USA, October 2017.
  [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)] [Poster (pptx) (pdf)]



Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology

Vivek Seshadri[1,5] Donghyuk Lee[2,5] Thomas Mullins[3,5] Hasan Hassan[4] Amirali Boroumand[5]
Jeremie Kim[4,5] Michael A. Kozuch[3] Onur Mutlu[4,5] Phillip B. Gibbons[5] Todd C. Mowry[5]

[1]Microsoft Research India [2]NVIDIA Research [3]Intel [4]ETH Zürich [5]Carnegie Mellon University

In-DRAM Bulk Bitwise Execution

- Vivek Seshadri and Onur Mutlu,
  "In-DRAM Bulk Bitwise Execution Engine"
  Invited Book Chapter in Advances in Computers, to appear in 2020.
  [Preliminary arXiv version]

In-DRAM Bulk Bitwise Execution Engine

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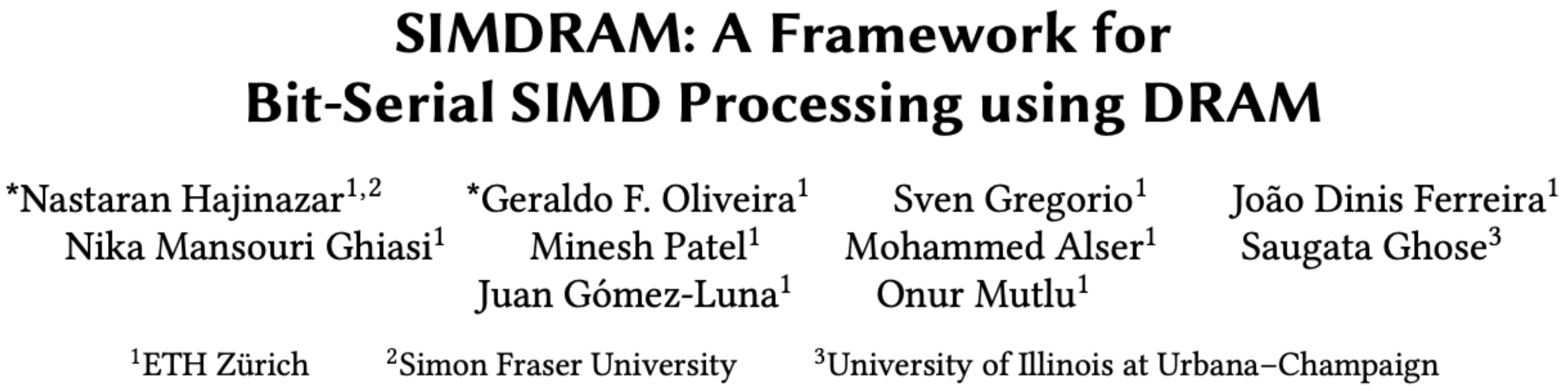
SIMDRAM Framework

- Nastaran Hajinazar, Geraldo F. Oliveira, Sven Gregorio, Joao Dinis Ferreira, Nika Mansouri Ghiasi, Minesh Patel, Mohammed Alser, Saugata Ghose, Juan Gomez-Luna, and Onur Mutlu, **"SIMDRAM: An End-to-End Framework for Bit-Serial SIMD Computing in DRAM"** *Proceedings of the 26th International Conference on Architectural Support for Programming Languages and Operating Systems (**ASPLOS**)*, Virtual, March-April 2021.
[2-page Extended Abstract]
[Short Talk Slides (pptx) (pdf)]
[Talk Slides (pptx) (pdf)]
[Short Talk Video (5 mins)]
[Full Talk Video (27 mins)]

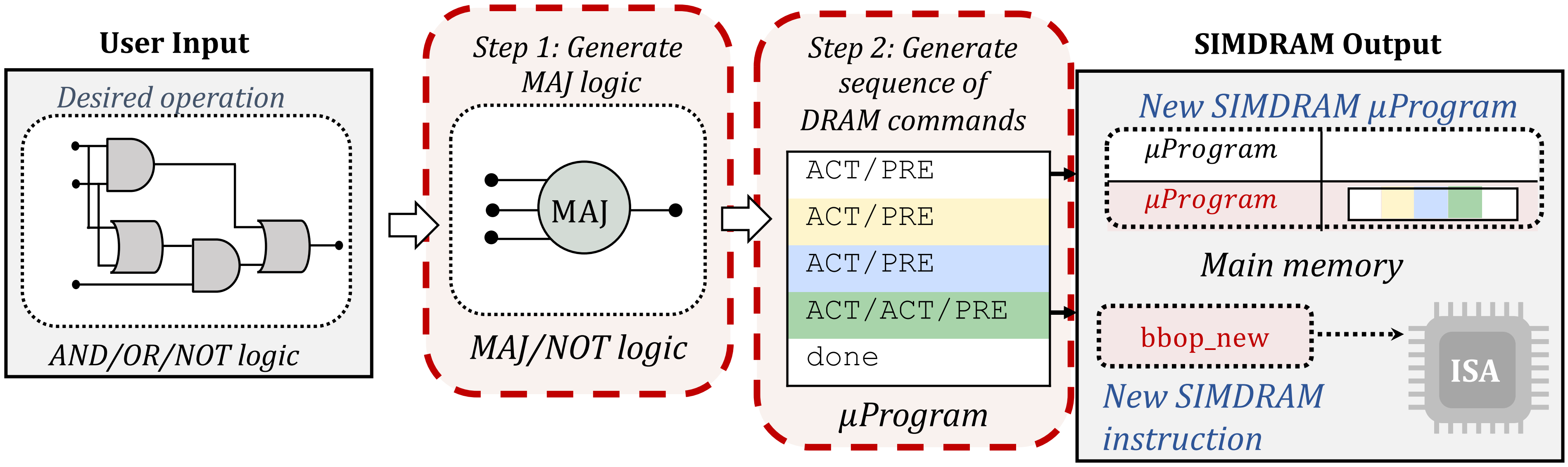


SIMDRAM: A Framework for Bit-Serial SIMD Processing using DRAM

*Nastaran Hajinazar[1,2] *Geraldo F. Oliveira[1] Sven Gregorio[1] João Dinis Ferreira[1]
Nika Mansouri Ghiasi[1] Minesh Patel[1] Mohammed Alser[1] Saugata Ghose[3]
Juan Gómez-Luna[1] Onur Mutlu[1]

[1]ETH Zürich [2]Simon Fraser University [3]University of Illinois at Urbana–Champaign

SIMDRAM Framework: Overview



User Input

Desired operation

AND/OR/NOT logic

Step 1: Generate MAJ logic

MAJ/NOT logic

Step 2: Generate sequence of DRAM commands

ACT/PRE
ACT/PRE
ACT/PRE
ACT/ACT/PRE
done

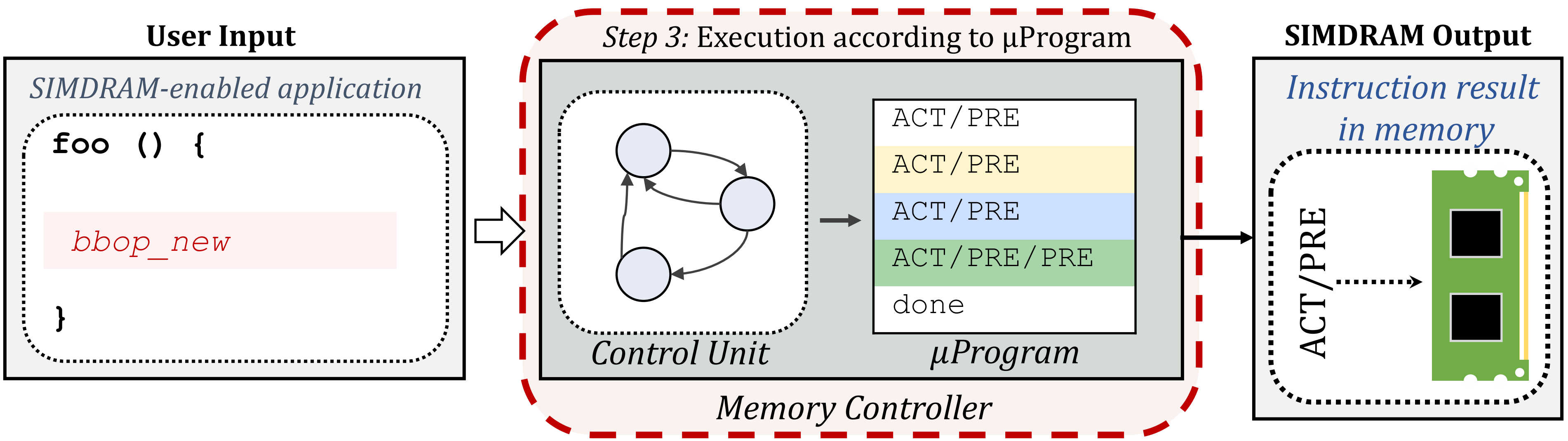
μProgram

SIMDRAM Output

New SIMDRAM μProgram

Main memory

New SIMDRAM instruction



User Input

SIMDRAM-enabled application

```
foo () {

  bbop_new

}
```

Step 3: Execution according to μProgram

ACT/PRE
ACT/PRE
ACT/PRE
ACT/PRE/PRE
done

Control Unit

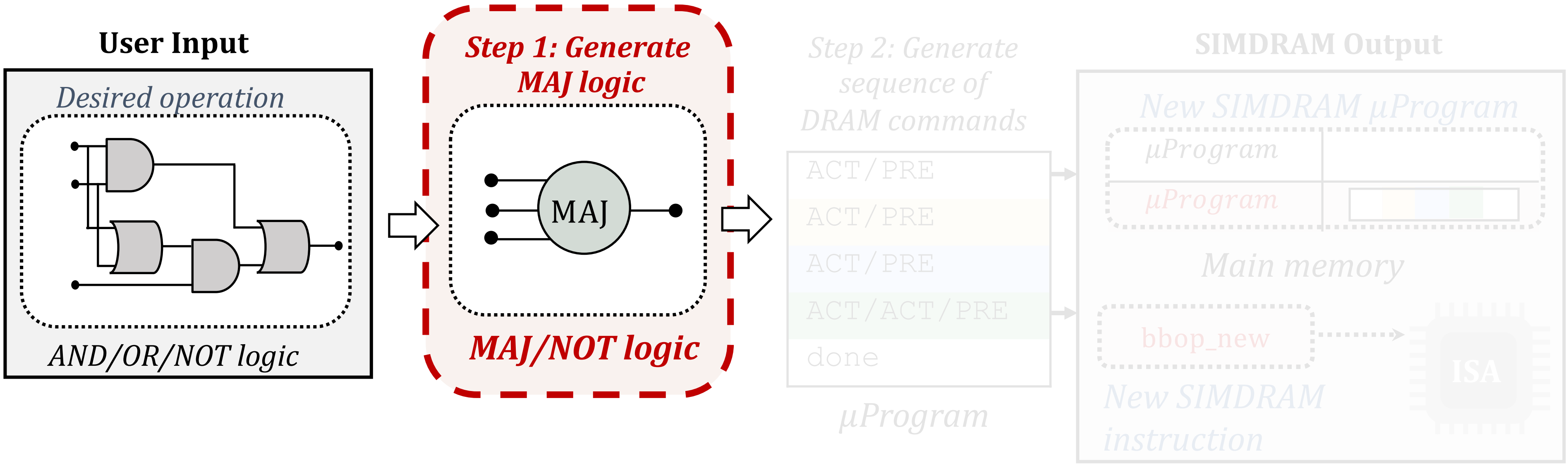
μProgram

Memory Controller

SIMDRAM Output

Instruction result in memory

SIMDRAM Framework: Step 1



User Input

Desired operation

AND/OR/NOT logic

Step 1: Generate MAJ logic

MAJ/NOT logic

Step 2: Generate sequence of DRAM commands

```
ACT/PRE
ACT/PRE
ACT/PRE
ACT/ACT/PRE
done
```

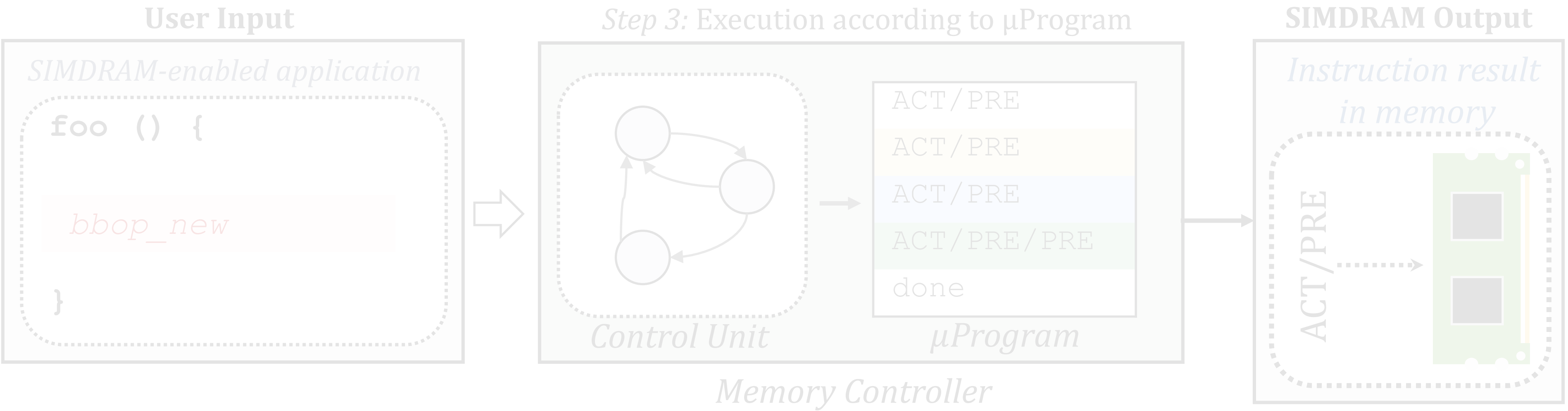
μProgram

SIMDRAM Output

New SIMDRAM μProgram

Main memory

New SIMDRAM instruction



User Input

SIMDRAM-enabled application

```
foo () {

    bbop_new

}
```

Step 3: Execution according to μProgram

```
ACT/PRE
ACT/PRE
ACT/PRE
ACT/PRE/PRE
done
```

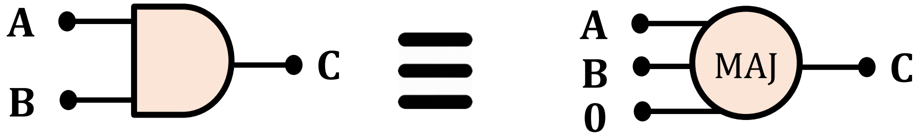
Control Unit *μProgram*

Memory Controller

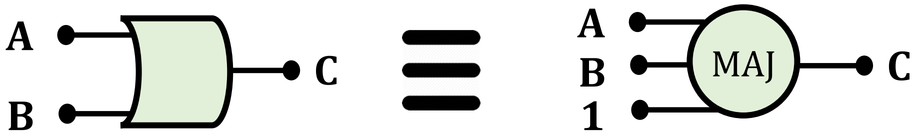
SIMDRAM Output

Instruction result in memory

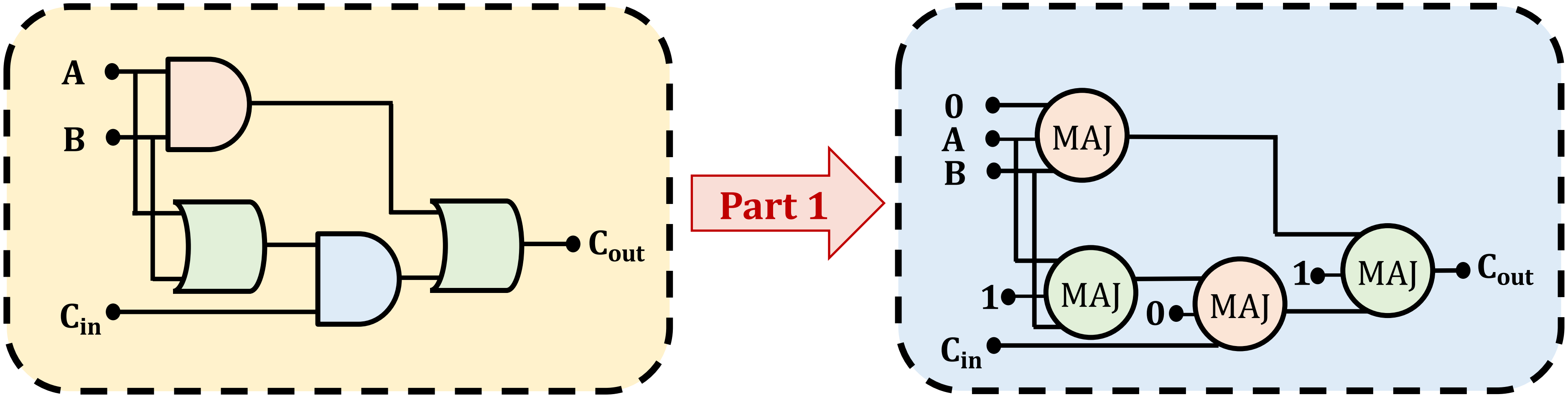
Step 1: Naïve MAJ/NOT Implementation



output is “1” only when A = B = “1”

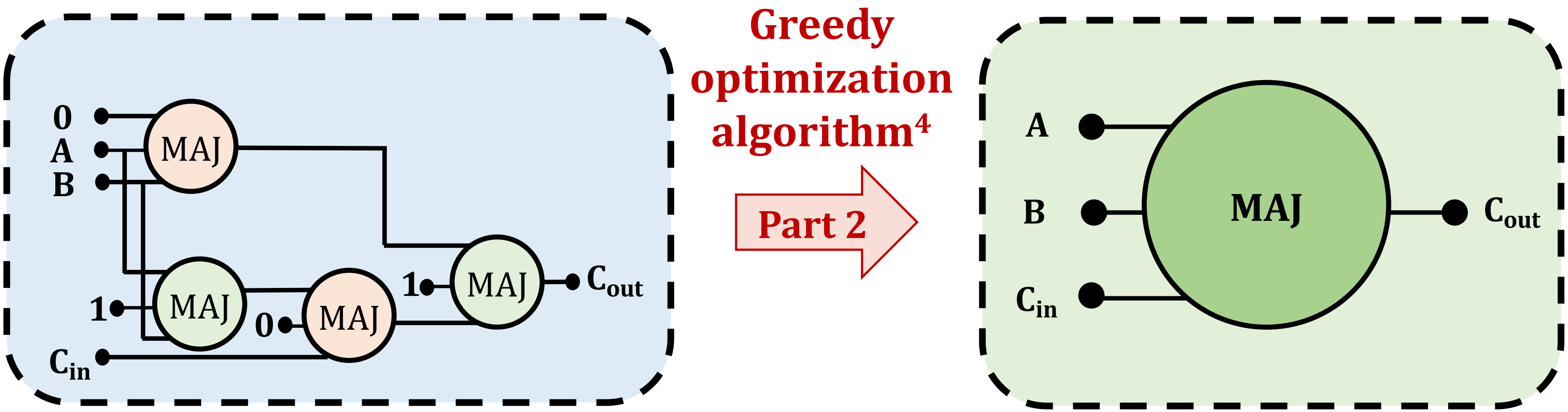


output is “0” only when A = B = “0”



Naïvely converting AND/OR/NOT-implementation to MAJ/NOT-implementation leads to an unoptimized circuit

Step 1: Efficient MAJ/NOT Implementation



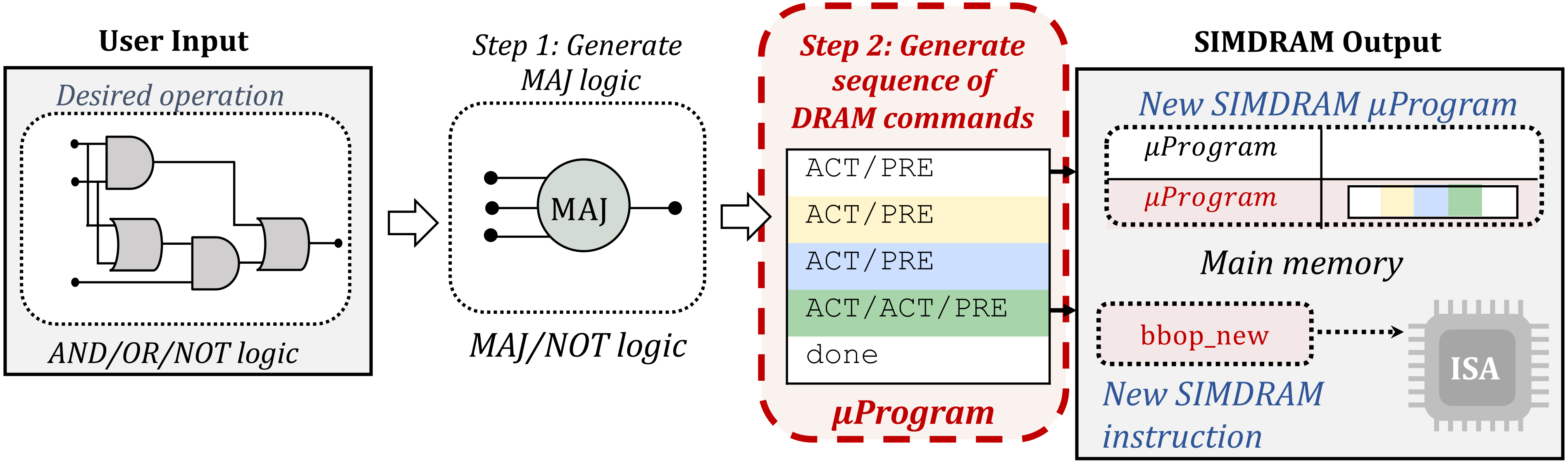
Greedy optimization algorithm[4]

Part 2

Step 1 generates an optimized MAJ/NOT-implementation of the desired operation

[4] L. Amarù et al, "*Majority-Inverter Graph: A Novel Data-Structure and Algorithms for Efficient Logic Optimization*", DAC, 2014.

SIMDRAM Framework: Step 2



User Input

Desired operation

AND/OR/NOT logic

Step 1: Generate MAJ logic

MAJ/NOT logic

Step 2: Generate sequence of DRAM commands

ACT/PRE
ACT/PRE
ACT/PRE
ACT/ACT/PRE
done

μProgram

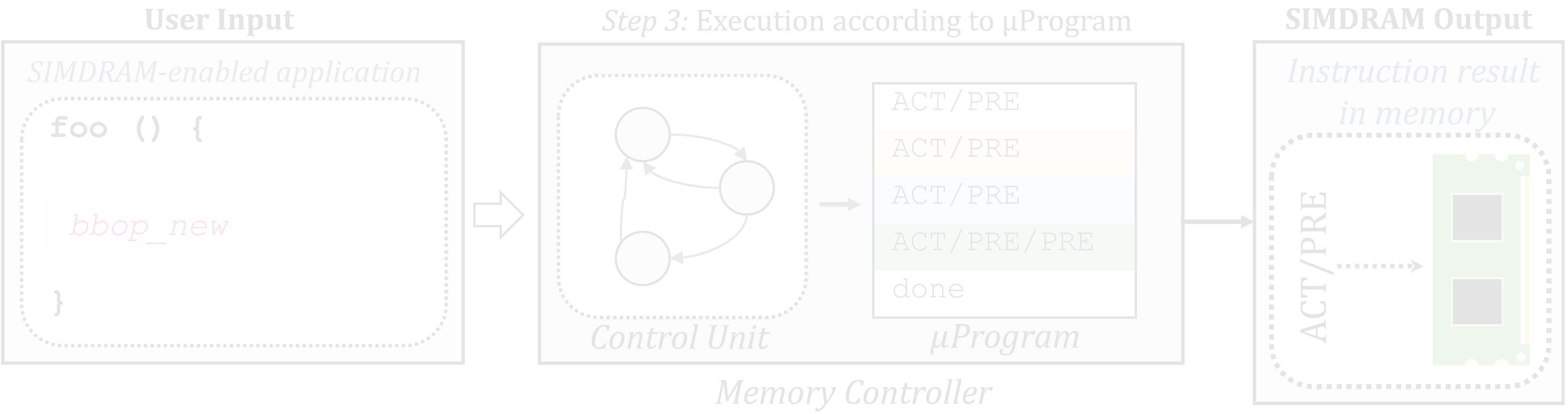
SIMDRAM Output

New SIMDRAM μProgram

Main memory

bbop_new

New SIMDRAM instruction



User Input

SIMDRAM-enabled application

```
foo () {

  bbop_new

}
```

Step 3: Execution according to μProgram

ACT/PRE
ACT/PRE
ACT/PRE
ACT/PRE/PRE
done

Control Unit

μProgram

Memory Controller

SIMDRAM Output

Instruction result in memory

Step 2: μProgram Generation

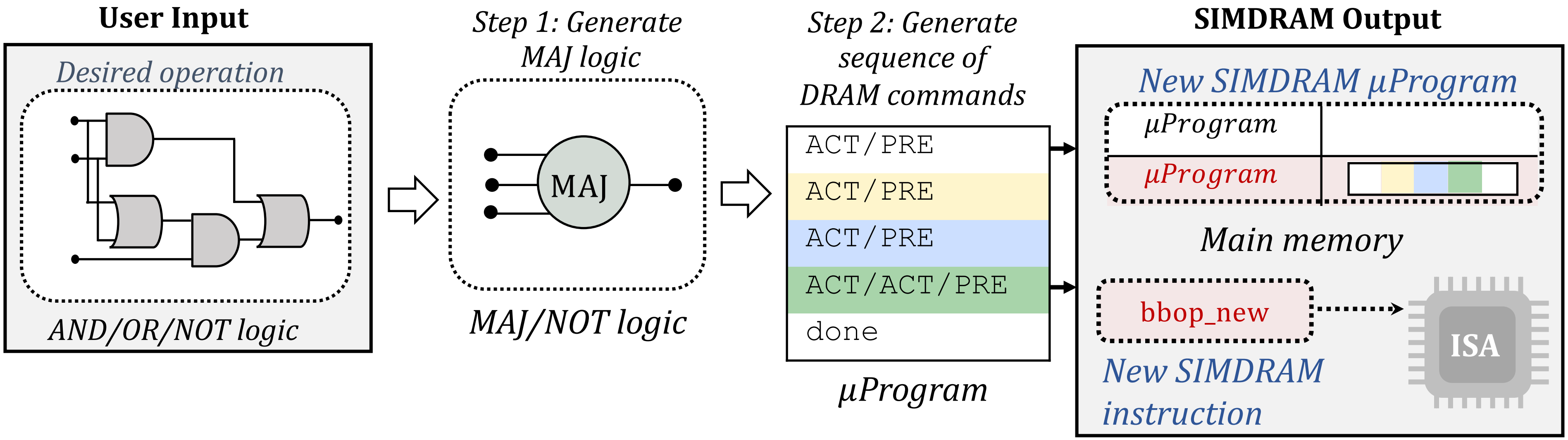
- **μProgram:** A series of microarchitectural operations (e.g., ACT/PRE) that SIMDRAM uses to execute SIMDRAM operation in DRAM

- **Goal of Step 2:** To generate the μProgram that executes the desired SIMDRAM operation in DRAM

Task 1: Allocate DRAM rows to the operands

Task 2: Generate μProgram

SIMDRAM Framework: Step 3



User Input

Desired operation

AND/OR/NOT logic

Step 1: Generate MAJ logic

MAJ

MAJ/NOT logic

Step 2: Generate sequence of DRAM commands

```
ACT/PRE
ACT/PRE
ACT/PRE
ACT/ACT/PRE
done
```

μProgram

SIMDRAM Output

New SIMDRAM μProgram

μProgram

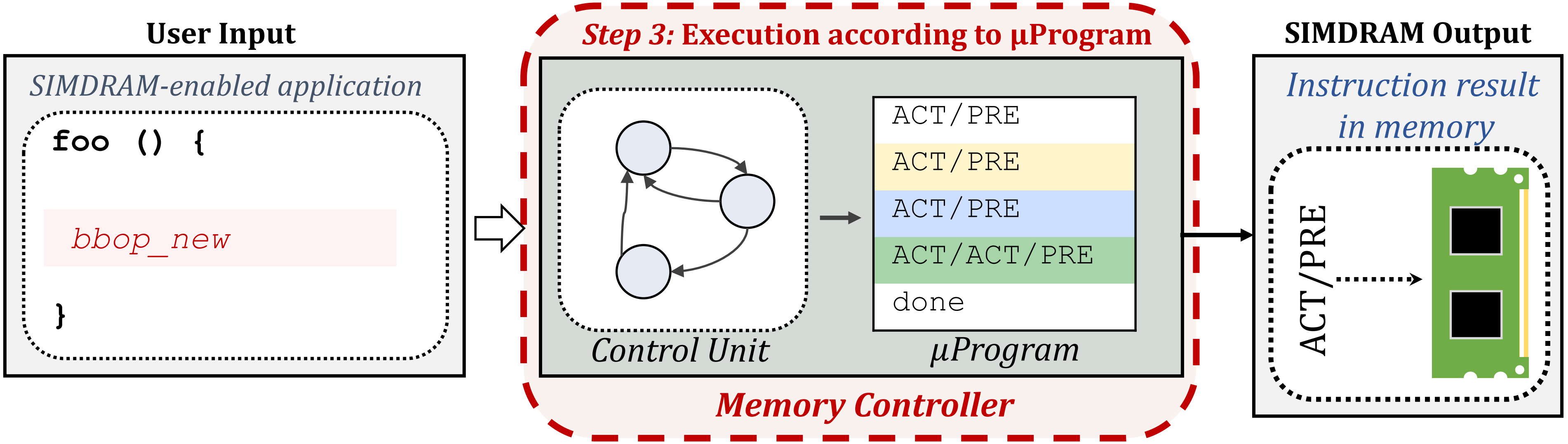
μProgram

Main memory

bbop_new

ISA

New SIMDRAM instruction



User Input

SIMDRAM-enabled application

```
foo () {

  bbop_new

}
```

***Step 3:* Execution according to μProgram**

Control Unit

```
ACT/PRE
ACT/PRE
ACT/PRE
ACT/ACT/PRE
done
```

μProgram

Memory Controller

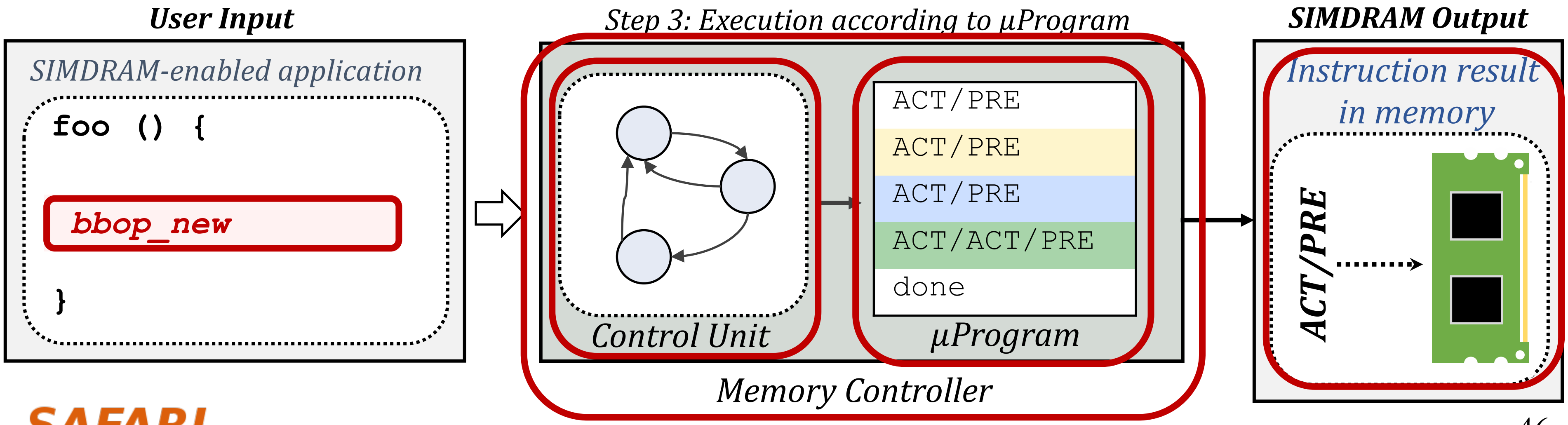
SIMDRAM Output

Instruction result in memory

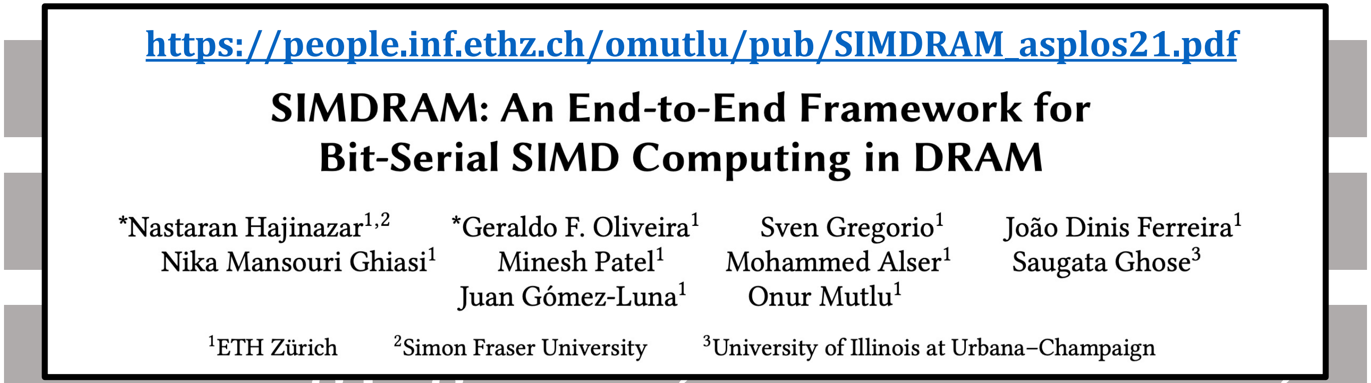
ACT/PRE

Step 3: μProgram Execution

- **SIMDRAM control unit:** handles the execution of the μProgram at runtime
- Upon receiving a **bbop instruction**, the control unit:
  1. Loads the μProgram corresponding to SIMDRAM operation
  2. Issues the sequence of DRAM commands (ACT/PRE) stored in the μProgram to SIMDRAM subarrays to perform the in-DRAM operation



More in the Paper



https://people.inf.ethz.ch/omutlu/pub/SIMDRAM_asplos21.pdf

SIMDRAM: An End-to-End Framework for Bit-Serial SIMD Computing in DRAM

*Nastaran Hajinazar[1,2] *Geraldo F. Oliveira[1] Sven Gregorio[1] João Dinis Ferreira[1]
Nika Mansouri Ghiasi[1] Minesh Patel[1] Mohammed Alser[1] Saugata Ghose[3]
Juan Gómez-Luna[1] Onur Mutlu[1]

[1]ETH Zürich [2]Simon Fraser University [3]University of Illinois at Urbana–Champaign

coherence, and interrupts

Handling limited subarray size

Security implications

Limitations of our framework

SIMDRAM Key Results

Evaluated on:

- 16 complex in-DRAM operations
- 7 commonly-used real-world applications

SIMDRAM provides:

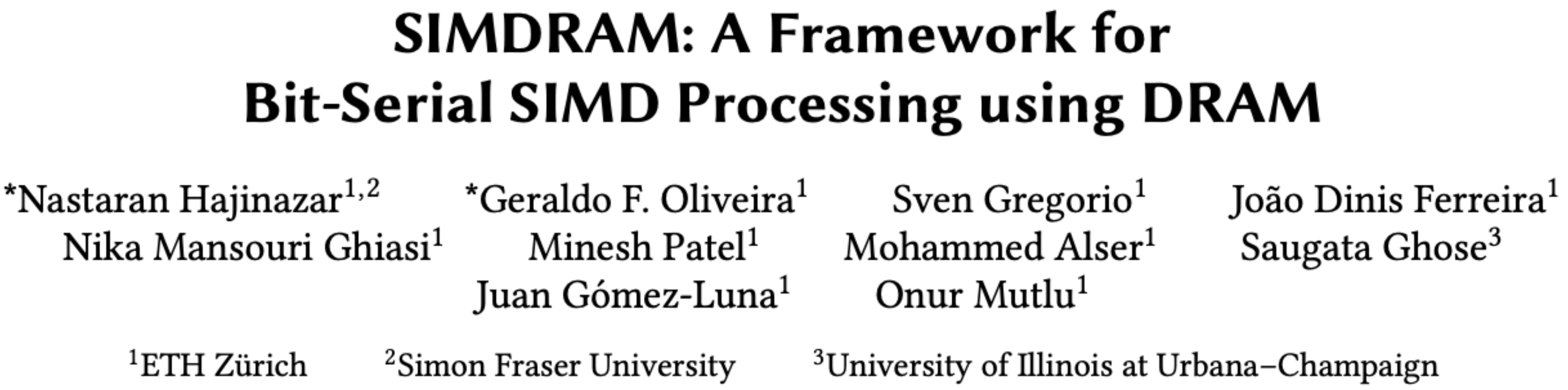
- **88×** and **5.8×** the **throughput** of a **CPU** and a **high-end GPU**, respectively, over **16 operations**

- **257×** and **31×** the **energy efficiency** of a **CPU** and a **high-end GPU**, respectively, over **16 operations**

- **21×** and **2.1×** the **performance** of a **CPU** an a **high-end GPU**, over **seven real-world applications**

More on SIMDRAM

- Nastaran Hajinazar, Geraldo F. Oliveira, Sven Gregorio, Joao Dinis Ferreira, Nika Mansouri Ghiasi, Minesh Patel, Mohammed Alser, Saugata Ghose, Juan Gomez-Luna, and Onur Mutlu, **"SIMDRAM: An End-to-End Framework for Bit-Serial SIMD Computing in DRAM"** *Proceedings of the 26th International Conference on Architectural Support for Programming Languages and Operating Systems* (***ASPLOS***), Virtual, March-April 2021.
[2-page Extended Abstract]
[Short Talk Slides (pptx) (pdf)]
[Talk Slides (pptx) (pdf)]
[Short Talk Video (5 mins)]
[Full Talk Video (27 mins)]



SIMDRAM: A Framework for Bit-Serial SIMD Processing using DRAM

*Nastaran Hajinazar[1,2] *Geraldo F. Oliveira[1] Sven Gregorio[1] João Dinis Ferreira[1]
Nika Mansouri Ghiasi[1] Minesh Patel[1] Mohammed Alser[1] Saugata Ghose[3]
Juan Gómez-Luna[1] Onur Mutlu[1]

[1]ETH Zürich [2]Simon Fraser University [3]University of Illinois at Urbana–Champaign

SIMDRAM: Follow-Ups

- Limitations of current substrate?
  - Computing granularity
  - Data layout conversion
  - High-latency bit-serial operations
  - Assembly-like programming model
  - Application scope
  - …

- We are working on even better processing-using-memory substrates
  - One step at a time!

Limitations of PUD Systems: Overview

PUD systems suffer from three sources of inefficiency due to the large and rigid DRAM access granularity

1 SIMD Underutilization

- due to data parallelism variation within and across applications
- leads to throughput and energy waste

2 Limited Computation Support

- due to a lack of low-cost interconnects across columns
- limits PUD operations to only parallel map constructs

3 Challenging Programming Model

- due to a lack of compiler support for PUD systems
- creates a burden on programmers, limiting PUD adoption

Problem & Goal

Problem

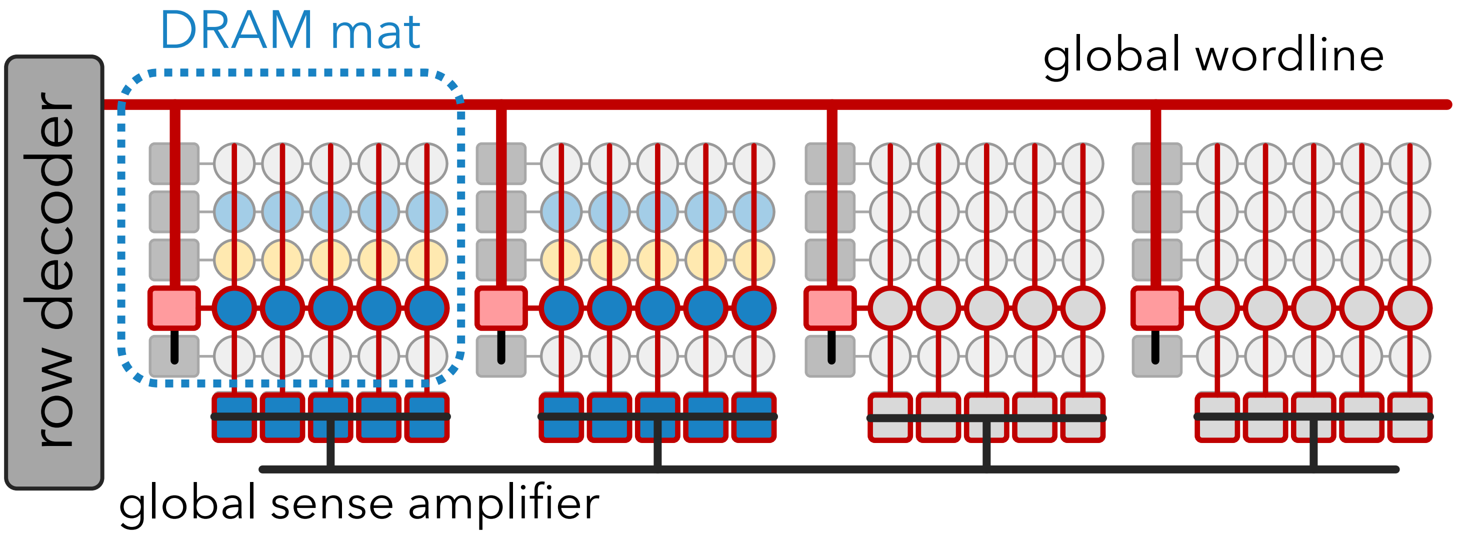
Processing-Using-DRAM's large and rigid granularity limits its applicability and efficiency for different applications

Goal

Design a flexible PUD system that overcomes the three limitations caused by large and rigid DRAM access granularity

MIMDRAM:
Key Idea (I)

DRAM's hierarchical organization can enable
fine-grained access



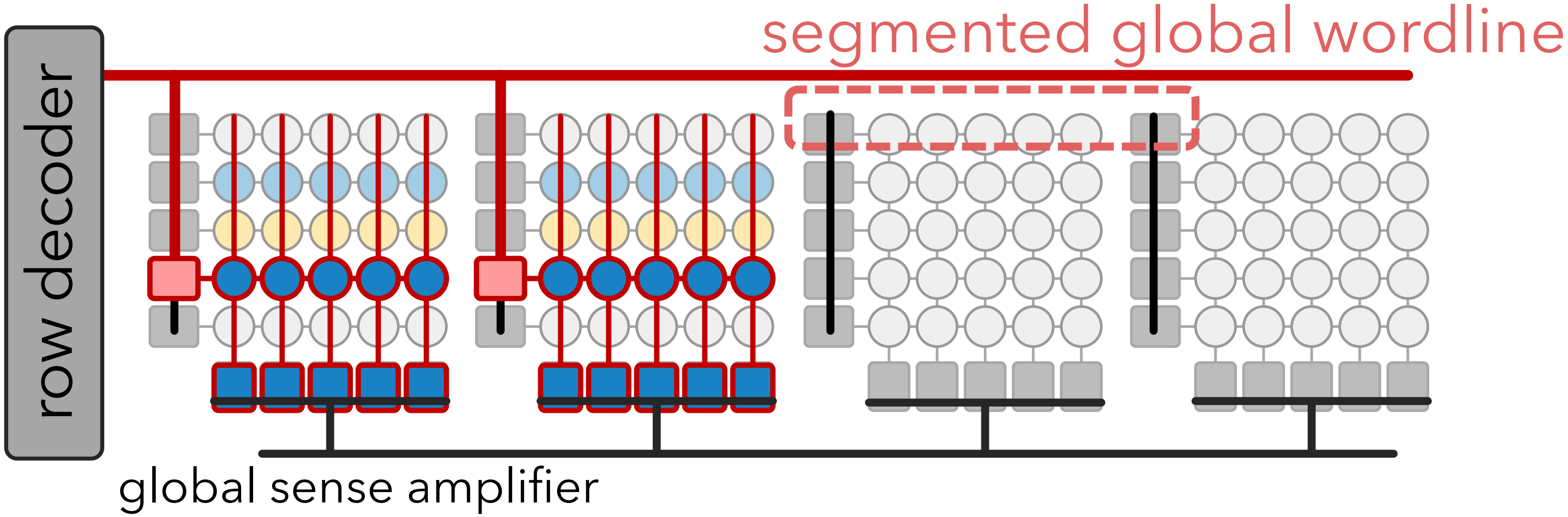
Key Issue:
on a DRAM access, the global wordline propagates across all DRAM mats

Fine-Grained DRAM:
segments the global wordline to access individual DRAM mats

SAFARI

MIMDRAM:
Key Idea (II)

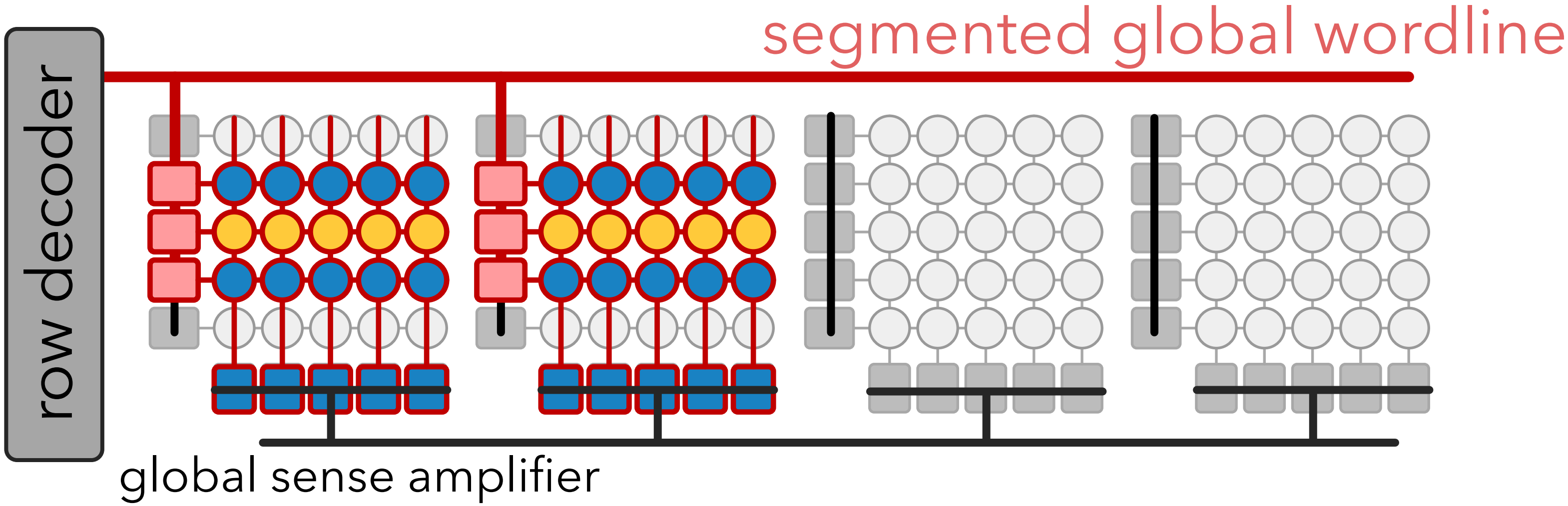
Fine-Grained DRAM:
segments the global wordline to access individual DRAM mats



Fine-grained DRAM for energy-efficient DRAM access:

[Cooper-Balis+, 2010]: Fine-Grained Activation for Power Reduction in DRAM
[Udipi+, 2010]: Rethinking DRAM Design and Organization for Energy-Constrained Multi-Cores
[Zhang+, 2014]: Half-DRAM
[Ha+, 2016]: Improving Energy Efficiency of DRAM by Exploiting Half Page Row Access
[O'Connor+, 2017]: Fine-Grained DRAM
[Olgun+, 2024]: Sectored DRAM

MIMDRAM:
Key Idea (III)

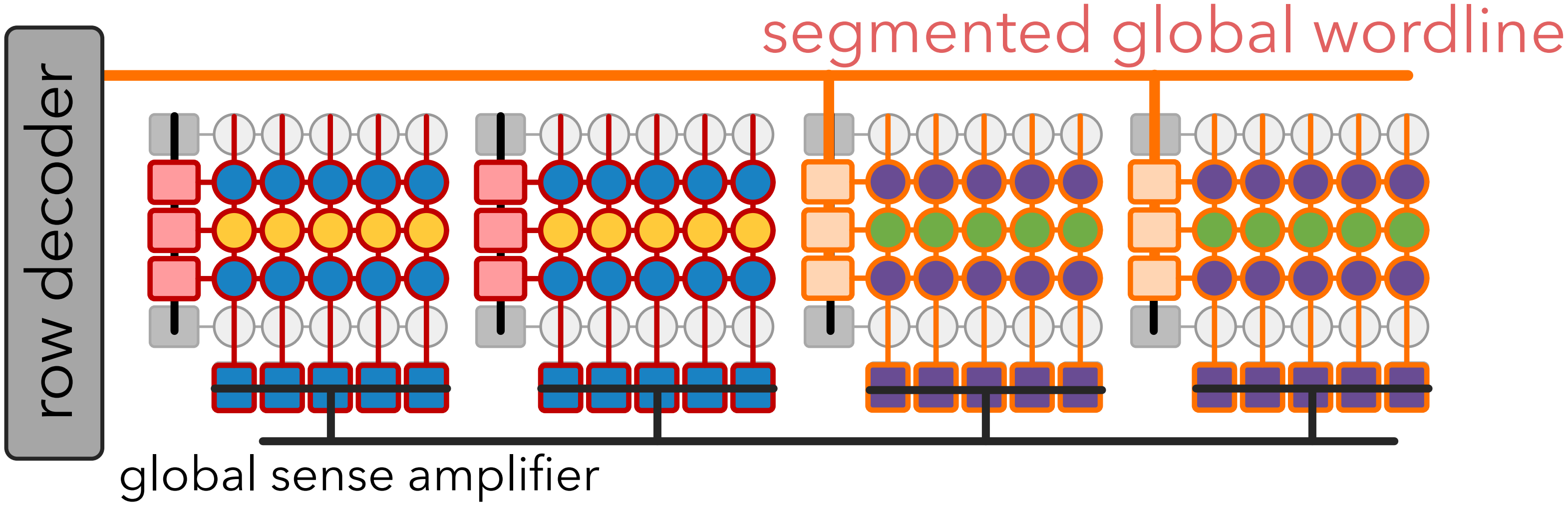


Fine-grained DRAM for processing-using-DRAM:

1 **Improves SIMD utilization**

- for a single PUD operation, only access the DRAM mats with target data

MIMDRAM:
Key Idea (III)



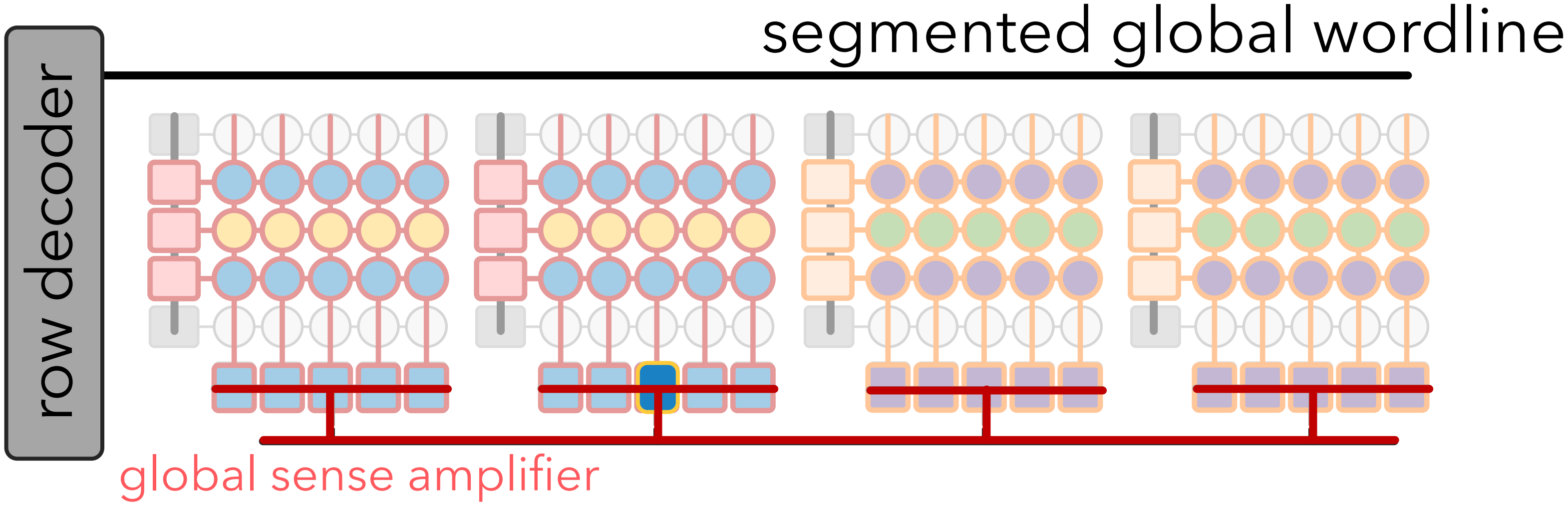
Fine-grained DRAM for processing-using-DRAM:

1 Improves SIMD utilization

- for a single PUD operation, only access the DRAM mats with target data
- for multiple PUD operations, execute independent operations concurrently

→ **multiple instruction, multiple data (MIMD) execution model**

MIMDRAM:
Key Idea (III)

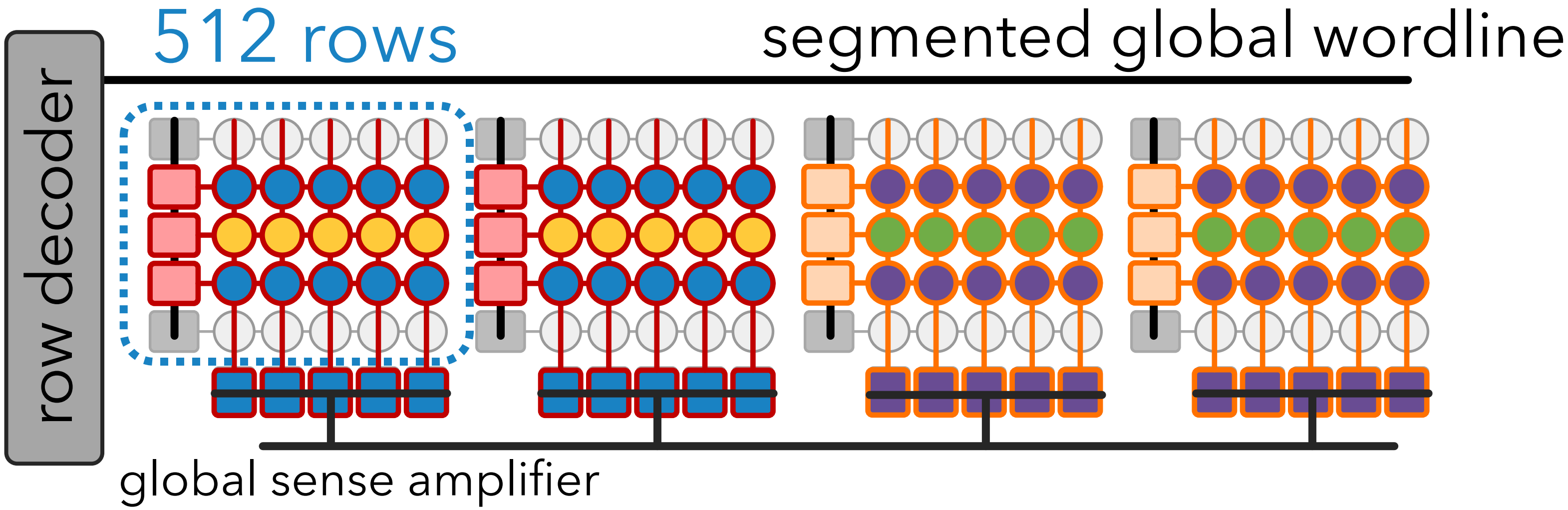


Fine-grained DRAM for processing-using-DRAM:

1 **Improves SIMD utilization**
- for a single PUD operation, only access the DRAM mats with target data
- for multiple PUD operations, execute independent operations concurrently
→ **multiple instruction, multiple data (MIMD) execution model**

2 **Enables low-cost interconnects for vector reduction**
- global and local data buses can be used for inter-/intra-mat communication

MIMDRAM:
Key Idea (III)



Fine-grained DRAM for processing-using-DRAM:

1 Improves SIMD utilization

- for a single PUD operation, only access the DRAM mats with target data
- for multiple PUD operations, execute independent operations concurrently
  → **multiple instruction, multiple data (MIMD) execution model**

2 Enables low-cost interconnects for vector reduction

- global and local data buses can be used for inter-/intra-mat communication

3 Eases programmability

- SIMD parallelism in a DRAM mat is on par with vector ISAs' SIMD width

MIMDRAM:
Overview

MIMDRAM is a hardware/software co-designed PUD system that enables fine-grained PUD computation at low cost and programming effort

Main components of MIMDRAM:

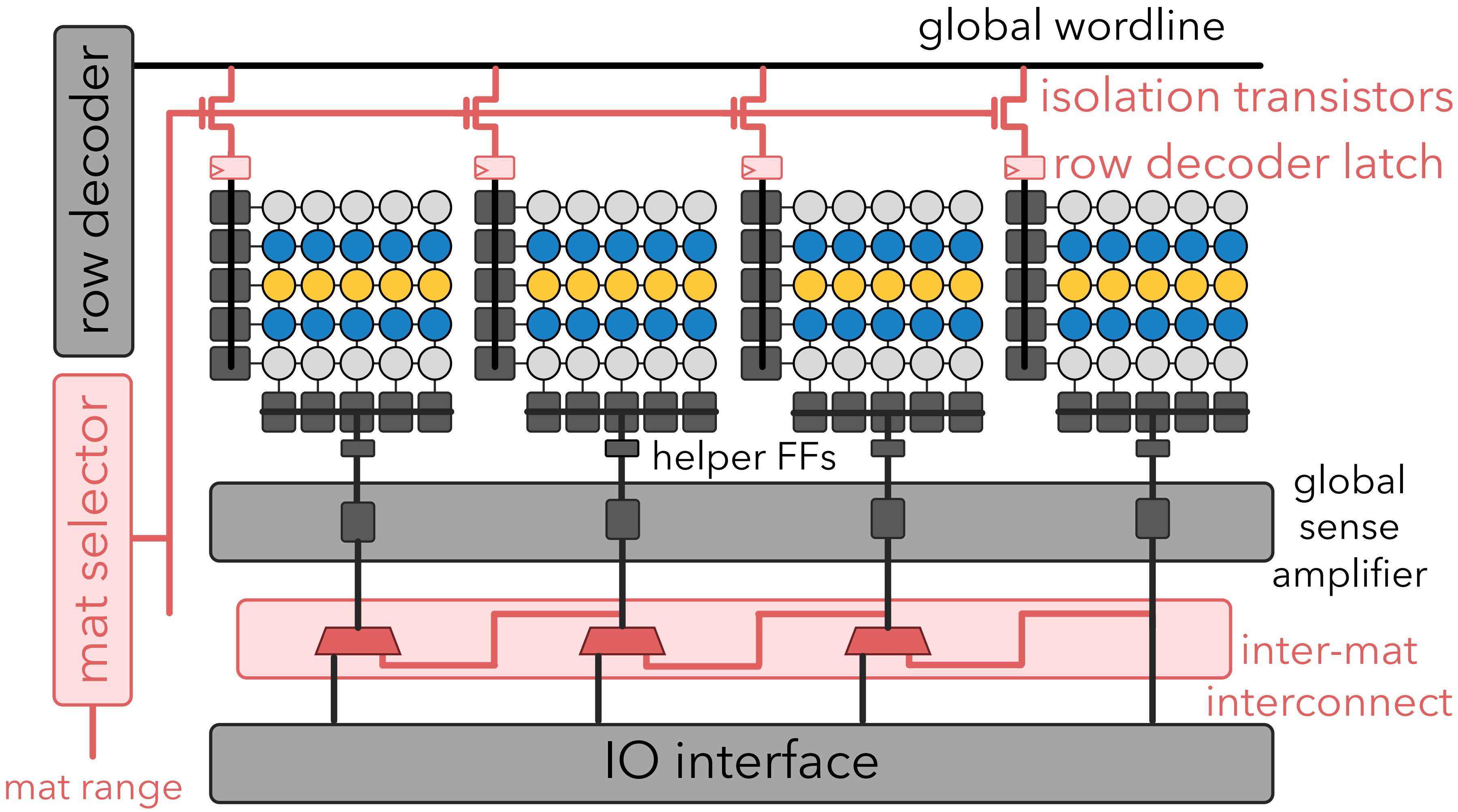
1 **Hardware**

- DRAM array modification to enable fine-grained PUD computation
- inter- and intra-mat interconnects to enable PUD vector reduction
- control unit design to orchestrate PUD execution

2 **Software**

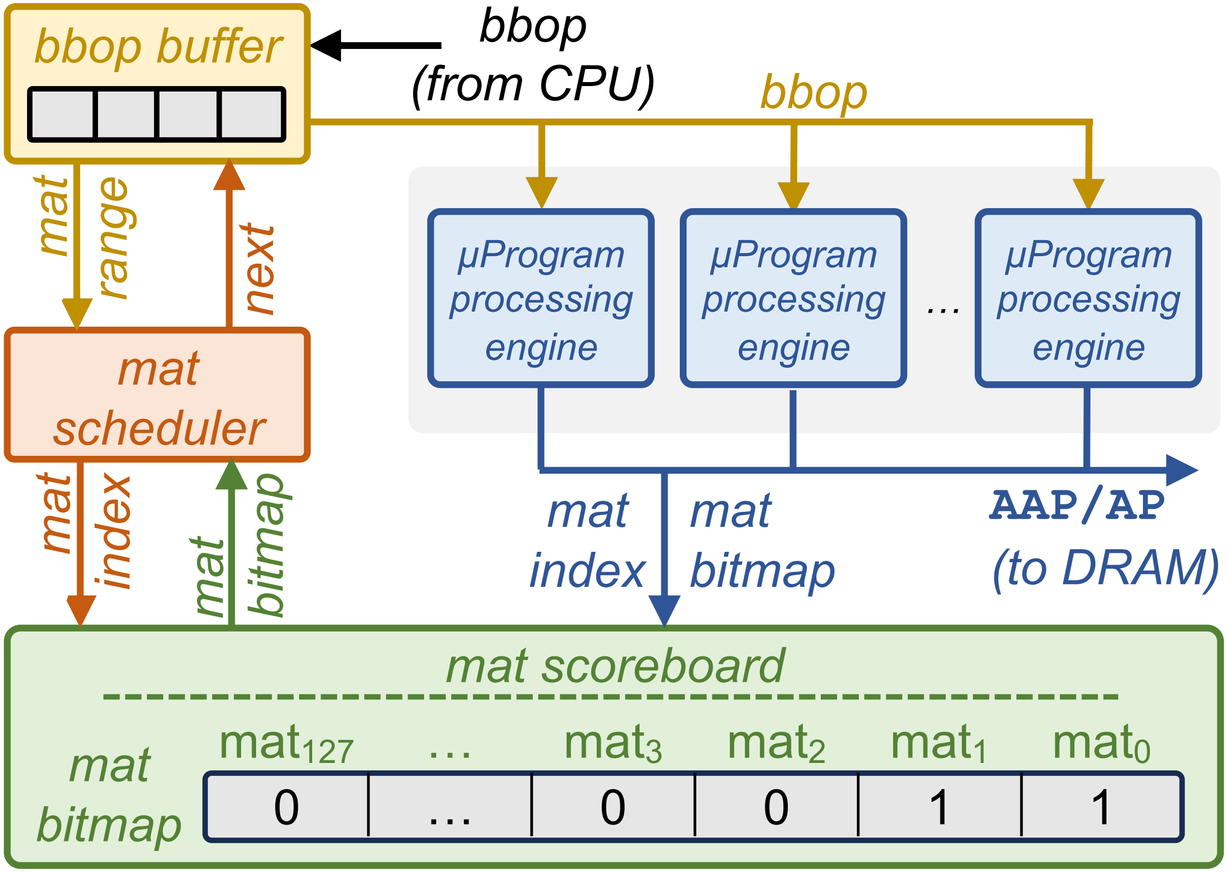
- compiler support to transparently generate PUD instructions
- system support to map and execute PUD instructions

MIMDRAM:
Modifications to DRAM Chip



MIMDRAM:
Control Unit Design

The control unit schedules and orchestrates the execution of multiple PUD operations transparently

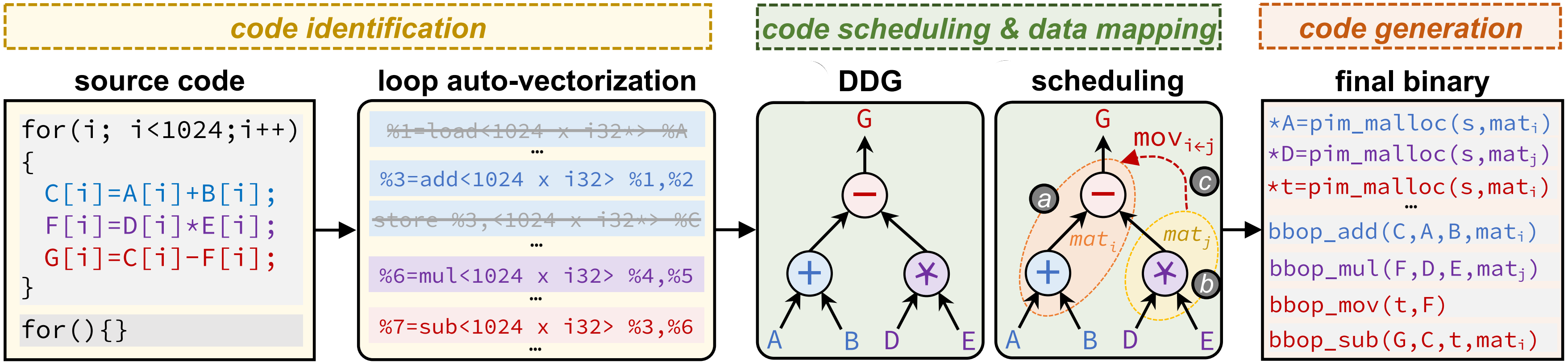


MIMDRAM:
Compiler Support

Goal

Transparently:
extract SIMD parallelism from an application, and
schedule PUD instructions while maximizing utilization

Three new LLVM-based passes targeting PUD execution



code identification

code scheduling & data mapping

code generation

source code

```
for(i; i<1024;i++)
{
  C[i]=A[i]+B[i];
  F[i]=D[i]*E[i];
  G[i]=C[i]-F[i];
}
for(){}
```

loop auto-vectorization

~~%1=load<1024 x i32*> %A~~
…
%3=add<1024 x i32> %1,%2
~~store %3,<1024 x i32*> %C~~
…
%6=mul<1024 x i32> %4,%5
…
%7=sub<1024 x i32> %3,%6
…

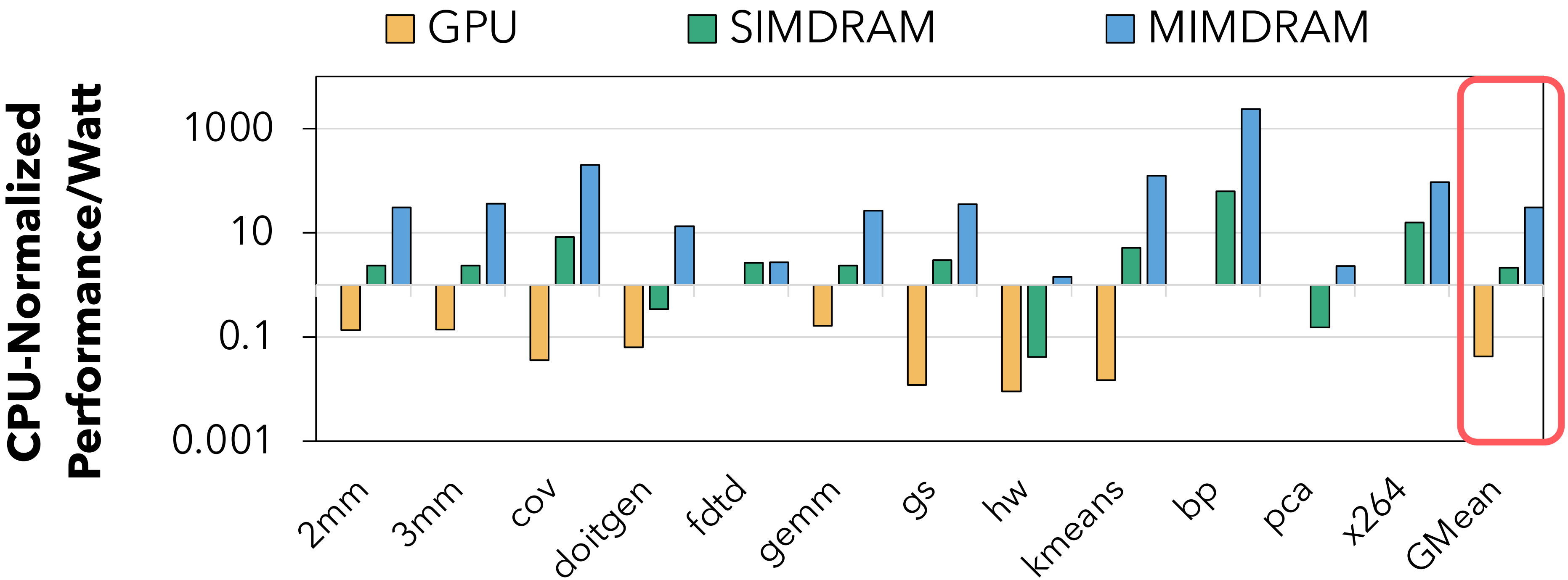
DDG

scheduling

final binary

```
*A=pim_malloc(s,mat_i)
*D=pim_malloc(s,mat_j)
*t=pim_malloc(s,mat_i)
…
bbop_add(C,A,B,mat_i)
bbop_mul(F,D,E,mat_j)
bbop_mov(t,F)
bbop_sub(G,C,t,mat_i)
```

Evaluation:
Single Application Analysis – Energy Efficiency

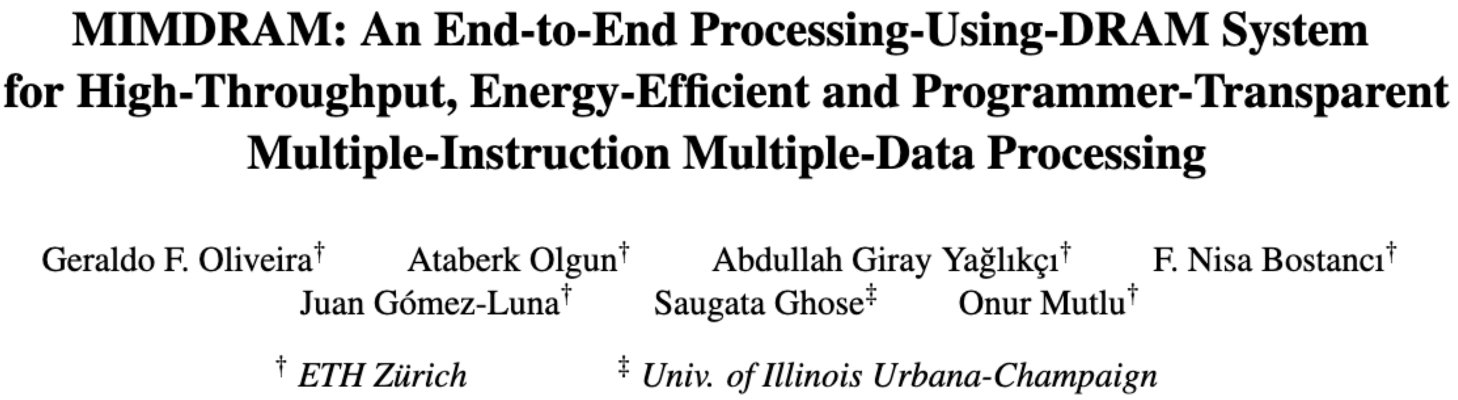


Takeaway

MIMDRAM significantly improves energy efficiency compared to CPU (30.6x), GPU (6.8x), and SIMDRAM (14.3x)

More on MIMDRAM

- Geraldo F. Oliveira, Ataberk Olgun, Abdullah Giray Yağlıkçı, F. Nisa Bostancı, Juan Gómez-Luna, Saugata Ghose, and Onur Mutlu
" MIMDRAM: An End-to-End Processing-Using-DRAM System for High-Throughput, Energy-Efficient and Programmer-Transparent Multiple-Instruction Multiple-Data Computing"
Proceedings of the 30th International Symposium on High-Performance Computer Architecture (***HPCA***), Edinburgh, Scotland, March 2024.



MIMDRAM: An End-to-End Processing-Using-DRAM System for High-Throughput, Energy-Efficient and Programmer-Transparent Multiple-Instruction Multiple-Data Processing

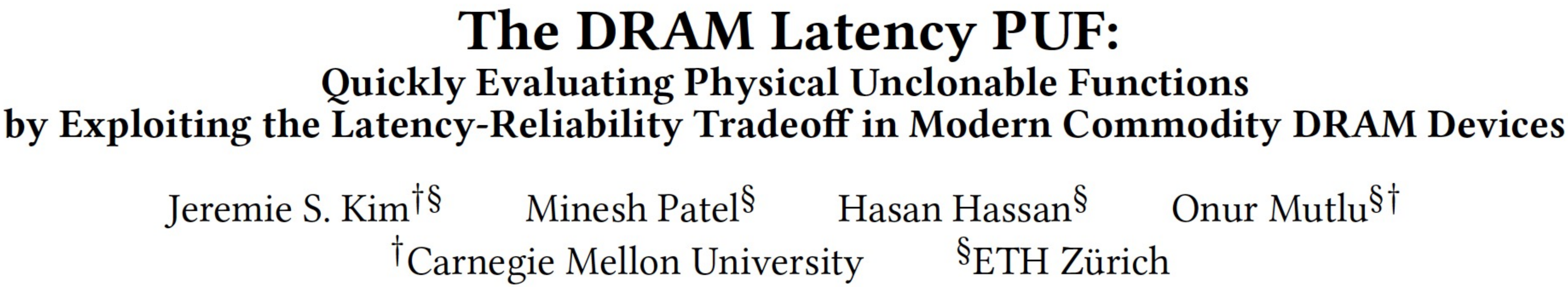
Geraldo F. Oliveira[†] Ataberk Olgun[†] Abdullah Giray Yağlıkçı[†] F. Nisa Bostancı[†]
Juan Gómez-Luna[†] Saugata Ghose[‡] Onur Mutlu[†]

[†] *ETH Zürich* [‡] *Univ. of Illinois Urbana-Champaign*

https://arxiv.org/pdf/2402.19080.pdf

In-DRAM Physical Unclonable Functions

- Jeremie S. Kim, Minesh Patel, Hasan Hassan, and Onur Mutlu,
  "The DRAM Latency PUF: Quickly Evaluating Physical Unclonable Functions by Exploiting the Latency-Reliability Tradeoff in Modern DRAM Devices"
  *Proceedings of the 24th International Symposium on High-Performance Computer Architecture (**HPCA**)*, Vienna, Austria, February 2018.
  [Lightning Talk Video]
  [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)]
  [Full Talk Lecture Video (28 minutes)]

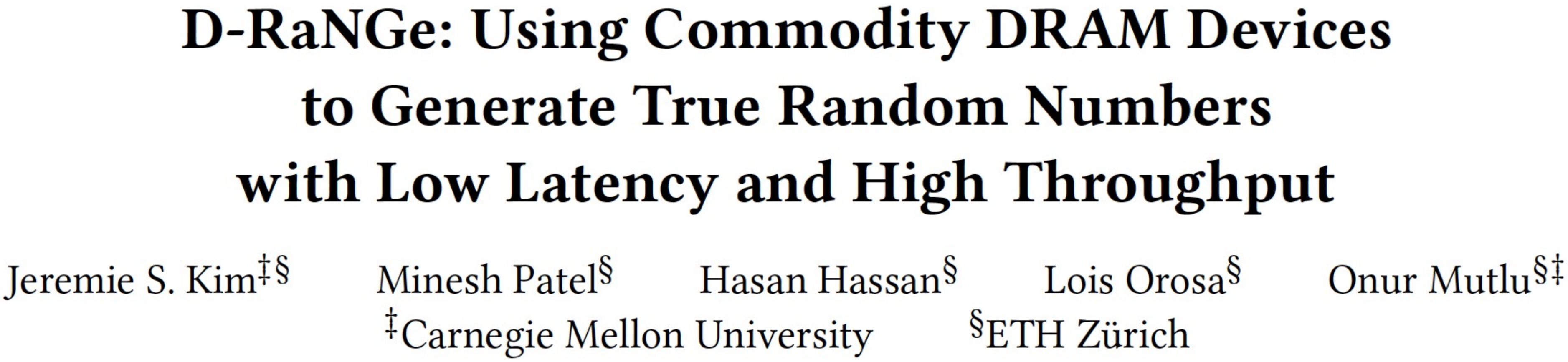


The DRAM Latency PUF:
Quickly Evaluating Physical Unclonable Functions
by Exploiting the Latency-Reliability Tradeoff in Modern Commodity DRAM Devices

Jeremie S. Kim[†§] Minesh Patel[§] Hasan Hassan[§] Onur Mutlu[§†]
[†]Carnegie Mellon University [§]ETH Zürich

In-DRAM True Random Number Generation

- Jeremie S. Kim, Minesh Patel, Hasan Hassan, Lois Orosa, and Onur Mutlu,
  "D-RaNGe: Using Commodity DRAM Devices to Generate True Random Numbers with Low Latency and High Throughput"
  *Proceedings of the 25th International Symposium on High-Performance Computer Architecture (**HPCA**)*, Washington, DC, USA, February 2019.
  [Slides (pptx) (pdf)]
  [Full Talk Video (21 minutes)]
  [Full Talk Lecture Video (27 minutes)]
  Top Picks Honorable Mention by IEEE Micro.

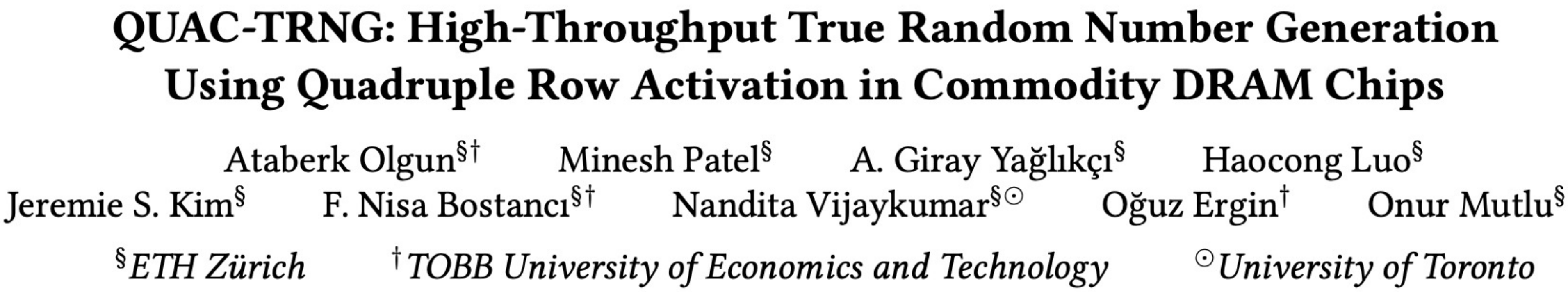


D-RaNGe: Using Commodity DRAM Devices to Generate True Random Numbers with Low Latency and High Throughput

Jeremie S. Kim[‡§] Minesh Patel[§] Hasan Hassan[§] Lois Orosa[§] Onur Mutlu[§‡]
[‡]Carnegie Mellon University [§]ETH Zürich

In-DRAM True Random Number Generation

- Ataberk Olgun, Minesh Patel, A. Giray Yaglikci, Haocong Luo, Jeremie S. Kim, F. Nisa Bostanci, Nandita Vijaykumar, Oguz Ergin, and Onur Mutlu,
  "QUAC-TRNG: High-Throughput True Random Number Generation Using Quadruple Row Activation in Commodity DRAM Chips"
  Proceedings of the 48th International Symposium on Computer Architecture (***ISCA***), Virtual, June 2021.
  [Slides (pptx) (pdf)]
  [Short Talk Slides (pptx) (pdf)]
  [Talk Video (25 minutes)]
  [SAFARI Live Seminar Video (1 hr 26 mins)]

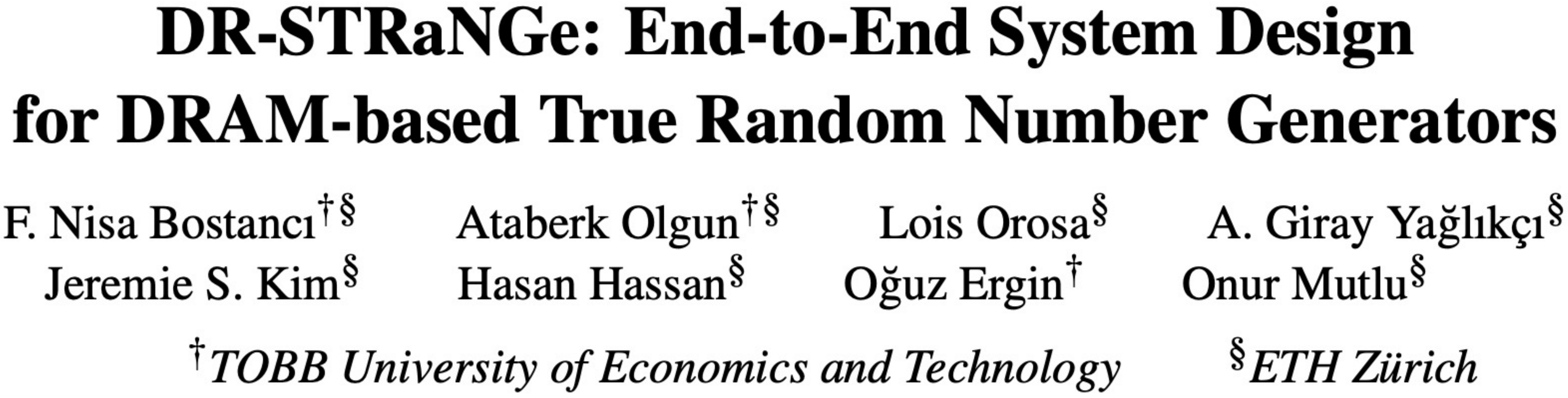


QUAC-TRNG: High-Throughput True Random Number Generation Using Quadruple Row Activation in Commodity DRAM Chips

Ataberk Olgun[§†] Minesh Patel[§] A. Giray Yağlıkçı[§] Haocong Luo[§]
Jeremie S. Kim[§] F. Nisa Bostancı[§†] Nandita Vijaykumar[§⊙] Oğuz Ergin[†] Onur Mutlu[§]
[§]*ETH Zürich* [†]*TOBB University of Economics and Technology* [⊙]*University of Toronto*

In-DRAM True Random Number Generation

- F. Nisa Bostanci, Ataberk Olgun, Lois Orosa, A. Giray Yaglikci, Jeremie S. Kim, Hasan Hassan, Oguz Ergin, and Onur Mutlu,
  "DR-STRaNGe: End-to-End System Design for DRAM-based True Random Number Generators"
  *Proceedings of the 28th International Symposium on High-Performance Computer Architecture (**HPCA**)*, Virtual, April 2022.
  [Slides (pptx) (pdf)]
  [Short Talk Slides (pptx) (pdf)]



DR-STRaNGe: End-to-End System Design for DRAM-based True Random Number Generators

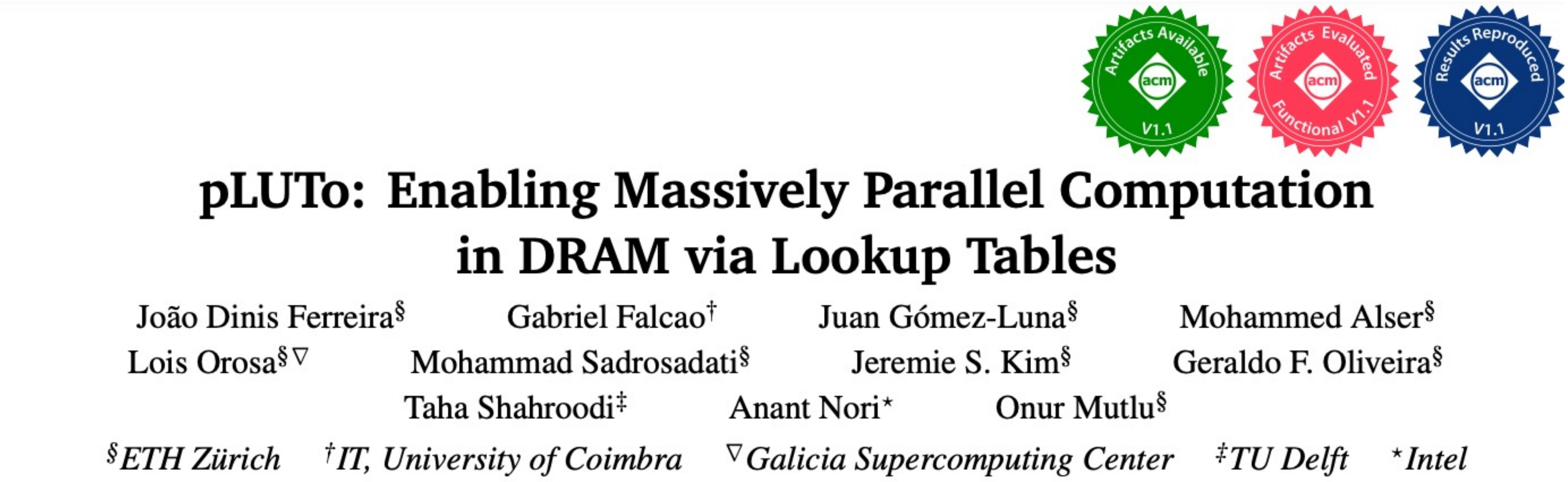
F. Nisa Bostancı[†][§] Ataberk Olgun[†][§] Lois Orosa[§] A. Giray Yağlıkçı[§]
Jeremie S. Kim[§] Hasan Hassan[§] Oğuz Ergin[†] Onur Mutlu[§]

[†]*TOBB University of Economics and Technology* [§]*ETH Zürich*

https://arxiv.org/pdf/2201.01385.pdf

In-DRAM Lookup-Table Based Execution

João Dinis Ferreira, Gabriel Falcao, Juan Gómez-Luna, Mohammed Alser, Lois Orosa, Mohammad Sadrosadati, Jeremie S. Kim, Geraldo F. Oliveira, Taha Shahroodi, Anant Nori, and Onur Mutlu,
"pLUTo: Enabling Massively Parallel Computation in DRAM via Lookup Tables"
Proceedings of the 55th International Symposium on Microarchitecture (***MICRO***), Chicago, IL, USA, October 2022.
[Slides (pptx) (pdf)]
[Longer Lecture Slides (pptx) (pdf)]
[Lecture Video (26 minutes)]
[arXiv version]
[Source Code (Officially Artifact Evaluated with All Badges)]
Officially artifact evaluated as available, reusable and reproducible.


Artifacts Available acm V1.1
Artifacts Evaluated acm Functional V1.1
Results Reproduced acm V1.1

pLUTo: Enabling Massively Parallel Computation in DRAM via Lookup Tables

João Dinis Ferreira[§] Gabriel Falcao[†] Juan Gómez-Luna[§] Mohammed Alser[§]
Lois Orosa[§∇] Mohammad Sadrosadati[§] Jeremie S. Kim[§] Geraldo F. Oliveira[§]
Taha Shahroodi[‡] Anant Nori[⋆] Onur Mutlu[§]
[§]*ETH Zürich* [†]*IT, University of Coimbra* [∇]*Galicia Supercomputing Center* [‡]*TU Delft* [⋆]*Intel*

https://arxiv.org/pdf/2104.07699.pdf

Limitations of Processing-using-DRAM

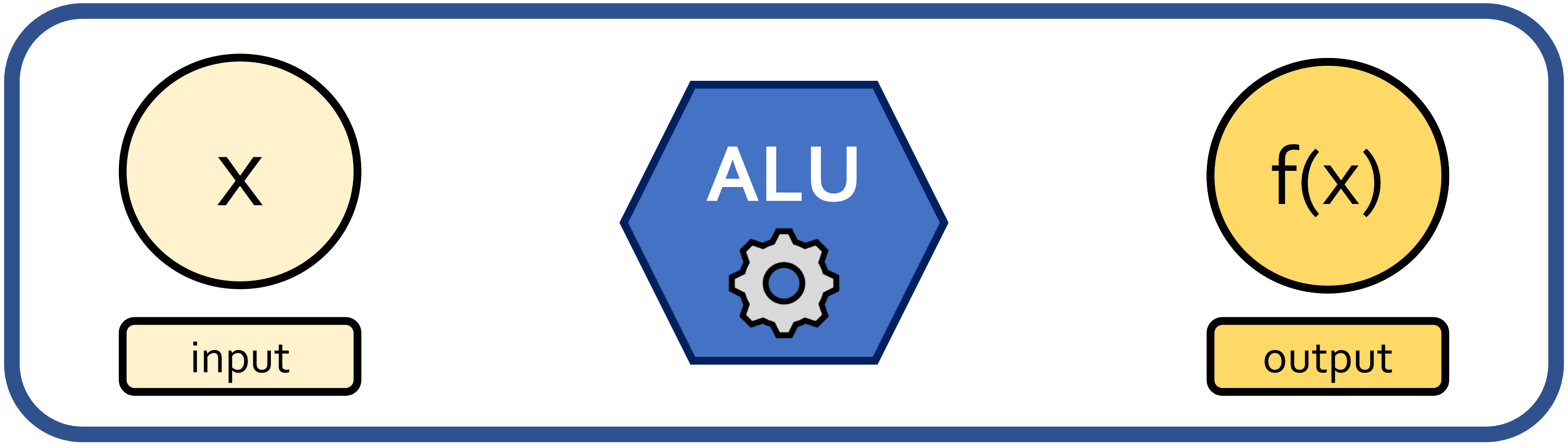
Data Movement	*RowClone, Seshadri+ 2013* *LISA, Chang+ 2013*
Bitwise Operations	*Ambit, Seshadri+ 2017*
Bit Shifting	*DRISA, Li+ 2017*
Arithmetic Operations	*SIMDRAM, Hajinazar & Oliveira+ 2021*

Existing Processing-using-DRAM architectures only support a limited range of operations

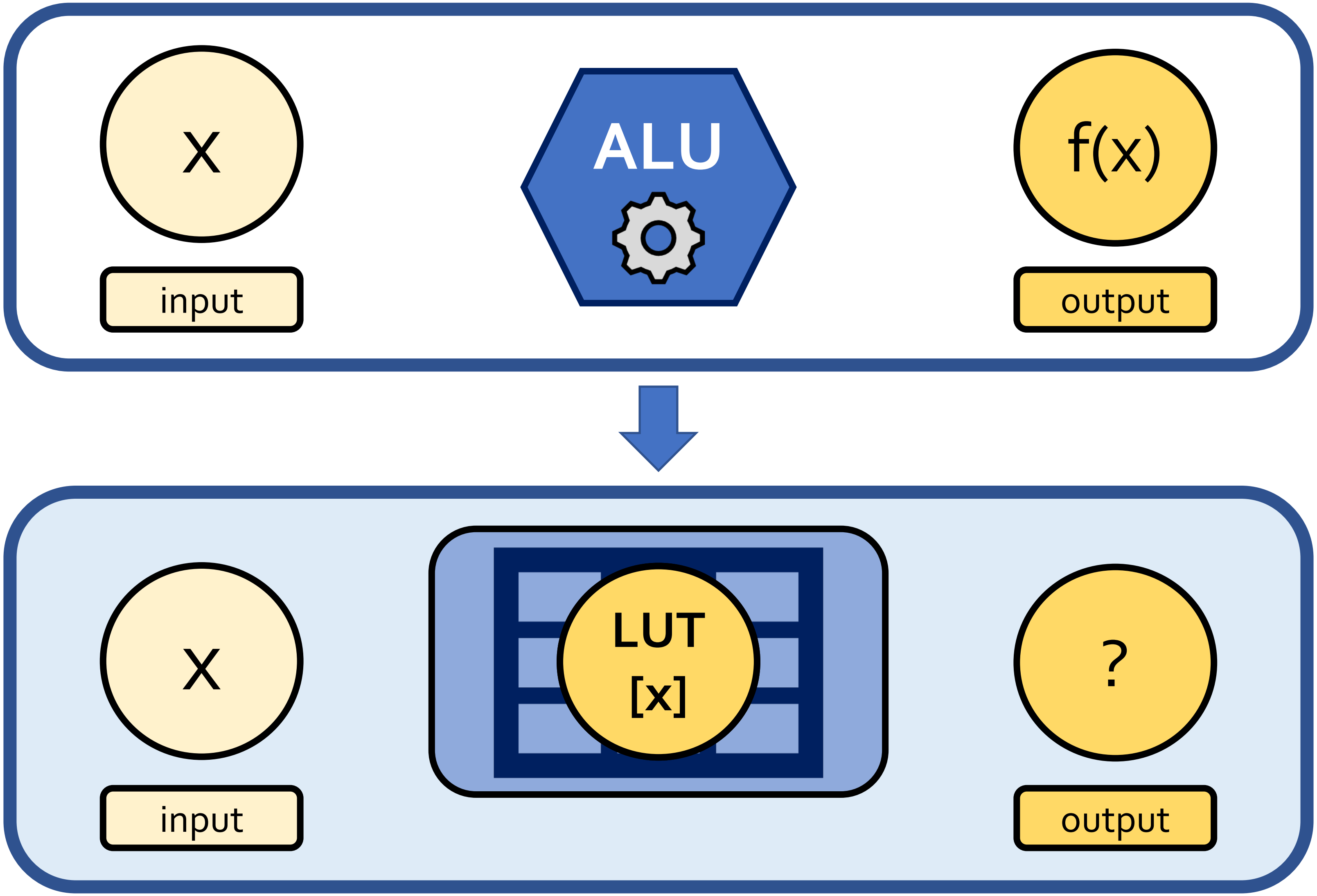
The Goal of pLUTo

Extend Processing-using-DRAM to support the execution of *arbitrarily complex operations*

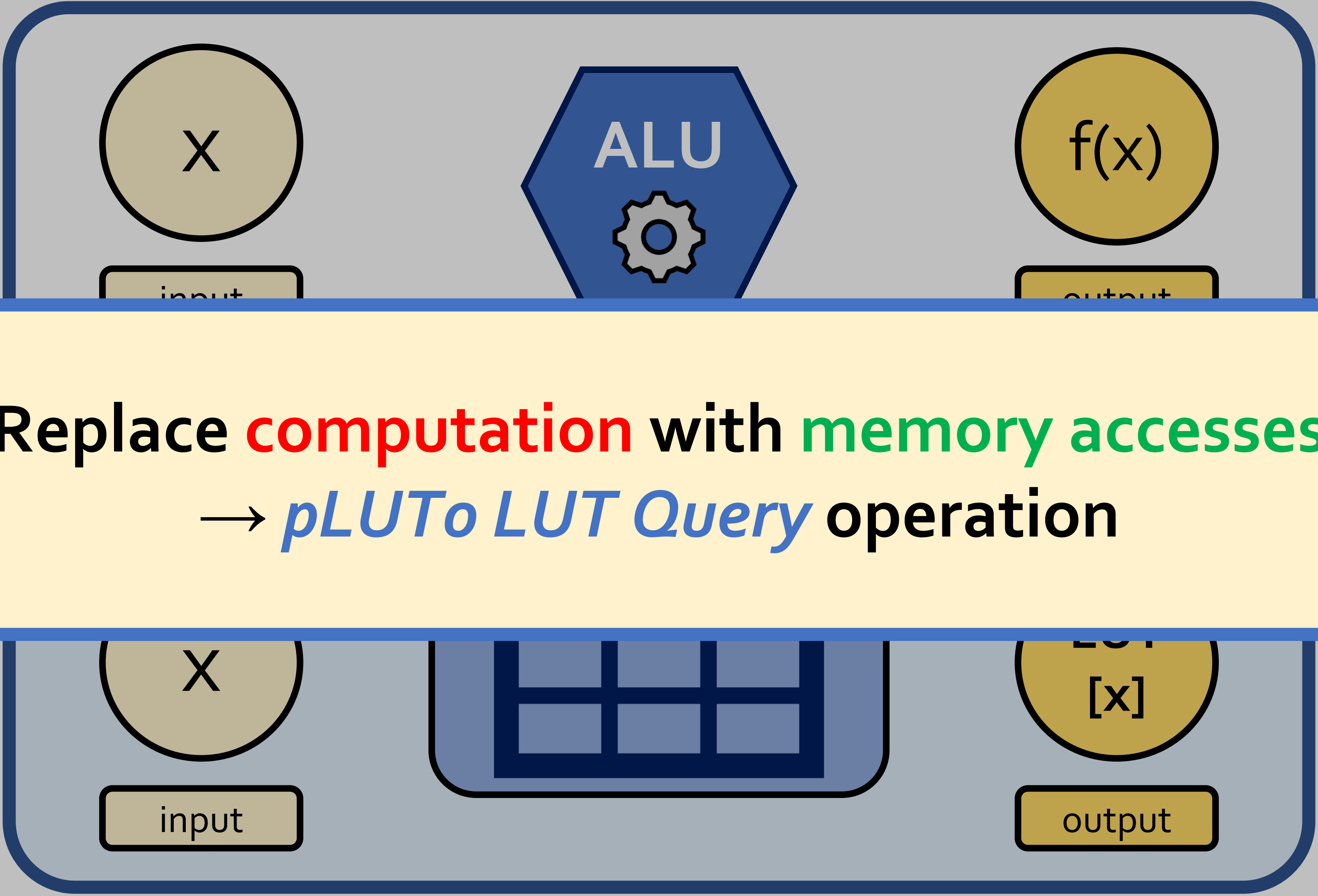
pLUTo: Key Idea



pLUTo: Key Idea

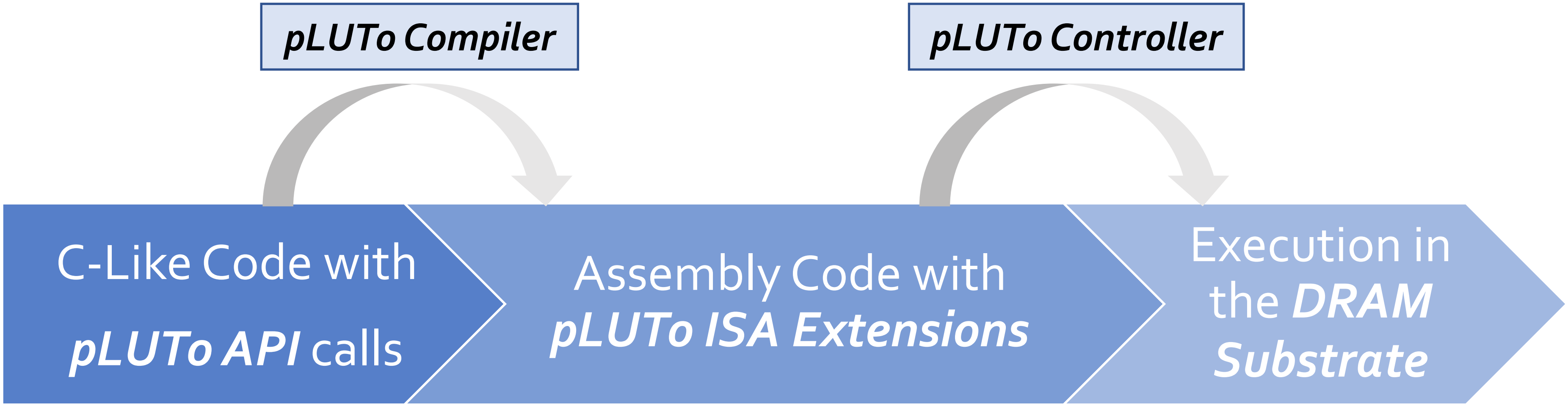


pLUTo: Key Idea



Replace computation with memory accesses
→ *pLUTo LUT Query* operation

System Integration



pLUTo Compiler

pLUTo Controller

C-Like Code with *pLUTo API* calls

Assembly Code with ***pLUTo ISA Extensions***

Execution in the ***DRAM Substrate***

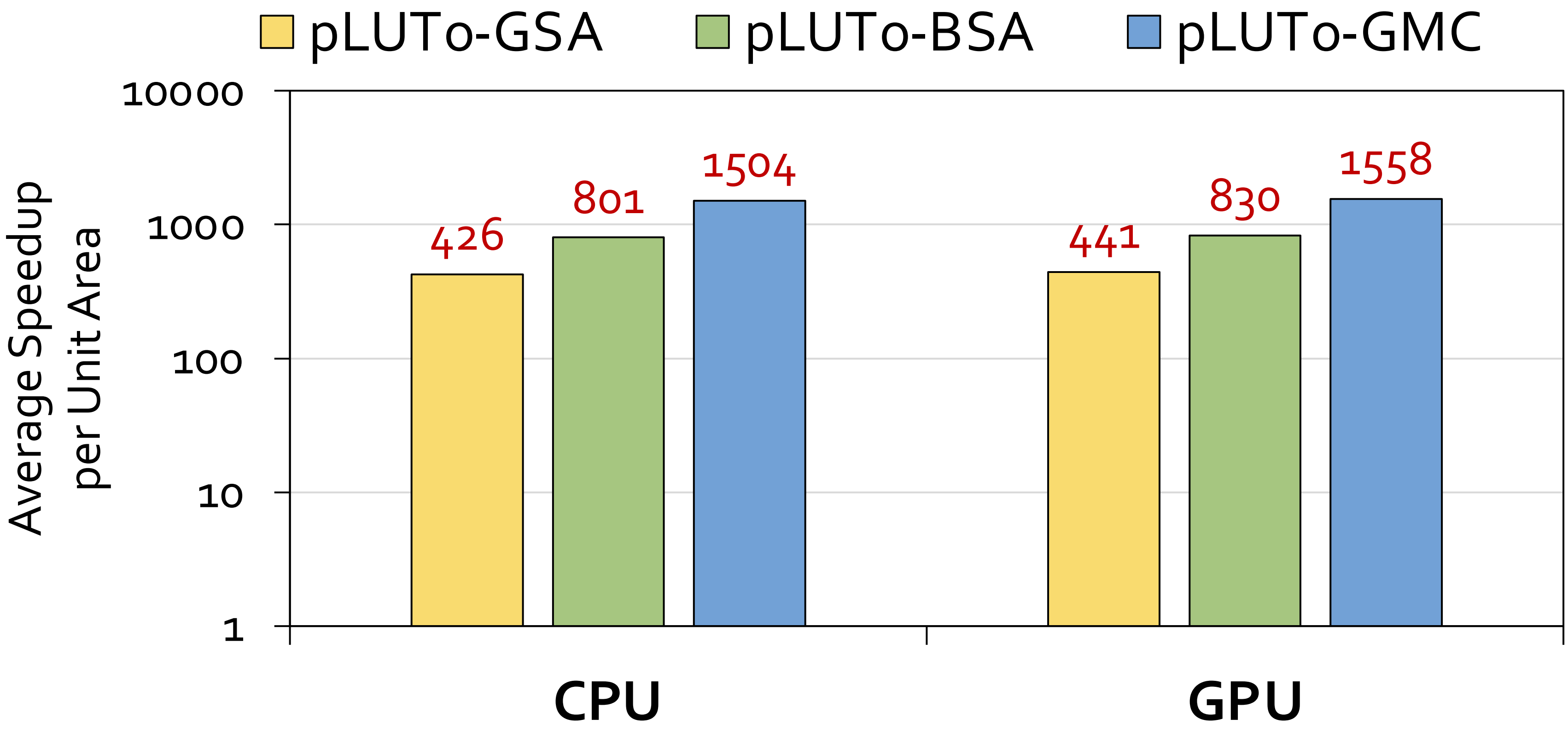
api_pluto_mul

pluto_subarray_alloc
pluto_bit_shift_l
pluto_or
pluto_op

ACT
PRE
ACT
ACT
PRE
...

Performance (normalized to area)

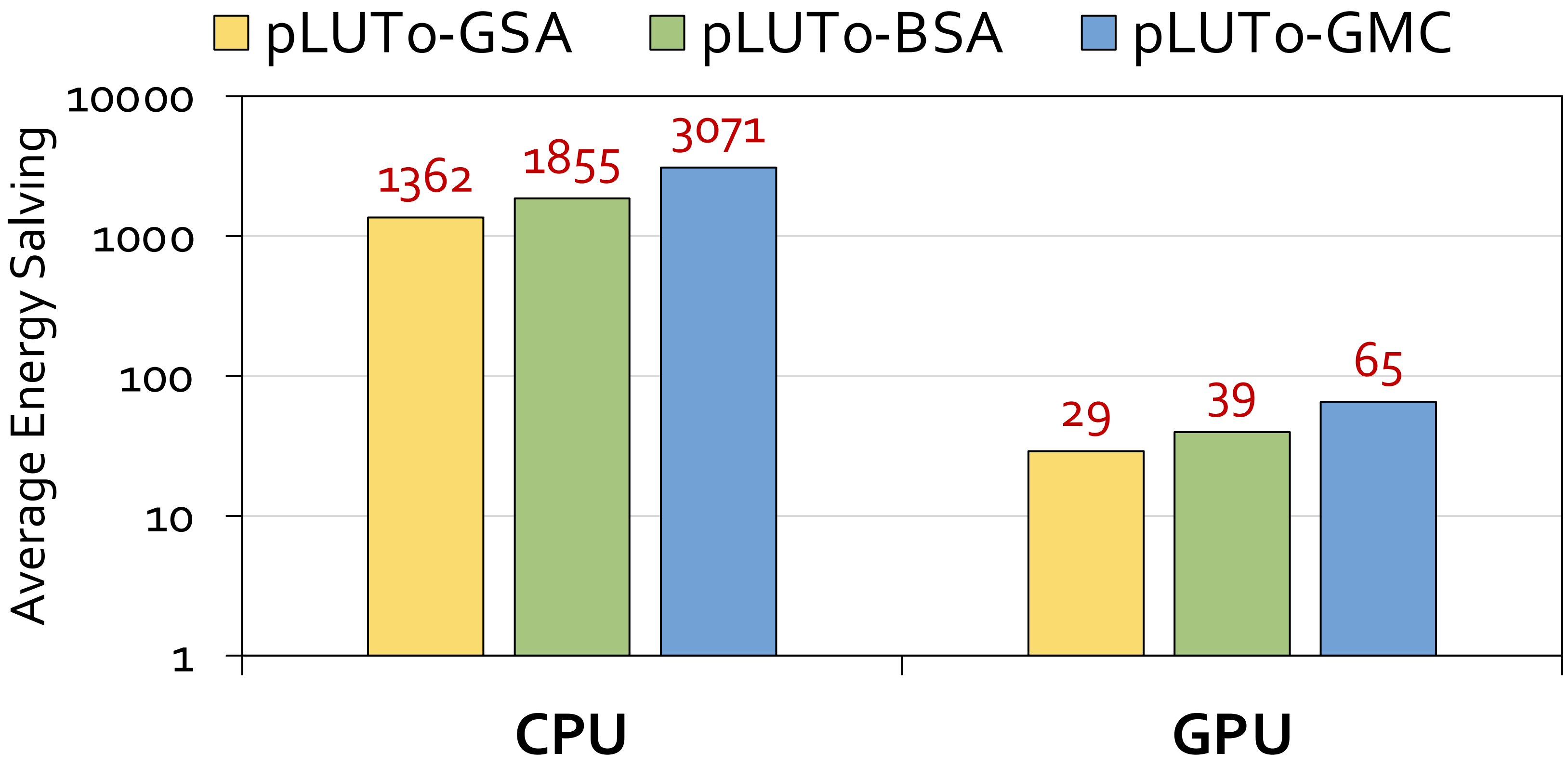
Average speedup normalized to area across 7 real-world workloads



pLUTo provides *substantially higher* performance per unit area than *both* the CPU and the GPU

Energy Consumption

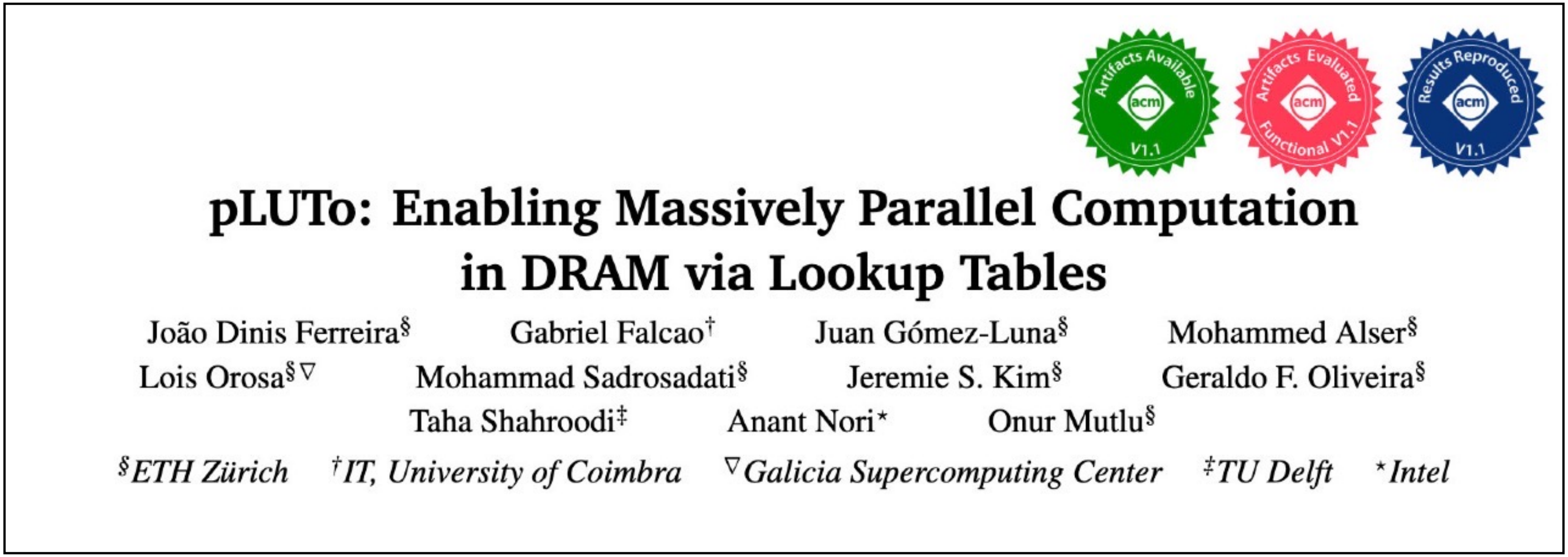
Average energy consumption across 7 real-world workloads



pLUTo ***significantly reduces energy consumption*** **compared to processor-centric architectures for various workloads**

More Results in the Paper

- Comparison with FPGA
- Area Overhead Analysis
- Circuit-Level Reliability & Correctness
- Subarray-Level Parallelism
- LUT Loading Overhead
- Range of Supported Operations


Artifacts Available
acm
V1.1
Artifacts Evaluated
acm
Functional V1.1
Results Reproduced
acm
V1.1

pLUTo: Enabling Massively Parallel Computation in DRAM via Lookup Tables

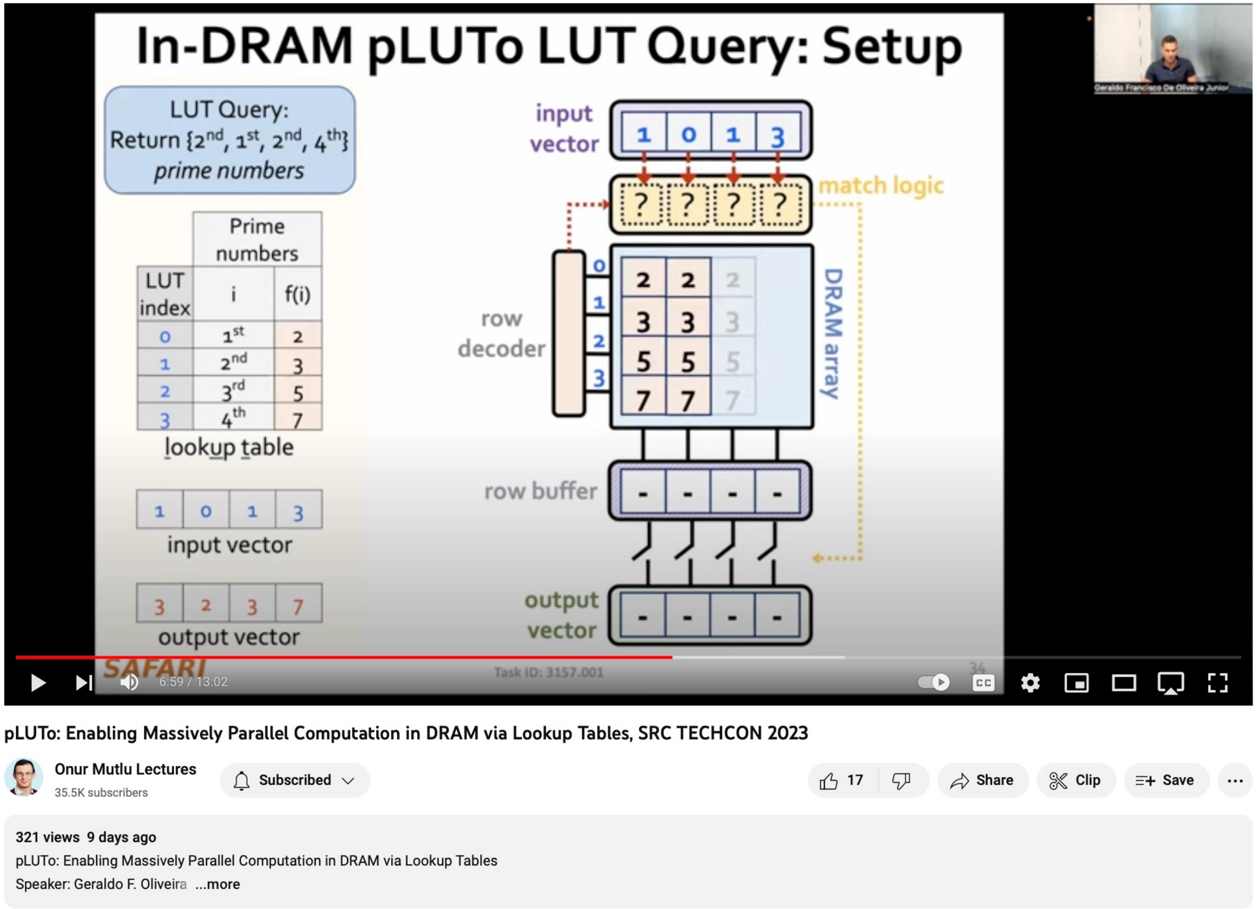
João Dinis Ferreira[§] Gabriel Falcao[†] Juan Gómez-Luna[§] Mohammed Alser[§]
Lois Orosa[§▽] Mohammad Sadrosadati[§] Jeremie S. Kim[§] Geraldo F. Oliveira[§]
Taha Shahroodi[‡] Anant Nori[*] Onur Mutlu[§]

[§]ETH Zürich [†]IT, University of Coimbra [▽]Galicia Supercomputing Center [‡]TU Delft [*]Intel

https://arxiv.org/pdf/2104.07699.pdf

SRC TECHCON Presentation

- Geraldo F. Oliveira
  - pLUTo: Enabling Massively Parallel Computation in DRAM via Lookup Tables
  - https://arxiv.org/pdf/2104.07699.pdf



In-DRAM pLUTo LUT Query: Setup

LUT Query:
Return {2nd, 1st, 2nd, 4th}
prime numbers

LUT index	Prime numbers	
	i	f(i)
0	1st	2
1	2nd	3
2	3rd	5
3	4th	7

lookup table

1	0	1	3

input vector

3	2	3	7

output vector

pLUTo: Enabling Massively Parallel Computation in DRAM via Lookup Tables, SRC TECHCON 2023

Onur Mutlu Lectures
35.5K subscribers

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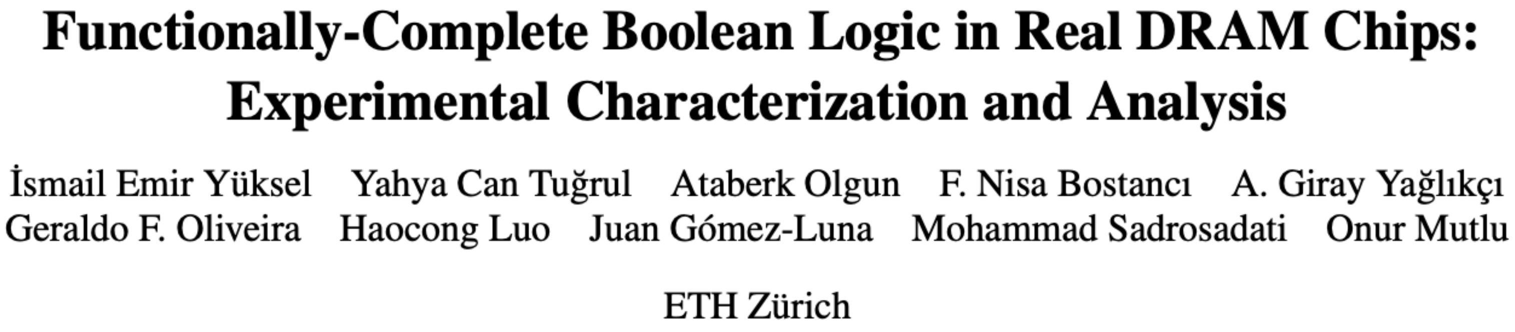
pLUTo: Enabling Massively Parallel Computation in DRAM via Lookup Tables
Speaker: Geraldo F. Oliveira ...more

https://youtu.be/9t1FJQ6nNw4?si=bhylWCLZde2DC7os

Bulk Bitwise Operations in Real DRAM Chips

- Ismail Emir Yüksel, Yahya Can Tugrul Ataberk Olgun, F. Nisa Bostancı, A. Giray Yaglıkçı, Geraldo F. Oliveira, Haocong Luo, Juan Gómez-Luna, Mohammad Sadrosadati, Onur Mutlu, "**Functionally-Complete Boolean Logic in Real DRAM Chips: Experimental Characterization and Analysis**," *Proceedings of the 30th International Symposium on High-Performance Computer Architecture* (***HPCA***), Edinburgh, Scotland, March 2024.



Functionally-Complete Boolean Logic in Real DRAM Chips: Experimental Characterization and Analysis

İsmail Emir Yüksel Yahya Can Tuğrul Ataberk Olgun F. Nisa Bostancı A. Giray Yağlıkçı
Geraldo F. Oliveira Haocong Luo Juan Gómez-Luna Mohammad Sadrosadati Onur Mutlu

ETH Zürich

https://arxiv.org/pdf/2402.18736

The Capability of COTS DRAM Chips

We **demonstrate** that **COTS DRAM chips:**

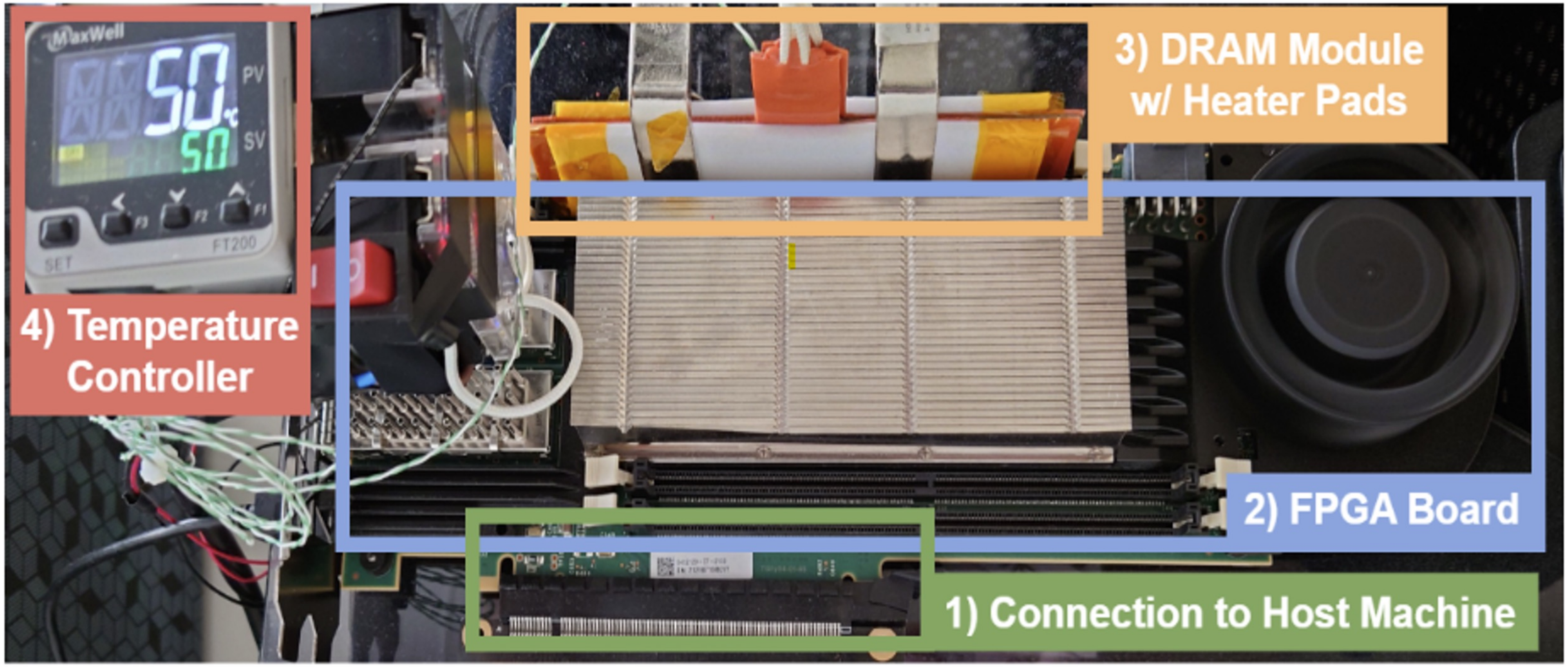
1 Can **simultaneously activate** up to **48 rows** in **two neighboring subarrays**

2 Can perform **NOT operation** with up to **32 output operands**

3 Can perform up to **16-input AND, NAND, OR, and NOR** operations

DRAM Testing Infrastructure

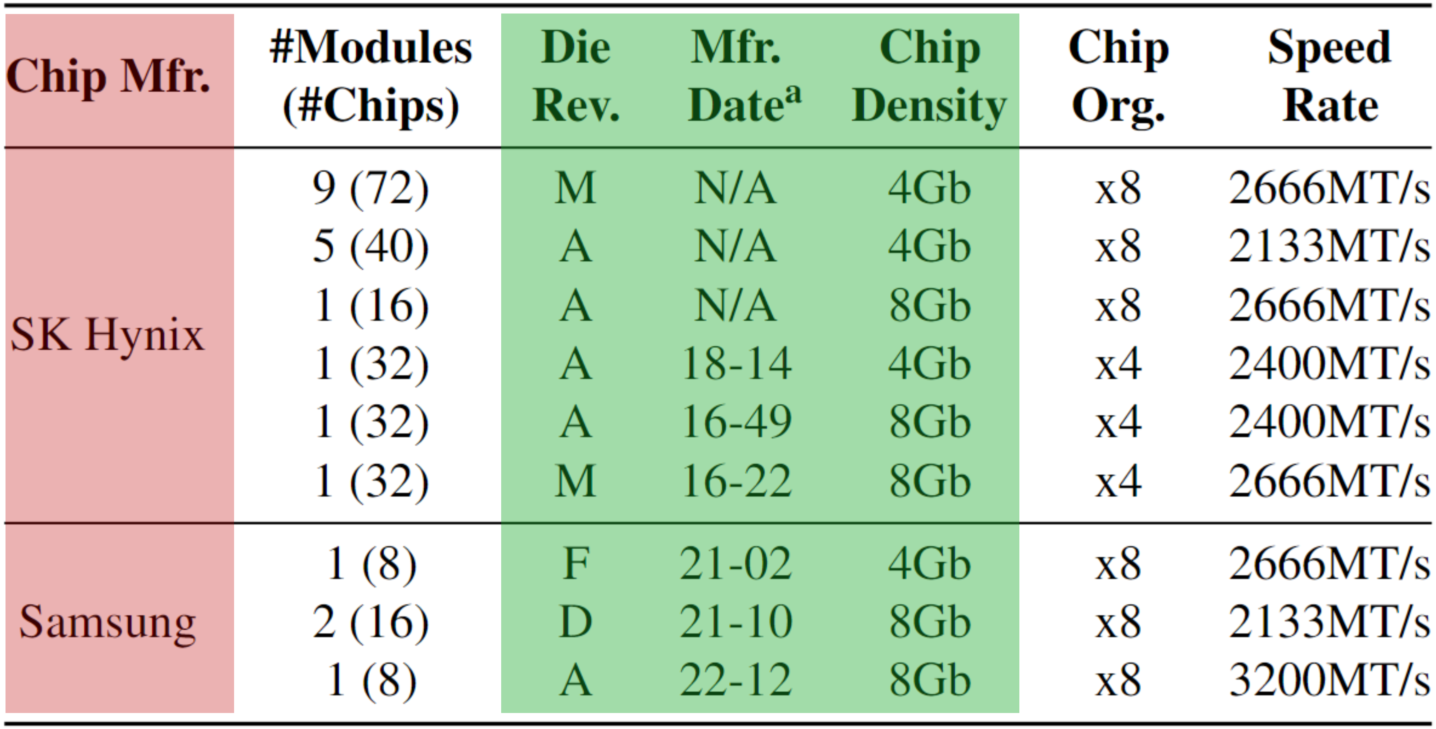
- Developed from DRAM Bender [Olgun+, TCAD'23]*
- Fine-grained control over DRAM commands, timings, and temperature


3) DRAM Module w/ Heater Pads
4) Temperature Controller
2) FPGA Board
1) Connection to Host Machine
MaxWell
50
50
PV
SV
SET
FT200

*Olgun et al., "DRAM Bender: An Extensible and Versatile FPGA-based Infrastructure to Easily Test State-of-the-art DRAM Chips," TCAD, 2023.

DRAM Chips Tested

- 256 DDR4 chips from two major DRAM manufacturers
- Covers different die revisions and chip densities



Chip Mfr.	#Modules (#Chips)	Die Rev.	Mfr. Date[a]	Chip Density	Chip Org.	Speed Rate
SK Hynix	9 (72)	M	N/A	4Gb	x8	2666MT/s
	5 (40)	A	N/A	4Gb	x8	2133MT/s
	1 (16)	A	N/A	8Gb	x8	2666MT/s
	1 (32)	A	18-14	4Gb	x4	2400MT/s
	1 (32)	A	16-49	8Gb	x4	2400MT/s
	1 (32)	M	16-22	8Gb	x4	2666MT/s
Samsung	1 (8)	F	21-02	4Gb	x8	2666MT/s
	2 (16)	D	21-10	8Gb	x8	2133MT/s
	1 (8)	A	22-12	8Gb	x8	3200MT/s

The Capability of COTS DRAM Chips

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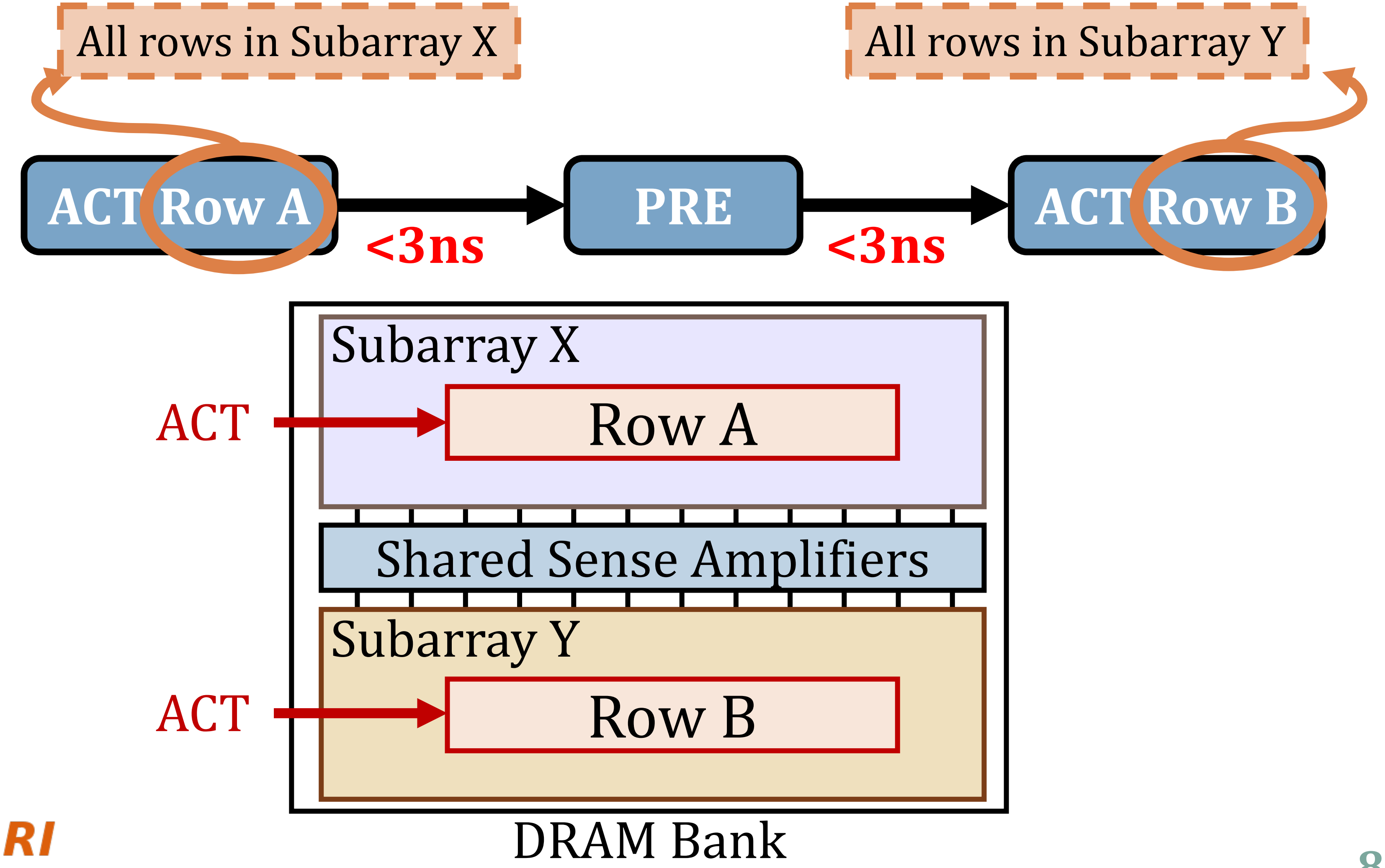
3 Can perform **up to 16-input AND, NAND, OR, and NOR** operations

Characterization Methodology

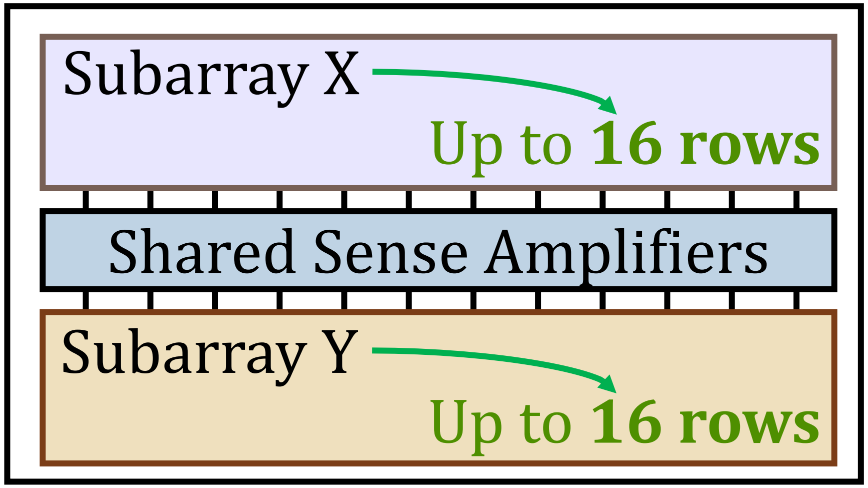
- To understand **which and how many** rows are simultaneously activated
  - **Sweep** Row A and Row B addresses



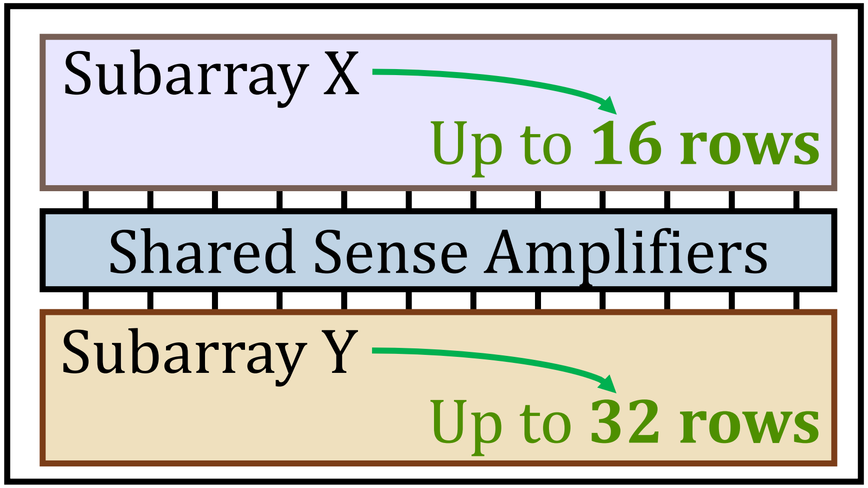
Key Results

COTS DRAM chips have **two distinct** sets of activation patterns in **neighboring subarrays** when two rows are activated with **violated timings**

Exactly the same number of rows in each subarray are activated	**Twice as many** rows in one subarray **compared to its neighbor subarray** are activated



A total of **32 rows**



A total of **48 rows**

The Capability of COTS DRAM Chips

We **demonstrate** that **COTS DRAM chips:**

1 Can **simultaneously activate** up to **48 rows in two neighboring subarrays**

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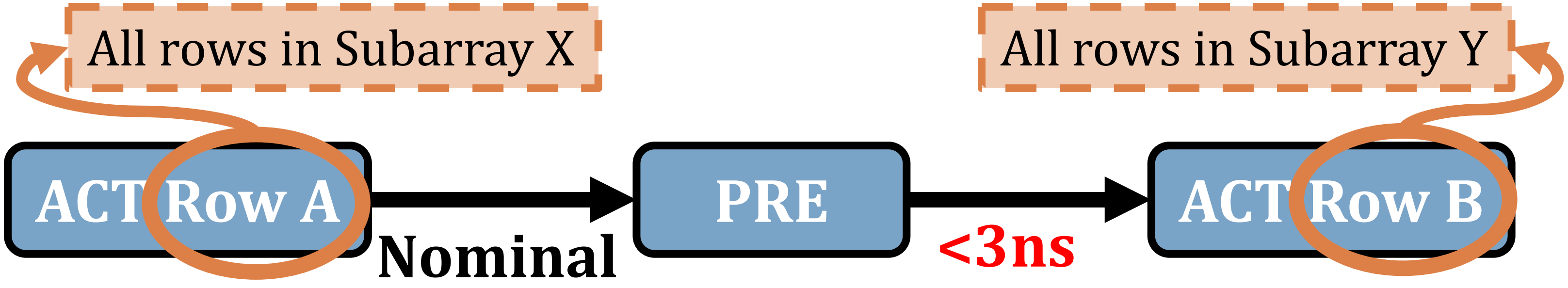


All rows in Subarray X

All rows in Subarray Y

ACT Row A

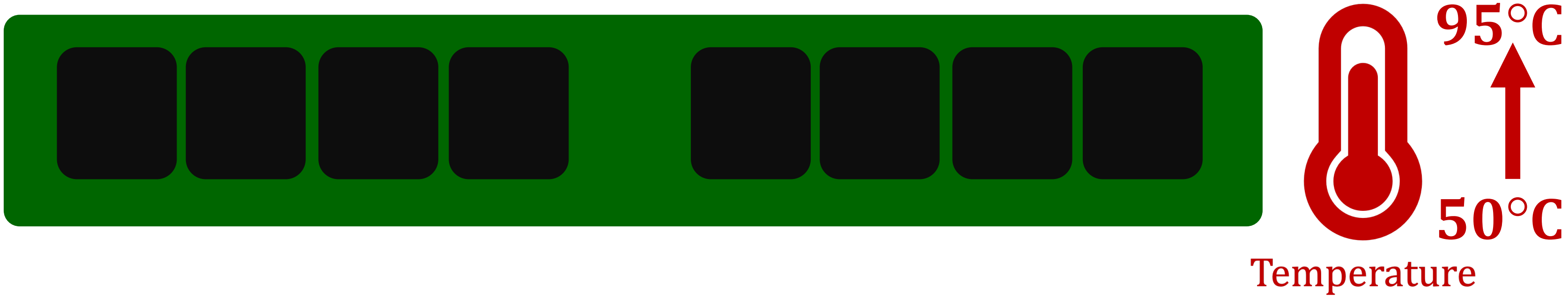
Nominal

PRE

<3ns

ACT Row B

- Sweep **DRAM chip temperature**



Key Takeaways from In-DRAM NOT Operation

Key Takeaway 1

COTS DRAM chips can perform NOT operations with up to 32 destination rows

Key Takeaway 2

Temperature has a small effect on the reliability of NOT operations

The Capability of COTS DRAM Chips

We **demonstrate** that **COTS DRAM chips:**

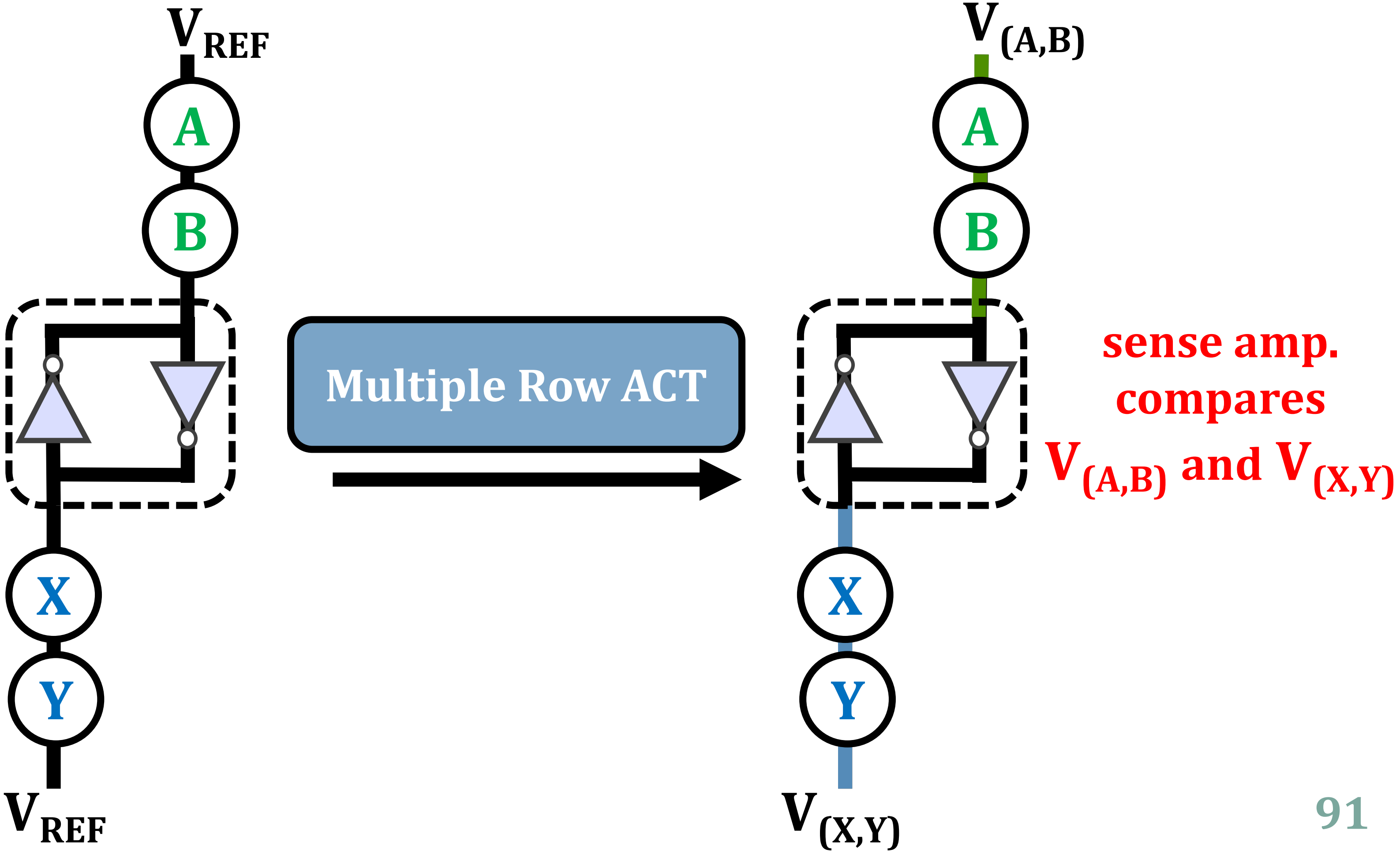
1 Can **simultaneously activate** up to **48 rows in two neighboring subarrays**

2 Can perform **NOT operation** with **up to 32** output operands

3 Can perform **up to 16-input AND, NAND, OR, and NOR** operations

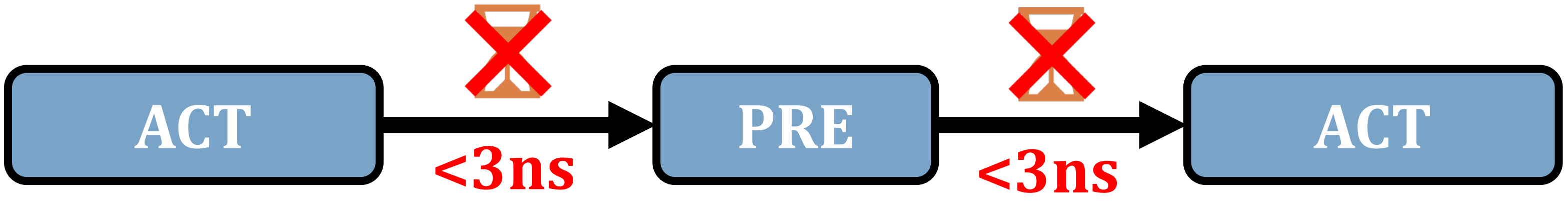
Key Idea

Manipulate the bitline voltage to express **a wide variety of functions** using multiple-row activation in neighboring subarrays



sense amp. compares $V_{(A,B)}$ and $V_{(X,Y)}$

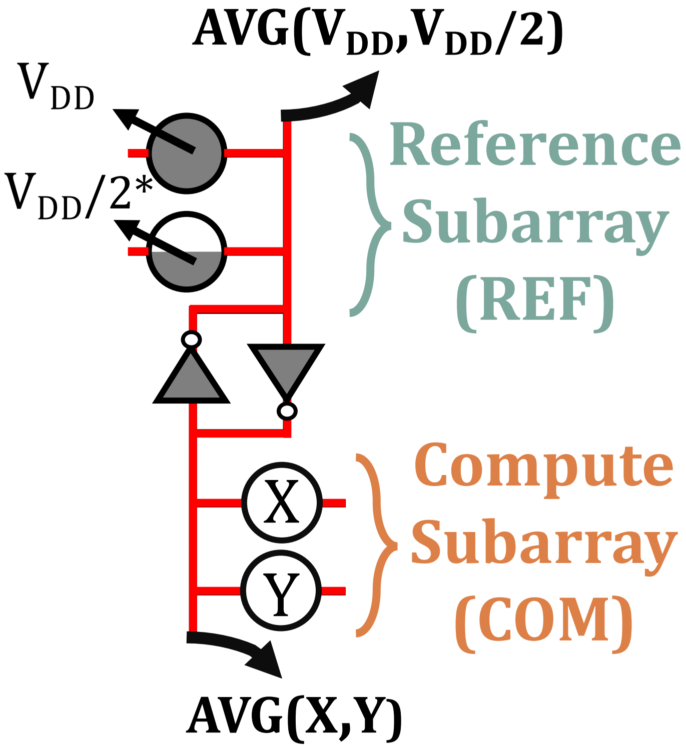
Two-Input AND and NAND Operations



ACT → PRE → ACT

<3ns

<3ns



V_{DD}=1 & GND = 0

X	Y	COM	REF
0	0	0	1
0	1	0	1
1	0	0	1
1	1	1	0
		AND	NAND

*Gao et al., "FracDRAM: Fractional Values in Off-the-Shelf DRAM," in MICRO, 2022.

Key Takeaways from In-DRAM Operations

Key Takeaway 1

COTS DRAM chips can perform {2, 4, 8, 16}-input AND, NAND, OR, and NOR operations

Key Takeaway 2

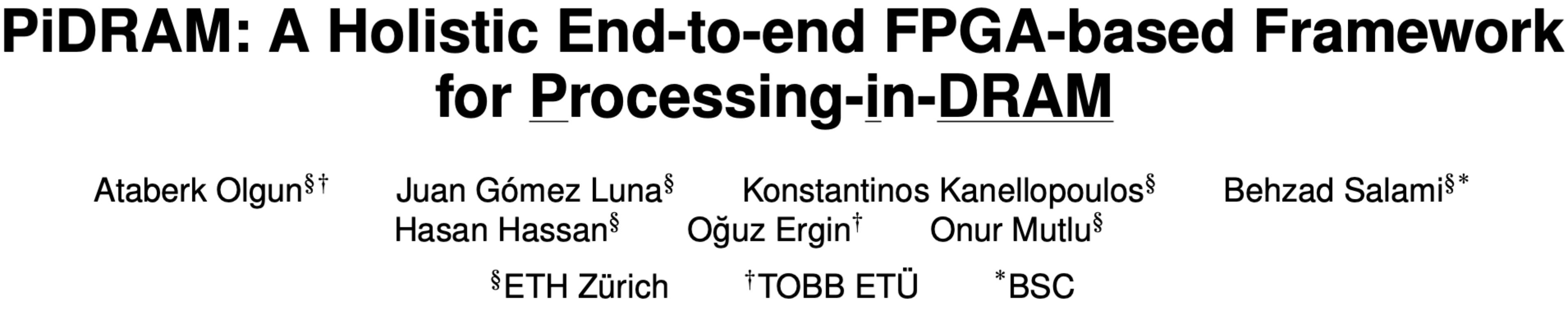
COTS DRAM chips can perform AND, NAND, OR, and NOR operations with very high reliability

Key Takeaway 3

Data pattern slightly affects the reliability of AND, NAND, OR, and NOR operations

Real Processing Using Memory Prototype

- End-to-end RowClone & TRNG using off-the-shelf DRAM chips
- Idea: Violate DRAM timing parameters to mimic RowClone



PiDRAM: A Holistic End-to-end FPGA-based Framework for Processing-in-DRAM

Ataberk Olgun[§†] Juan Gómez Luna[§] Konstantinos Kanellopoulos[§] Behzad Salami[§*]
Hasan Hassan[§] Oğuz Ergin[†] Onur Mutlu[§]

[§]ETH Zürich [†]TOBB ETÜ [*]BSC

https://arxiv.org/pdf/2111.00082.pdf

https://github.com/cmu-safari/pidram

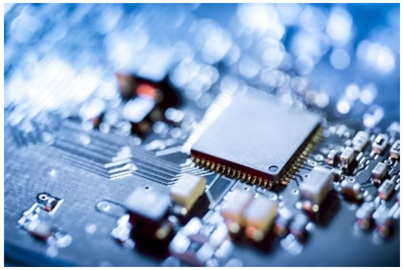
https://www.youtube.com/watch?v=qeukNs5XI3g&t=4192s

PiDRAM

Goal: Develop a **flexible** platform to explore **end-to-end** implementations of PuM techniques

- Enable rapid integration via key components

Hardware



❶ Easy-to-extend Memory Controller

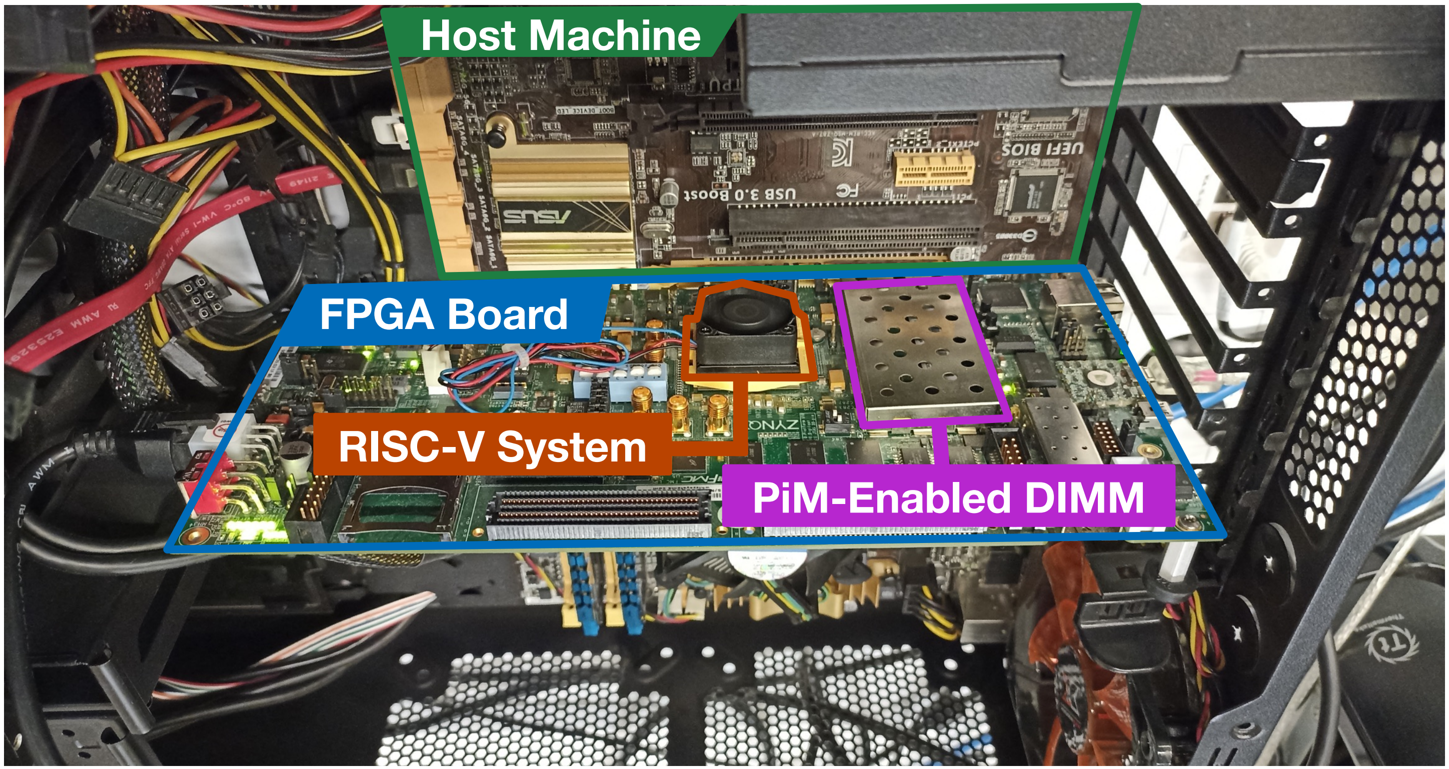
❷ ISA-transparent PuM Controller

Software

❶ Extensible Software Library

❷ Custom Supervisor Software

Real Processing Using Memory Prototype

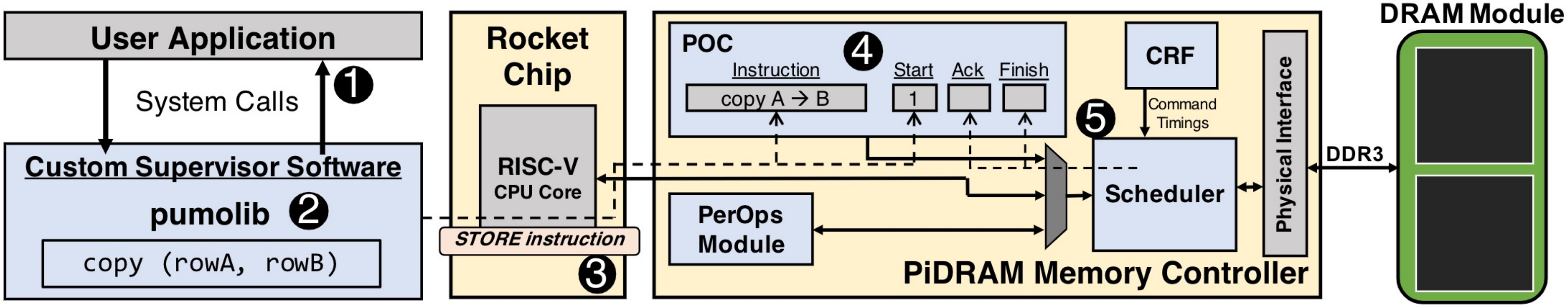


https://arxiv.org/pdf/2111.00082.pdf

https://github.com/cmu-safari/pidram

https://www.youtube.com/watch?v=qeukNs5XI3g&t=4192s

PiDRAM Workflow



1- User application interfaces with the OS via system calls

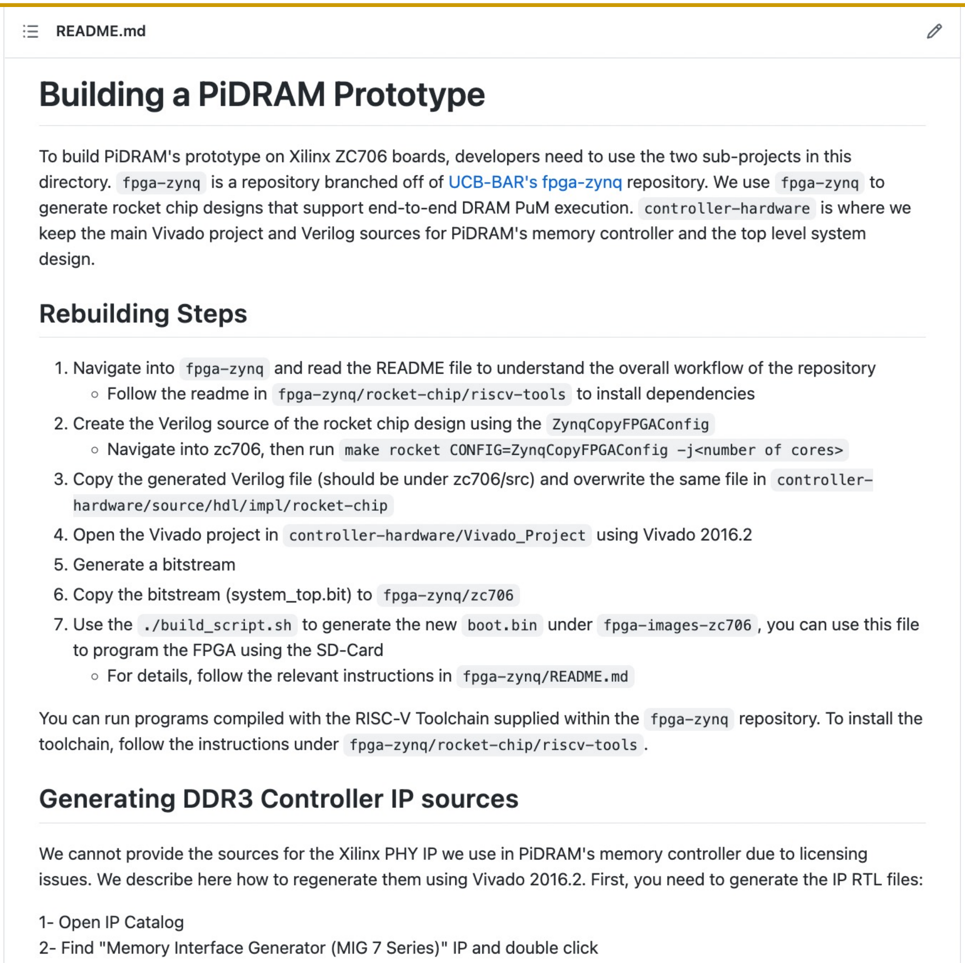
2- OS uses PuM Operations Library (pumolib) to convey operation related information to the hardware *using*

3- STORE instructions that target the memory mapped registers of the PuM Operations Controller (POC)

4- POC oversees the execution of a PuM operation (e.g., RowClone, bulk bitwise operations)

5- Scheduler arbitrates between regular (load, store) and PuM operations and issues DRAM commands with custom timings

Real Processing Using Memory Prototype



README.md

Building a PiDRAM Prototype

To build PiDRAM's prototype on Xilinx ZC706 boards, developers need to use the two sub-projects in this directory. `fpga-zynq` is a repository branched off of UCB-BAR's fpga-zynq repository. We use `fpga-zynq` to generate rocket chip designs that support end-to-end DRAM PuM execution. `controller-hardware` is where we keep the main Vivado project and Verilog sources for PiDRAM's memory controller and the top level system design.

Rebuilding Steps

1. Navigate into `fpga-zynq` and read the README file to understand the overall workflow of the repository
   - Follow the readme in `fpga-zynq/rocket-chip/riscv-tools` to install dependencies
2. Create the Verilog source of the rocket chip design using the `ZynqCopyFPGAConfig`
   - Navigate into zc706, then run `make rocket CONFIG=ZynqCopyFPGAConfig -j<number of cores>`
3. Copy the generated Verilog file (should be under zc706/src) and overwrite the same file in `controller-hardware/source/hdl/impl/rocket-chip`
4. Open the Vivado project in `controller-hardware/Vivado_Project` using Vivado 2016.2
5. Generate a bitstream
6. Copy the bitstream (system_top.bit) to `fpga-zynq/zc706`
7. Use the `./build_script.sh` to generate the new `boot.bin` under `fpga-images-zc706`, you can use this file to program the FPGA using the SD-Card
   - For details, follow the relevant instructions in `fpga-zynq/README.md`

You can run programs compiled with the RISC-V Toolchain supplied within the `fpga-zynq` repository. To install the toolchain, follow the instructions under `fpga-zynq/rocket-chip/riscv-tools`.

Generating DDR3 Controller IP sources

We cannot provide the sources for the Xilinx PHY IP we use in PiDRAM's memory controller due to licensing issues. We describe here how to regenerate them using Vivado 2016.2. First, you need to generate the IP RTL files:

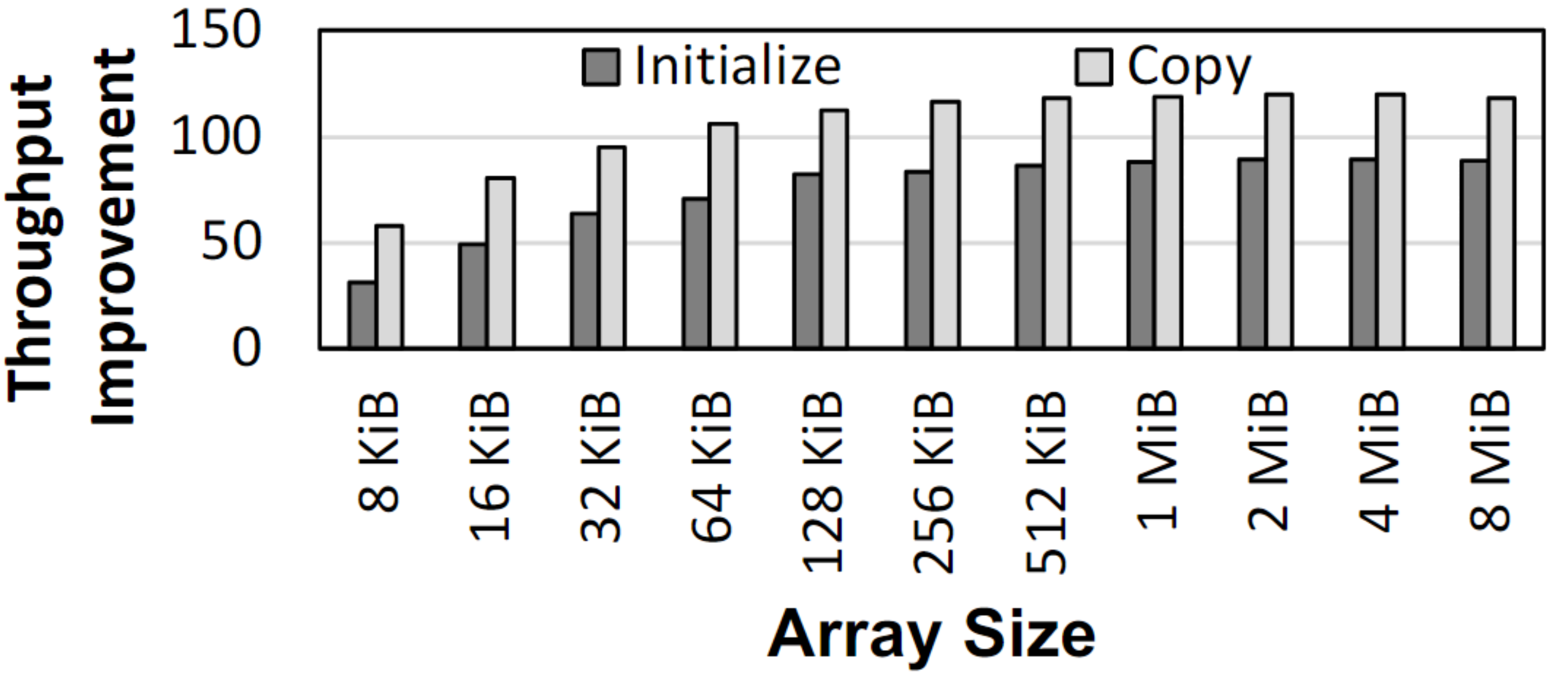
1- Open IP Catalog
2- Find "Memory Interface Generator (MIG 7 Series)" IP and double click

https://arxiv.org/pdf/2111.00082.pdf

https://github.com/cmu-safari/pidram

https://www.youtube.com/watch?v=qeukNs5XI3g&t=4192s

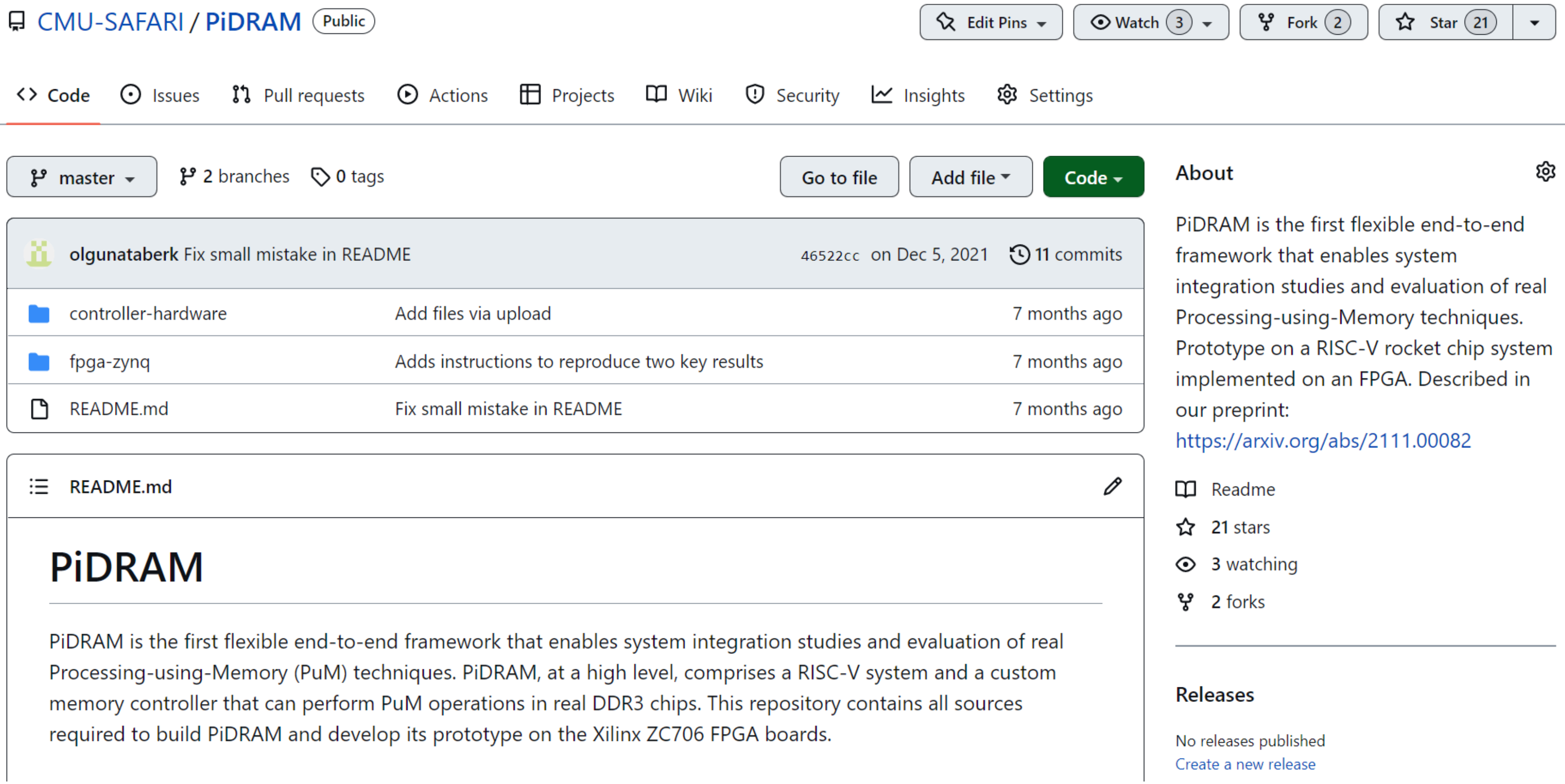
Microbenchmark Copy/Initialization Throughput



In-DRAM Copy and Initialization improve throughput by 119x and 89x

PiDRAM is Open Source

https://github.com/CMU-SAFARI/PiDRAM



olgunataberk Fix small mistake in README 46522cc on Dec 5, 2021 11 commits

controller-hardware	Add files via upload	7 months ago
fpga-zynq	Adds instructions to reproduce two key results	7 months ago
README.md	Fix small mistake in README	7 months ago

README.md

PiDRAM

PiDRAM is the first flexible end-to-end framework that enables system integration studies and evaluation of real Processing-using-Memory (PuM) techniques. PiDRAM, at a high level, comprises a RISC-V system and a custom memory controller that can perform PuM operations in real DDR3 chips. This repository contains all sources required to build PiDRAM and develop its prototype on the Xilinx ZC706 FPGA boards.

About

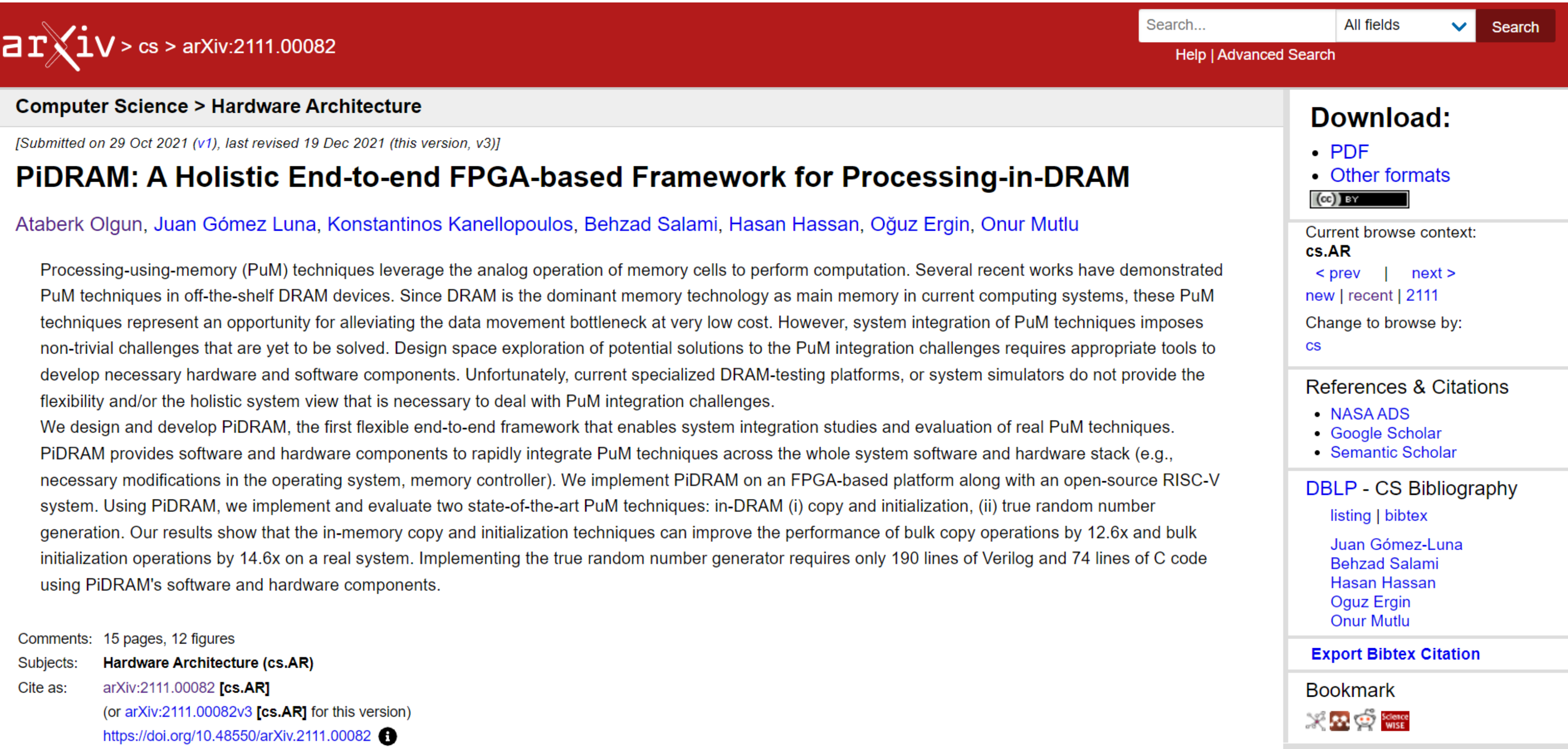
PiDRAM is the first flexible end-to-end framework that enables system integration studies and evaluation of real Processing-using-Memory techniques. Prototype on a RISC-V rocket chip system implemented on an FPGA. Described in our preprint: https://arxiv.org/abs/2111.00082

Releases

No releases published
Create a new release

Extended Version on ArXiv

https://arxiv.org/abs/2111.00082



Computer Science > Hardware Architecture

[Submitted on 29 Oct 2021 (v1), last revised 19 Dec 2021 (this version, v3)]

PiDRAM: A Holistic End-to-end FPGA-based Framework for Processing-in-DRAM

Ataberk Olgun, Juan Gómez Luna, Konstantinos Kanellopoulos, Behzad Salami, Hasan Hassan, Oğuz Ergin, Onur Mutlu

Processing-using-memory (PuM) techniques leverage the analog operation of memory cells to perform computation. Several recent works have demonstrated PuM techniques in off-the-shelf DRAM devices. Since DRAM is the dominant memory technology as main memory in current computing systems, these PuM techniques represent an opportunity for alleviating the data movement bottleneck at very low cost. However, system integration of PuM techniques imposes non-trivial challenges that are yet to be solved. Design space exploration of potential solutions to the PuM integration challenges requires appropriate tools to develop necessary hardware and software components. Unfortunately, current specialized DRAM-testing platforms, or system simulators do not provide the flexibility and/or the holistic system view that is necessary to deal with PuM integration challenges.

We design and develop PiDRAM, the first flexible end-to-end framework that enables system integration studies and evaluation of real PuM techniques. PiDRAM provides software and hardware components to rapidly integrate PuM techniques across the whole system software and hardware stack (e.g., necessary modifications in the operating system, memory controller). We implement PiDRAM on an FPGA-based platform along with an open-source RISC-V system. Using PiDRAM, we implement and evaluate two state-of-the-art PuM techniques: in-DRAM (i) copy and initialization, (ii) true random number generation. Our results show that the in-memory copy and initialization techniques can improve the performance of bulk copy operations by 12.6x and bulk initialization operations by 14.6x on a real system. Implementing the true random number generator requires only 190 lines of Verilog and 74 lines of C code using PiDRAM's software and hardware components.

Comments:	15 pages, 12 figures
Subjects:	**Hardware Architecture (cs.AR)**
Cite as:	arXiv:2111.00082 **[cs.AR]**
	(or arXiv:2111.00082v3 **[cs.AR]** for this version)
	https://doi.org/10.48550/arXiv.2111.00082 ℹ

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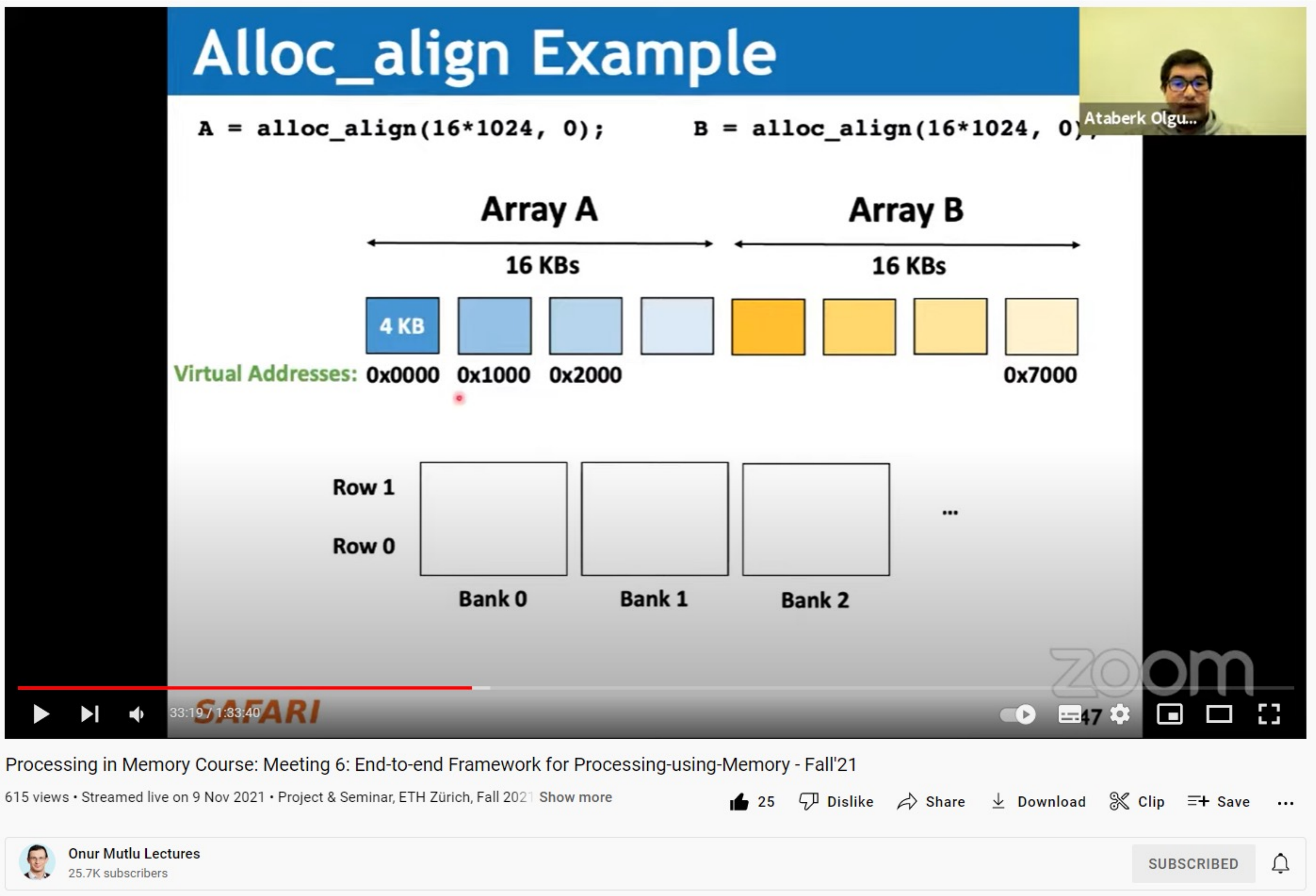

Alloc_align Example

```
A = alloc_align(16*1024, 0);        B = alloc_align(16*1024, 0);
```

Processing in Memory Course: Meeting 6: End-to-end Framework for Processing-using-Memory - Fall'21

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Onur Mutlu Lectures
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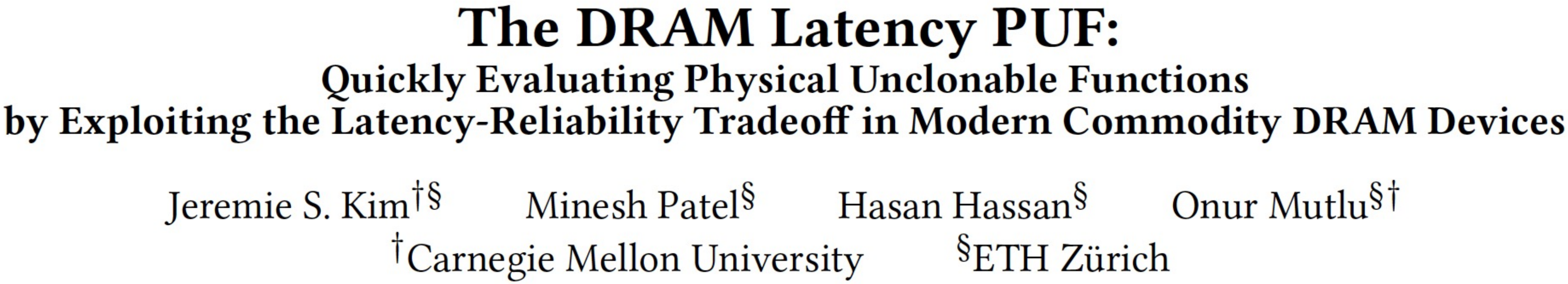
In-DRAM Physical Unclonable Functions

- Jeremie S. Kim, Minesh Patel, Hasan Hassan, and Onur Mutlu,
"The DRAM Latency PUF: Quickly Evaluating Physical Unclonable Functions by Exploiting the Latency-Reliability Tradeoff in Modern DRAM Devices"
*Proceedings of the 24th International Symposium on High-Performance Computer Architecture (**HPCA**)*, Vienna, Austria, February 2018.
[Lightning Talk Video]
[Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)]
[Full Talk Lecture Video (28 minutes)]

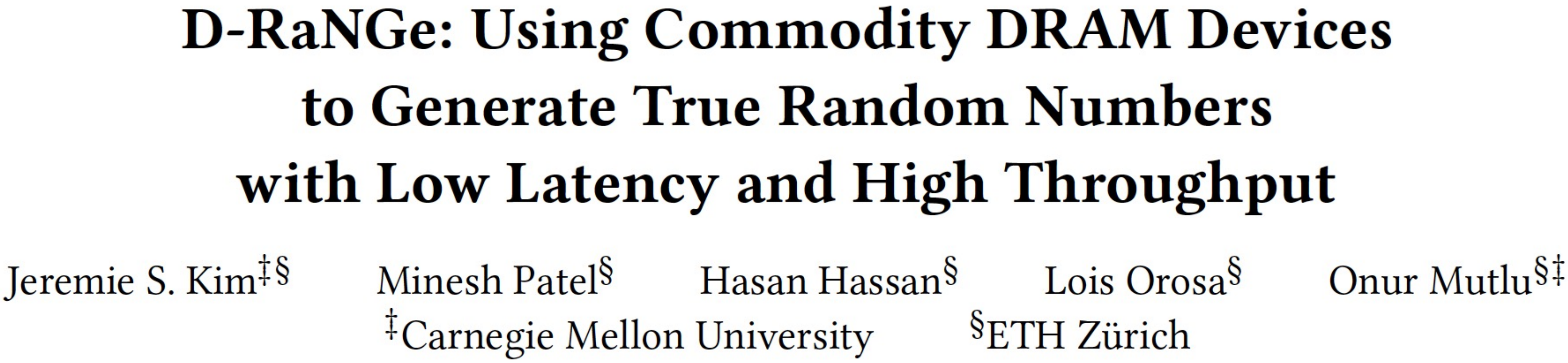


The DRAM Latency PUF:
Quickly Evaluating Physical Unclonable Functions
by Exploiting the Latency-Reliability Tradeoff in Modern Commodity DRAM Devices

Jeremie S. Kim[†§] Minesh Patel[§] Hasan Hassan[§] Onur Mutlu[§†]
[†]Carnegie Mellon University [§]ETH Zürich

In-DRAM True Random Number Generation

- Jeremie S. Kim, Minesh Patel, Hasan Hassan, Lois Orosa, and Onur Mutlu, **"D-RaNGe: Using Commodity DRAM Devices to Generate True Random Numbers with Low Latency and High Throughput"**
  Proceedings of the 25th International Symposium on High-Performance Computer Architecture (***HPCA***), Washington, DC, USA, February 2019.
  [Slides (pptx) (pdf)]
  [Full Talk Video (21 minutes)]
  [Full Talk Lecture Video (27 minutes)]
  Top Picks Honorable Mention by IEEE Micro.



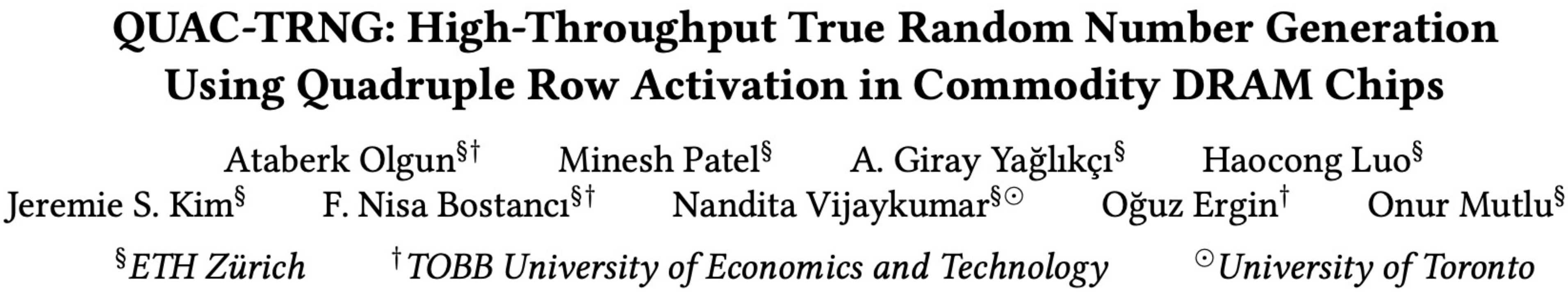
D-RaNGe: Using Commodity DRAM Devices to Generate True Random Numbers with Low Latency and High Throughput

Jeremie S. Kim‡§ Minesh Patel§ Hasan Hassan§ Lois Orosa§ Onur Mutlu§‡

‡Carnegie Mellon University §ETH Zürich

In-DRAM True Random Number Generation

- Ataberk Olgun, Minesh Patel, A. Giray Yaglikci, Haocong Luo, Jeremie S. Kim, F. Nisa Bostanci, Nandita Vijaykumar, Oguz Ergin, and Onur Mutlu,
  "QUAC-TRNG: High-Throughput True Random Number Generation Using Quadruple Row Activation in Commodity DRAM Chips"
  Proceedings of the 48th International Symposium on Computer Architecture (***ISCA***), Virtual, June 2021.
  [Slides (pptx) (pdf)]
  [Short Talk Slides (pptx) (pdf)]
  [Talk Video (25 minutes)]
  [SAFARI Live Seminar Video (1 hr 26 mins)]



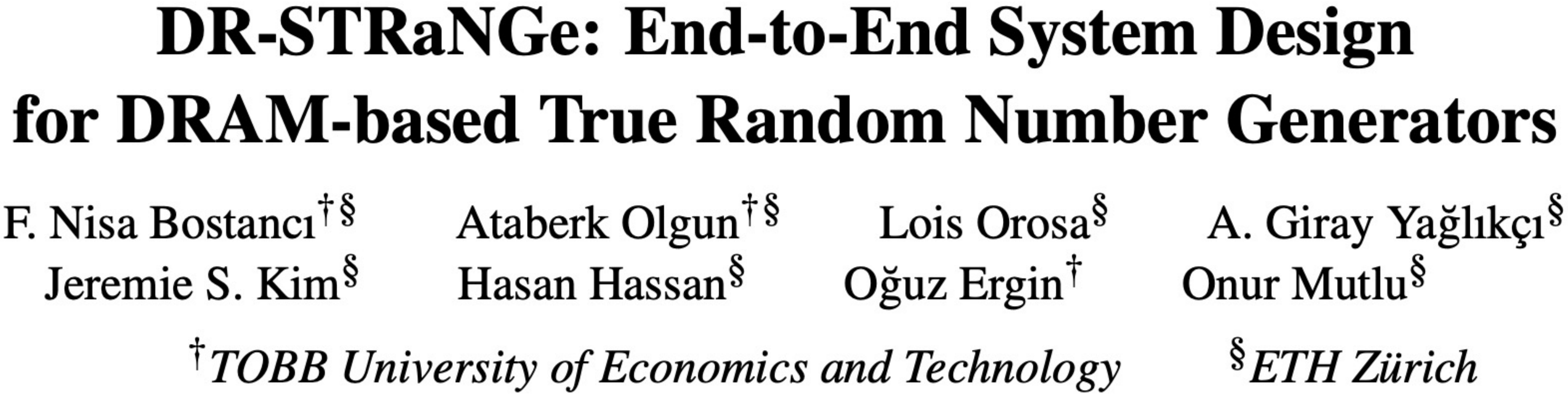
QUAC-TRNG: High-Throughput True Random Number Generation Using Quadruple Row Activation in Commodity DRAM Chips

Ataberk Olgun[§†] Minesh Patel[§] A. Giray Yağlıkçı[§] Haocong Luo[§]
Jeremie S. Kim[§] F. Nisa Bostancı[§†] Nandita Vijaykumar[§⊙] Oğuz Ergin[†] Onur Mutlu[§]

[§]ETH Zürich *[†]TOBB University of Economics and Technology* *[⊙]University of Toronto*

In-DRAM True Random Number Generation

- F. Nisa Bostanci, Ataberk Olgun, Lois Orosa, A. Giray Yaglikci, Jeremie S. Kim, Hasan Hassan, Oguz Ergin, and Onur Mutlu,
"DR-STRaNGe: End-to-End System Design for DRAM-based True Random Number Generators"
Proceedings of the 28th International Symposium on High-Performance Computer Architecture (***HPCA***), Virtual, April 2022.
[Slides (pptx) (pdf)]
[Short Talk Slides (pptx) (pdf)]



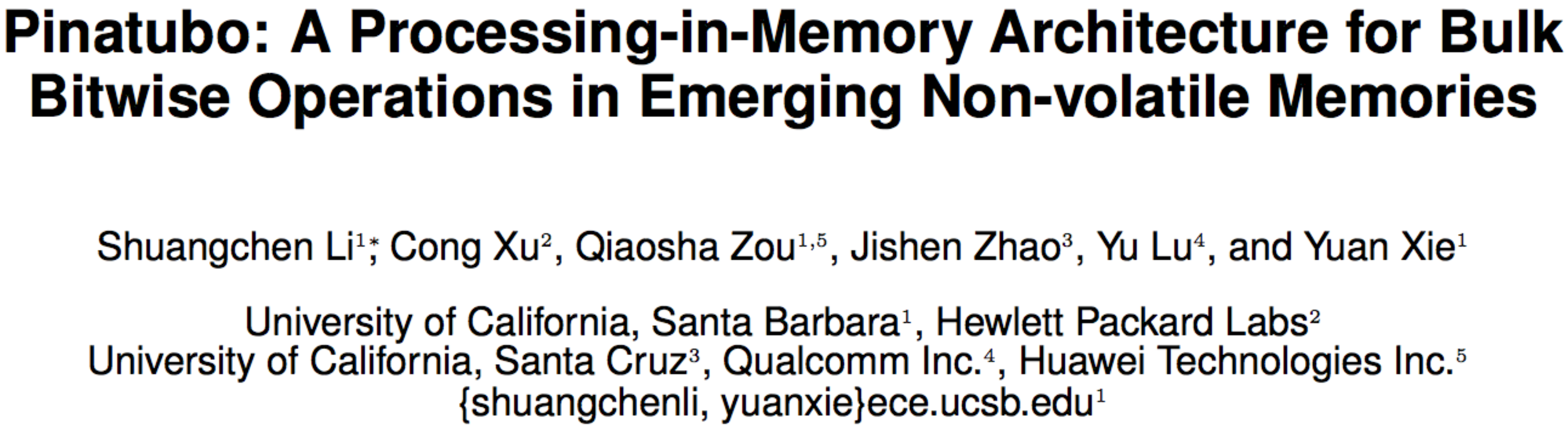
DR-STRaNGe: End-to-End System Design for DRAM-based True Random Number Generators

F. Nisa Bostancı[†][§] Ataberk Olgun[†][§] Lois Orosa[§] A. Giray Yağlıkçı[§]
Jeremie S. Kim[§] Hasan Hassan[§] Oğuz Ergin[†] Onur Mutlu[§]

[†]*TOBB University of Economics and Technology* [§]*ETH Zürich*

https://arxiv.org/pdf/2201.01385.pdf

Pinatubo: RowClone and Bitwise Ops in PCM



Pinatubo: A Processing-in-Memory Architecture for Bulk Bitwise Operations in Emerging Non-volatile Memories

Shuangchen Li[1]*, Cong Xu[2], Qiaosha Zou[1,5], Jishen Zhao[3], Yu Lu[4], and Yuan Xie[1]

University of California, Santa Barbara[1], Hewlett Packard Labs[2]
University of California, Santa Cruz[3], Qualcomm Inc.[4], Huawei Technologies Inc.[5]
{shuangchenli, yuanxie}ece.ucsb.edu[1]

https://cseweb.ucsd.edu/~jzhao/files/Pinatubo-dac2016.pdf

Pinatubo: RowClone and Bitwise Ops in PCM

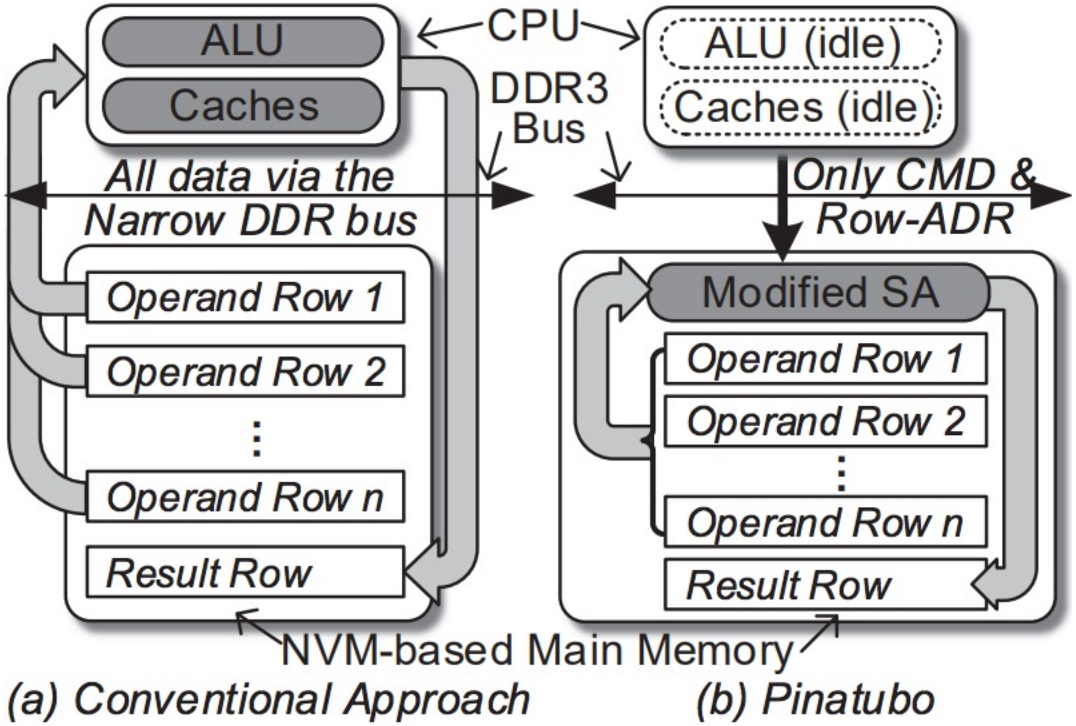
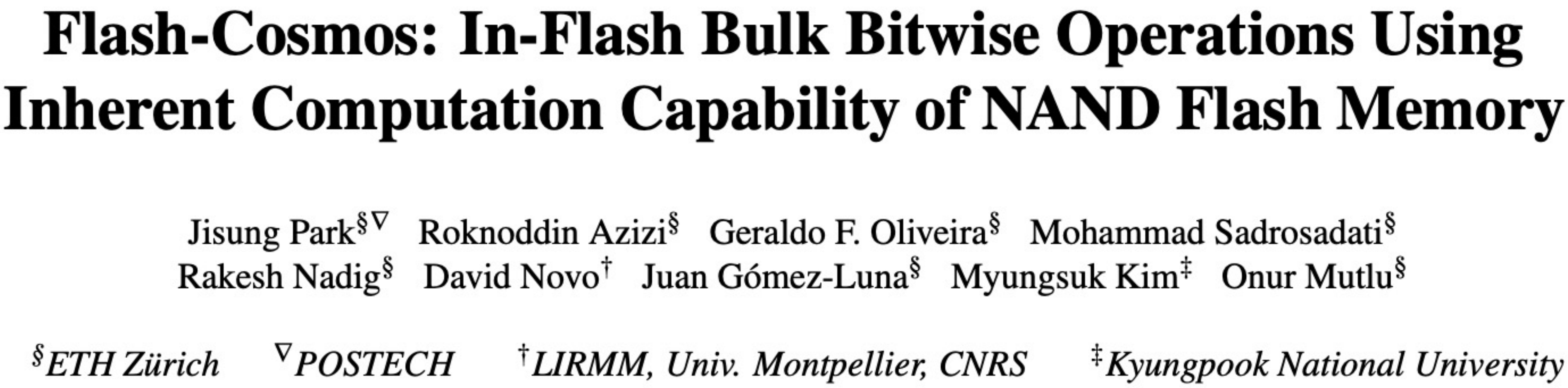


Figure 2: Overview: (a) Computing-centric approach, moving tons of data to CPU and write back. (b) The proposed Pinatubo architecture, performs n-row bitwise operations inside NVM in one step.

https://cseweb.ucsd.edu/~jzhao/files/Pinatubo-dac2016.pdf

In-Flash Bulk Bitwise Execution

- Jisung Park, Roknoddin Azizi, Geraldo F. Oliveira, Mohammad Sadrosadati, Rakesh Nadig, David Novo, Juan Gómez-Luna, Myungsuk Kim, and Onur Mutlu,
"Flash-Cosmos: In-Flash Bulk Bitwise Operations Using Inherent Computation Capability of NAND Flash Memory"
*Proceedings of the 55th International Symposium on Microarchitecture (**MICRO**)*, Chicago, IL, USA, October 2022.
[Slides (pptx) (pdf)]
[Longer Lecture Slides (pptx) (pdf)]
[Lecture Video (44 minutes)]
[arXiv version]



Flash-Cosmos: In-Flash Bulk Bitwise Operations Using Inherent Computation Capability of NAND Flash Memory

Jisung Park[§∇] Roknoddin Azizi[§] Geraldo F. Oliveira[§] Mohammad Sadrosadati[§]
Rakesh Nadig[§] David Novo[†] Juan Gómez-Luna[§] Myungsuk Kim[‡] Onur Mutlu[§]

[§]*ETH Zürich* [∇]*POSTECH* [†]*LIRMM, Univ. Montpellier, CNRS* [‡]*Kyungpook National University*

https://arxiv.org/pdf/2209.05566.pdf

Aside: In-Memory Crossbar Computation

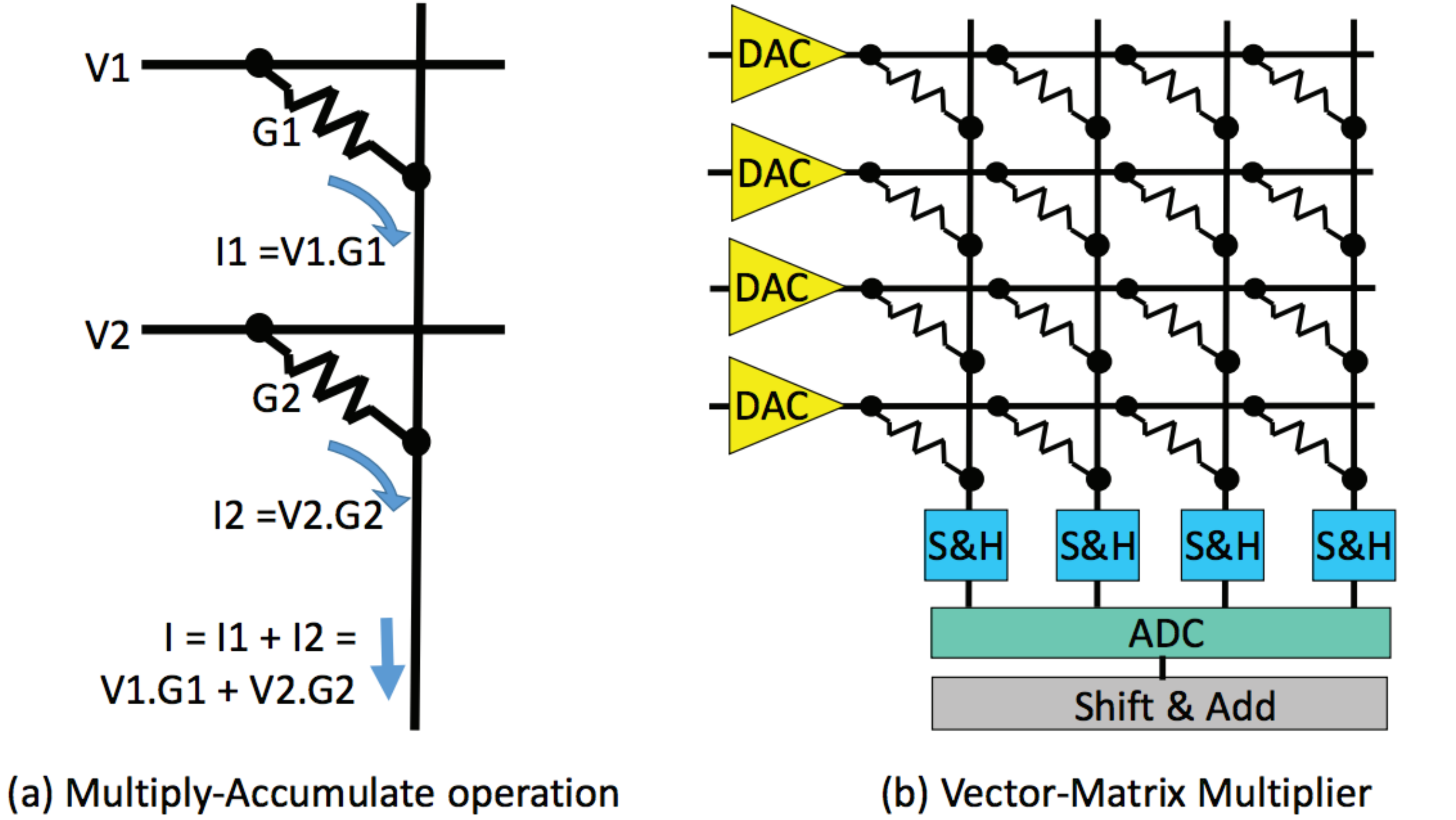
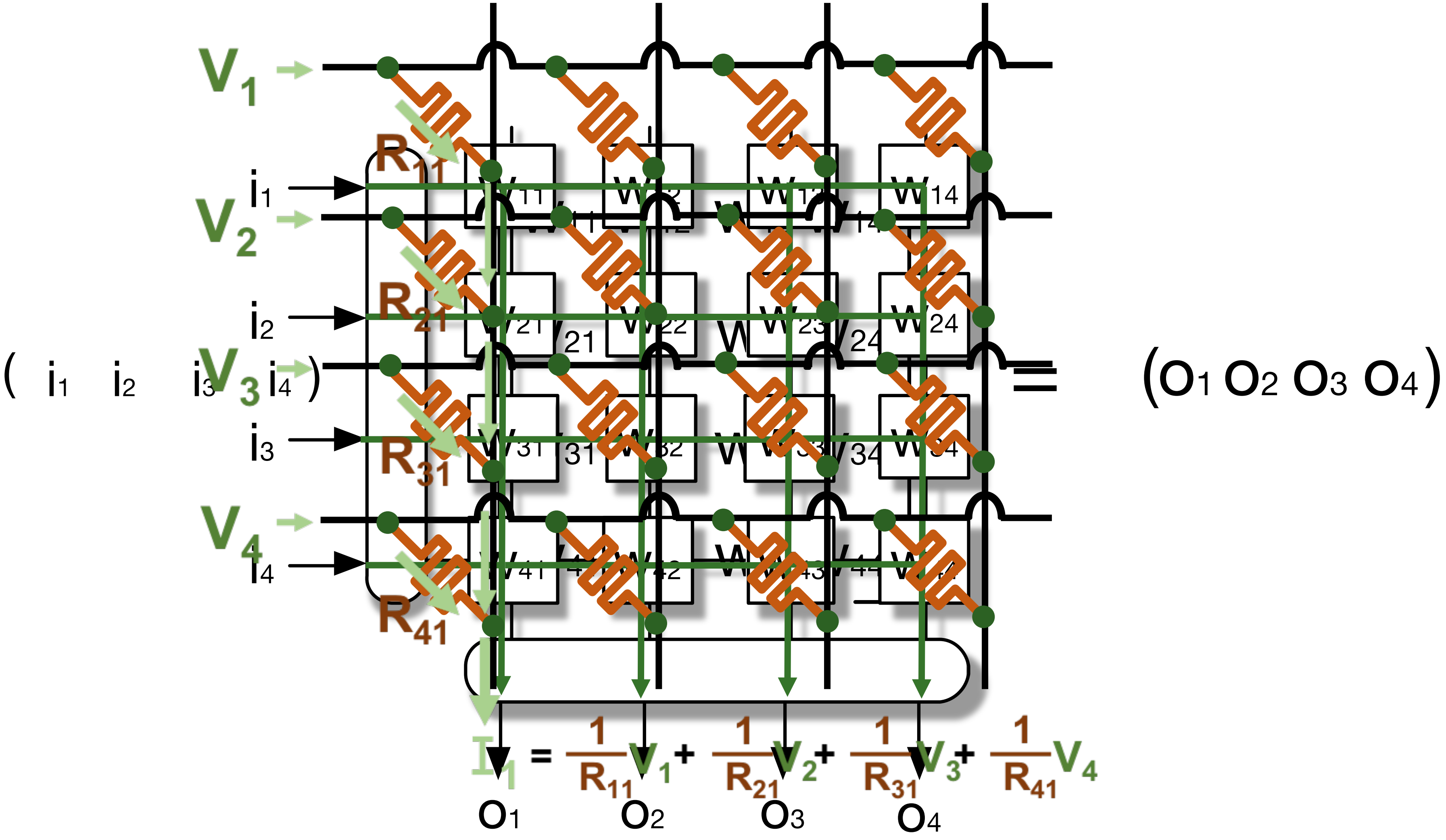


Fig. 1. (a) Using a bitline to perform an analog sum of products operation. (b) A memristor crossbar used as a vector-matrix multiplier.

Shafiee+, "ISAAC: A Convolutional Neural Network Accelerator with In-Situ Analog Arithmetic in Crossbars", ISCA 2016.

Aside: In-Memory Crossbar Computation



$$(i_1\ \ i_2\ \ i_3\ \ i_4) = (O_1\ O_2\ O_3\ O_4)$$

$$I_1 = \frac{1}{R_{11}}V_1 + \frac{1}{R_{21}}V_2 + \frac{1}{R_{31}}V_3 + \frac{1}{R_{41}}V_4$$

Tutorial on Memory-Centric Computing: Processing-Using-Memory

Geraldo F. Oliveira

Prof. Onur Mutlu

ISCA 2024

29 June 2024

Agenda

- Introduction to Memory-Centric Computing Systems
- Invited Talk by Prof. Minsoo Rhu:
  "*Memory-Centric Computing Systems – For AI and Beyond*"
- Coffee Break
- Real-World Processing-Near-Memory Systems
- Processing-Using-Memory Architectures for Bulk Bitwise Op.
- Invited Talk by Prof. Saugata Ghose:
  "*RACER and ReRAM PUM*"
- PIM Programming & Infrastructure for PIM Research
- Closing Remarks